Photomultiplier Tubes



HAMAMATSU

Opening The Future with Photonics

Hamamatsu has been engaged in photonics technology for 45 years and has developed a variety of photonic devices such as photodetectors, imaging devices, and scientific light sources. Our state-of-the-art photonic devices have applications in a wide range of fields, including scientific research, industrial instrumentation, and physical photometry as well as general electronics. The continually expanding frontiers of science demand equally constant exploration of new technology. Hamamatsu's research and development of photonic devices not only keep pace with scientific needs, but stay one step ahead, pioneering new trails into the future of light and optics.

This catalog provides information on our photomultiplier tubes, their accessories, electron multipliers and microchannel plates. But this catalog is just the starting point of our line because we will modify our production specs or design completely new types to match your performance specs.

Variants of the listed types are usually available with:

- 1. Different photocathode materials
- 2. Different window materials
- 3. Different configurations and pin connections
- 4. Other special requirements for your applications

For further information, please contact your nearest Hamamatsu sales offices.

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PHOTOMULTIPLIER TUBES

Construction and Operating Characteristics

INTRODUCTION

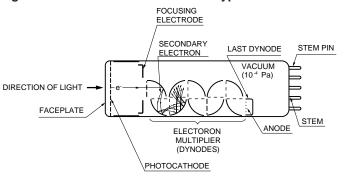
Among the photosensitive devices in use today, the photomultiplier tube (or PMT) is a versatile device that provides extremely high sensitivity and ultra-fast response. A typical photomultiplier tube consists of a photoemissive cathode (photocathode) followed by focusing electrodes, an electron multiplier and an electron collector (anode) in a vacuum tube, as shown in Figure 1

When light enters the photocathode, the photocathode emits photoelectrons into the vacuum. These photoelectrons are then directed by the focusing electrode voltages towards the electron multiplier where electrons are multiplied by the process of secondary emission. The multiplied electrons are collected by the anode as an output signal.

Because of secondary-emission multiplication, photomultiplier tubes provide extremely high sensitivity and exceptionally low noise among the photosensitive devices currently used to detect radiant energy in the ultraviolet, visible, and near infrared regions. The photomultiplier tube also features fast time response, low noise and a choice of large photosensitive areas.

This section describes the prime features of photomultiplier tube construction and basic operating characteristics.

Figures 1: Cross-Section of Head-On Type PMT



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CONSTRUCTION

The photomultiplier tube generally has a photocathode in either a side-on or a head-on configuration. The side-on type receives incident light through the side of the glass bulb, while in the head-on type, it is received through the end of the glass bulb. In general, the side-on type photomultiplier tube is relatively low priced and widely used for spectrophotometers and general photometric systems. Most of the side-on types employ an opaque photocathode (reflection-mode photocathode) and a circular-cage structure electron multiplier which has good sensitivity and high amplification at a relatively low supply voltage.

The head-on type (or the end-on type) has a semitransparent photocathode (transmission-mode photocathode) deposited upon the inner surface of the entrance window. The head-on type provides better spatial uniformity (see page 10) than the side-on type having a reflection-mode photocathode. Other features of head-on types include a choice of photosensitive areas from tens of square millimeters to hundreds of square centimeters.

Variants of the head-on type having a large-diameter hemispherical window have been developed for high energy physics experiments where good angular light acceptability is important.

Figure 2: External Appearance
a) Side-On Type
b) Head-On Type

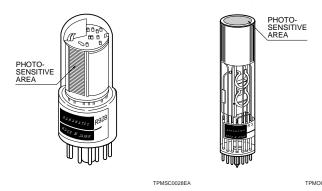
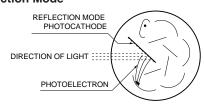
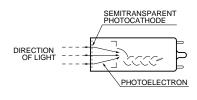


Figure 3: Types of Photocathode a) Reflection Mode



b) Transmission Mode



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ELECTRON MULTIPLIER

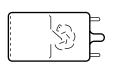
The superior sensitivity (high current amplification and high S/N ratio) of photomultiplier tubes is due to the use of a low-noise electron multiplier which amplifies electrons by a cascade secondary electron emission process. The electron multiplier consists of from 8, up to 19 stages of electrodes called dynodes.

There are several principal types in use today.

1) Circular-cage type

The circular-cage is generally used for the side-on type of photomultiplier tube. The prime features of the circular-cage are compactness and fast time response.

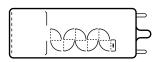




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2) Box-and-grid type

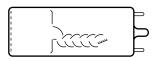
This type consists of a train of quarter cylindrical dynodes and is widely used in head-on type photomultiplier tubes because of its relatively simple dynode design and improved uniformity, although time response may be too slow in some applications.



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3) Linear-focused type

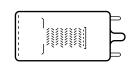
The linear-focused type features extremely fast response time and is widely used in head-on type photomultiplier tubes where time resolution and pulse linearity are important.



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4) Venetian blind type

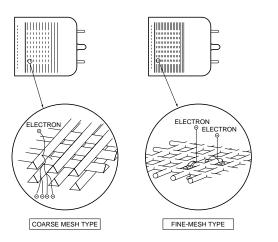
The venetian blind type has a large dynode area and is primarily used for tubes with large photocathode areas. It offers better uniformity and a larger pulse output current. This structure is usually used when time response is not a prime consideration.



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5) Mesh type

The mesh type has a structure of fine mesh electrodes stacked in close proximity. This type provides high immunity to magnetic fields, as well as good uniformity and high pulse linearity. In addition, it has position-sensitive capability when used with cross-wire anodes or multiple anodes. (See pages 58 and 59.)



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6) Microchannel plate (MCP)

The MCP is a thin disk consisting of millions of micro glass tubes (channels) fused in parallel with each other. Each channel acts as an independent electron multiplier. The MCP offers much faster time response than the other discrete dynodes. It also features good immunity from magnetic fields and two-dimensional detection ability when multiple anodes are used. (See pages 60 and 61 for MCP-PMTs.)



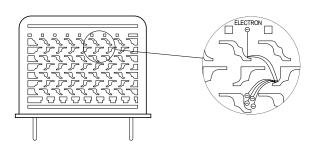
TPMOC008

7) Metal channel type

The Metal channel dynode has a compact dynode costruction manufactured by our unique fine machining technique.

It achieves high speed response due to its narrower space between each stage of dynodes than the other type of conventional dynode construction.

It is also adequate for position sensitive measurement.



In addition, hybrid dynodes combining two of the above dynodes are available. These hybrid dynodes are designed to

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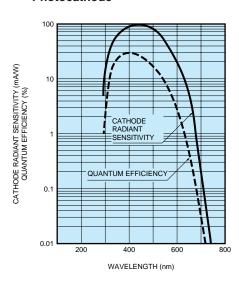
provide the merits of each dynode.

SPECTRAL RESPONSE

The photocathode of a photomultiplier tube converts energy of incident light into photoelectrons. The conversion efficiency (photocathode sensitivity) varies with the wavelength of the incident light. This relationship between photocathode sensitivity and wavelength is called the spectral response characteristic. Figure 4 shows the typical spectral response of a bialkali photomultiplier tube. The spectral response characteristics are determined on the long wavelength side by the photocathode material and on the short wavelength side by the window material. Typical spectral response characteristics for various types of photomultiplier tubes are shown on pages 88 and 89. In this catalog, the longwavelength cut-off of spectral response characteristics is defined as the wavelength at which the cathode radiant sensitivity becomes 1% of the maximum sensitivity for bialkali and Ag-O-Cs photocathodes, and 0.1% of the maximum sensitivity for multialkali photocathodes.

Spectral response characteristics shown at the end of this catalog are typical curves for representative tube types. Actual data may be different from type to type.

Figure 4: Typical Spectral Response of Head-On, Bialkali Photocathode



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PHOTOCATHODE MATERIALS

The photocathode is a photoemissive surface usually consisting of alkali metals with very low work functions. The photocathode materials most commonly used in photomultiplier tubes are as follows:

1) Ag-O-Cs

The transmission-mode photocathode using this material is designated S-1 and sensitive from the visible to infrared range (300 to 1200nm). Since Ag-O-Cs has comparatively high thermionic dark emission (refer to "ANODE DARK CURRENT" on page 8), tubes of this photocathode are mainly used for detection in the near infrared region with the photocathode cooled.

2) GaAs(Cs)

GaAs activated in cesium is also used as a photocathode. The spectral response of this photocathode usually covers a wider spectral response range than multialkali, from ultraviolet to 930nm, which is comparatively flat over 300 to 850nm.

3) InGaAs(Cs)

This photocathode has greater extended sensitivity in the infrared range than GaAs. Moreover, in the range between 900 and 1000nm, InGaAs has much higher S/N ratio than Ag-O-Cs.

4) Sb-Cs

This is a widely used photocathode and has a spectral response in the ultraviolet to visible range. This is not suited for transmission-mode photocathodes and mainly used for reflection-mode photocathodes.

5) Bialkali (Sb-Rb-Cs, Sb-K-Cs)

These have a spectral response range similar to the Sb-Cs photocathode, but have higher sensitivity and lower noise than Sb-Cs. The transmission mode bialkali photocathodes also have a favorable blue sensitivity for scintillator flashes from NaI (TI) scintillators, thus are frequently used for radiation measurement using scintillation counting.

6) High temperature bialkali or low noise bialkali (Na-K-Sb)

This is particularly useful at higher operating temperatures since it can withstand up to 175°C. A major application is in the oil well logging industry. At room temperatures, this photocathode operates with very low dark current, making it ideal for use in photon counting applications.

7) Multialkali (Na-K-Sb-Cs)

The multialkali photocathode has a high, wide spectral response from the ultraviolet to near infrared region. It is widely used for broad-band spectrophotometers. The long wavelength response can be extended out to 930nm by special photocathode processing.

8) Cs-Te, Cs-I

These materials are sensitive to vacuum UV and UV rays but not to visible light and are therefore called solar blind. Cs-Te is quite insensitive to wavelengths longer than 320nm, and Cs-I to those longer than 200nm.

WINDOW MATERIALS

The window materials commonly used in photomultiplier tubes are as follows:

1) Borosilicate glass

This is frequently used glass material. It transmits radiation from the near infrared to approximately 300nm. It is not suitable for detection in the ultraviolet region. For some applications, the combination of a bialkali photocathode and a low-noise borosilicate glass (so called K-free glass) is used. The K-free glass contains very low potassium (K2O) which can cause background counts by ⁴⁰K. In particular, tubes designed for scintillation counting often employ K-free glass not only for the faceplate but also for the side bulb to minimize noise pulses.

2) UV-transmitting glass (UV glass)

This glass transmits ultraviolet radiation well, as the name implies, and is widely used as a borosilicate glass. For spectroscopy applications, UV glass is commonly used. The UV cut-off is approximately 185nm.

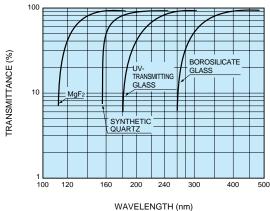
3) Synthetic silica

The synthetic silica transmits ultraviolet radiation down to 160nm and offers lower absorption in the ultraviolet range compared to fused silica. Since thermal expansion coefficient of the synthetic silica is different from Kovar which is used for the tube leads, it is not suitable for the stem material of the tube (see Figure 1 on page 4). Borosilicate glass is used for the stem, then a graded seal using glasses with gradually different thermal expansion coefficients are connected to the synthetic silica window. Because of this structure, the graded seal is vulnerable to mechanical shock so that sufficient care should be taken in handling the tube.

4) MgF₂ (magnesium fluoride)

The crystals of alkali halide are superior in transmitting ultraviolet radiation, but have the disadvantage of deliquescence. Among these, MgF2 is known as a practical window material because it offers low deliquescence and transmits ultraviolet radiation down to 115nm.

Figure 5: Typical Transmittance of Various Window Materials



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As stated above, spectral response range is determined by the photocathode and window materials. It is important to select an appropriate combination which will suit your applications.

RADIANT SENSITIVITY AND QUANTUM EFFICIENCY

As Figure 4 shows, spectral response is usually expressed in terms of radiant sensitivity or quantum efficiency as a function of wavelength. Radiant sensitivity (S) is the photoelectric current from the photocathode, divided by the incident radiant power at a given wavelength, expressed in A/W (amperes per watt). Quantum efficiency (QE) is the number of photoelectrons emitted from the photocathode divided by the number of incident photons. It is customary to present quantum efficiency in a percentage. Quantum efficiency and radiant sensitivity have the following relationship at a given wavelength.

$$QE = \frac{S \times 1240}{\lambda} \times 100\%$$

Where S is the radiant sensitivity in A/W at the given wavelength, and λ is the wavelength in nm (nanometers).

LUMINOUS SENSITIVITY

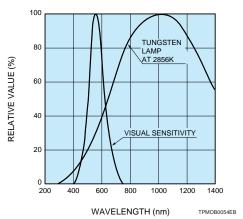
Since the measurement of the spectral response characteristic of a photomultiplier tube requires a sophisticated system and much time, it is not practical to provide customers with spectral response characteristics for each tube ordered. Instead cathode or anode luminous sensitivity is commonly used.

The cathode luminous sensitivity is the photoelectric current from the photocathode per incident light flux (10-5 to 10-2 lumens) from a tungsten filament lamp operated at a distribution temperature of 2856K. The anode luminous sensitivity is the anode output current (amplified by the secondary emission process) per incident light flux (10-10 to 10-5 lumens) on the photocathode. Although the same tungsten lamp is used, the light flux and the applied voltage are adjusted to an appropriate level. These parameters are particularly useful when comparing tubes having the same or similar spectral response range. Hamamatsu final

test sheets accompanying the tubes usually indicate these parameters except for tubes with Cs-I or Cs-Te photocathodes, which are not sensitive to tungsten lamp light. (Radiant sensitivity at a specific wavelength is listed for those tubes instead.)

Both the cathode and anode luminous sensitivities are expressed in units of A/Im (amperes per lumen). Note that the lumen is a unit used for luminous flux in the visible region and therefore these values may be meaningless for tubes which are sensitive beyond the visible region. (For those tubes, the blue sensitivity or red/white ratio is often used.)

Figure 6: Typical Human Eye Response and Spectral Energy Distribution of 2856K Tungsten Lamp



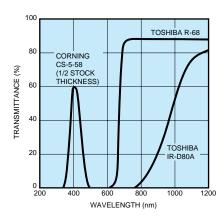
BLUE SENSITIVITY AND RED/WHITE RATIO

For simple comparison of spectral response of photomultiplier tubes, cathode blue sensitivity and red/white ratio are often used

The cathode blue sensitivity is the photoelectric current from the photocathode produced by a light flux of a tungsten lamp at 2856K passing through a blue filter (Corning CS No. 5-58 polished to half stock thickness). Since the light flux, once transmitted through the blue filter cannot be expressed in lumens, blue sensitivity is conveniently expressed in A/lm-b (amperes per lumen-blue). The blue sensitivity is an important parameter in scintillation counting using an NaI (TI) scintillator since the NaI (TI) scintillator produces emissions in the blue region of the spectrum, and may be the decisive factor in energy resolution.

The red/white ratio is used for photomultiplier tubes with a spectral response extending to the near infrared region. This parameter is defined as the quotient of the cathode sensitivity measured with a light flux of a tungsten lamp at 2856K passing through a red filter (Toshiba IR-D80A for the S-1 photocathode or R-68 for others) divided by the cathode luminous sensitivity with the filter removed.

Figure 7: Transmittance of Various Filters



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CURRENT AMPLIFICATION (GAIN)

Photoelectrons emitted from a photocathode are accelerated by an electric field so as to strike the first dynode and produce secondary electron emissions. These secondary electrons then impinge upon the next dynode to produce additional secondary electron emissions. Repeating this process over successive dynode stages, a high current amplification is achieved. A very small photoelectric current from the photocathode can be observed as a large output current from the anode of the photomultiplier tube.

Current amplification is simply the ratio of the anode output current to the photoelectric current from the photocathode. Ideally, the current amplification of a photomultiplier tube having n dynode stage and an average secondary emission ratio δ per stage is δ^n . While the secondary electron emission ratio δ is given by

$$\delta = A \ EE^{\alpha}$$

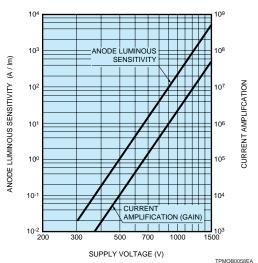
where A is constant, E is an interstage voltage, and α is a coefficient determined by the dynode material and geometric structure. It usually has a value of 0.7 to 0.8.

When a voltage V is applied between the cathode and the anode of a photomultiplier tube having n dynode stages, current amplification, μ , becomes

$$\mu = \delta^{n} = (A \cdot E^{\alpha})^{n} = \left\{ A \cdot \left(\frac{V}{n+1} \right)^{\alpha} \right\}^{n}$$
$$= \frac{A^{n}}{(n+1)^{\alpha n}} \cdot V^{\alpha n} = K \cdot V^{\alpha n}$$

Since photomultiplier tubes generally have 9 to 12 dynode stages, the anode output varies directly with the 6th to 10th power of the change in applied voltage. The output signal of the photomultiplier tube is extremely susceptible to fluctuations in the power supply voltage, thus the power supply must be very stable and provide minimum ripple, drift and temperature coefficient. Various types of regulated high-voltage power supplies designed with this consideration are available from Hamamatsu (see page 80).

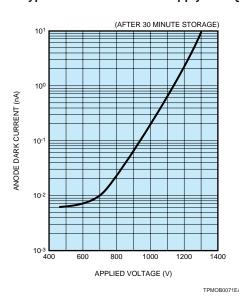
Figure 8: Typical Current Amplification vs. Supply Voltage



ANODE DARK CURRENT

A small amount of current flows in a photomultiplier tube even when the tube is operated in a completely dark state. This output current, called the anode dark current, and the resulting noise are critical factors in determining the detectivity of a photomultiplier tube. As Figure 9 shows, dark current is greatly dependent on the supply voltage.

Figure 9: Typical Dark Current vs. Supply Voltage



Major sources of dark current may be categorized as follows:

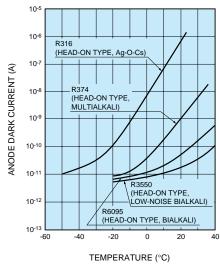
1) Thermionic emission of electrons

Since the materials of the photocathode and dynodes have very low work functions, they emit thermionic electrons even at room temperature. Most of dark currents originate from the thermionic emissions, especially those from the photocathode as they are multiplied by the dynodes. Cooling the photocathode is most effective in reducing thermionic emission and, this is particularly useful in applications where

low dark counts are essential such as in photon counting.

Figure 10 shows the relationship between dark current and temperature for various photocathodes. Photocathodes which have high sensitivity in the red to infrared region, especially S-1, show higher dark current at room temperature. Hamamatsu provides thermoelectric coolers (C659 and C4877) designed for various sizes of photomultiplier tubes (see page 81).

Figure 10: Temperature Characteristics of Dark Current



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2) Ionization of residual gases (ion feedback)

Residual gases inside a photomultiplier tube can be ionized by collision with electrons. When these ions strike the photocathode or earlier stages of dynodes, secondary electrons may be emitted, thus resulting in relatively large output noise pulses. These noise pulses are usually observed as afterpulses following the primary signal pulses and may be a problem in detecting light pulses. Present photomultiplier tubes are designed to minimize afterpulses.

3) Glass scintillation

When electrons deviating from their normal trajectories strike the glass envelope, scintillations may occur and dark pulses may result. To minimize this type of dark pulse, photomultiplier tubes may be operated with the anode at high voltage and the cathode at ground potential. But this is inconvenient to handle the tube. To obtain the same effect without difficulty, Hamamatsu provides "HA coating" in which the glass bulb is coated with a conductive paint connected to the cathode. (See "GROUND POLARITY AND HA COATING" on page 13.)

4) Leakage current (ohmic leakage)

Leakage current resulting from the glass stem base and socket may be another source of dark current. This is predominant when the photomultiplier tube is operated at a low voltage or low temperature. The flatter slopes in Figures 9 and 10 are mainly due to leakage current.

Contamination from dirt and moisture on the surface of the tube may increase the leakage current, and therefore should be avoided.

5) Field emission

When a photomultiplier tube is operated at a voltage near the maximum rated value, electrons may be emitted from electrodes by the strong electric field and may cause noise pulses. It is therefore recommended that the tube be operated at a voltage 20 to 30% lower than the maximum rating. The anode dark current decreases with time after the tube is placed in a dark state. In this catalog, anode dark currents are measured after 30-minute storage in a dark state.

ENI (EQUIVALENT NOISE INPUT)

ENI is an indication of the photon-limited signal-to-noise ratio. It refers to the amount of light usually in watts or lumens necessary to produce a signal-to-noise ratio of unity in the output of a photomultiplier tube. ENI is expressed in units of lumens or watts. For example the value of ENI (in watts) is given by

$$ENI = \frac{\sqrt{2q \cdot Idb \cdot \mu \cdot \Delta f}}{S}$$
 (watts or lumens)

wher

q = electronic charge $(1.60 \times 10^{-19} \text{ coul.})$

Idb = anode dark current in amperes after 30-minute storage in darkness

μ = current amplification

μ = current amplification

 \(\Delta = \) bandwidth of the system in hertz (usually 1 hertz)

 \(S = \) anode radiant sensitivity in amperes per watt at the wavelength of interest or anode luminous

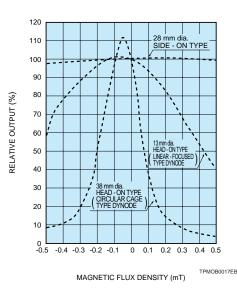
sensitivity in amperes per lumen

For the tubes listed in this catalog, the value of ENI may be calculated by the above equation. Usually it has a value between 10^{-15} and 10^{-16} watts or lumens.

MAGNETIC FIELD EFFECTS

Most photomultiplier tubes are affected by the presence of magnetic fields. Magnetic fields may deflect electrons from their normal trajectories and cause a loss of gain. The extent of the loss of gain depends on the type of photomultiplier tube and its orientation in the magnetic field. Figure 11 shows typical effects of magnetic fields on some types of photomultiplier tubes. In general, tubes having a long path from the photocathode to the first dynode are very vulnerable to magnetic fields. Therefore headon types, especially large diameter tubes, tend to be more adversely influenced by magnetic fields.

Figure 11: Typical Effects by Magnetic Fields Perpendicular to Tube Axis

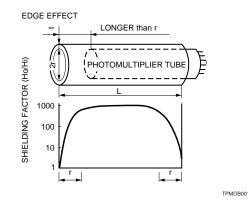


When a tube has to be operated in magnetic fields, it may be necessary to shield the tube with a magnetic shield case. Hamamatsu provides a variety of magnetic shield cases (see page 81). To express the effect of a magnetic shield case, the magnetic shielding factor is used. This is the ratio of the strength of the magnetic field outside the shield case, Hout, to that inside the shield case, Hin. It is determined by the permeability $\mu,$ the thickness t (mm) and inner diameter D (mm) of the shield case, as follows:

$$\frac{\text{Hout}}{\text{Hin}} = \frac{3\mu t}{4 \text{ D}}$$

It should be noted that the magnetic shielding effect decreases towards the edge of the shield case as shown in Figure 12. It is recommended that the tube be covered by a shield case longer than the tube length by at least half the tube diameter.

Figure 12: Edge Effect of Magnetic Shield Case



Hamamatsu provides photomultiplier tubes using fine mesh dynodes (see page 56). These tube types (see page 56) exhibit much higher immunity to external magnetic fields than the photomultiplier tubes using other dynodes. In addition, when the light level to be measured is rather high, triode or tetrode type photomultiplier tubes can be used in hishly magnetic fields.

SPATIAL UNIFORMITY

Spatial uniformity is the variation of sensitivity with position of incident light on a photocathode.

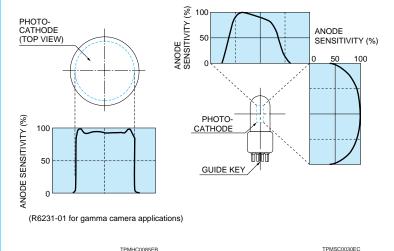
Although the focusing electrodes of a photomultiplier tube are designed so that electrons emitted from the photocathode or dynodes are collected efficiently by the first or following dynodes, some electrons may deviate from their desired trajectories in the focusing and multiplication processes, resulting in a loss of collection efficiency. This loss of collection efficiency varies with the position on the photocathode from which the photoelectrons are emitted and influences the spatial uniformity of a photomultiplier tube. The spatial uniformity is also determined by the photocathode surface uniformity itself.

In general, head-on type photomultiplier tubes provide better spatial uniformity than side-on types because of the photocath-ode to first dynode geometry. Tubes especially designed for gamma camera applications have excellent spatial uniformity, because uniformity is the decisive factor in the overall performance of a gamma camera.

Figure 13: Examples of Spatial Uniformity

(a) Head-On Type
(R6231-01 for gamma camera applications)

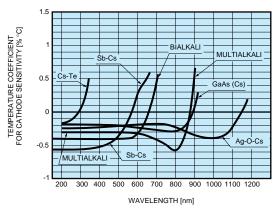
(b) Side-On Type
Reflection-mode photocathode



TEMPERATURE CHARACTERISTICS

By decreasing the temperature of a photomultiplier tube, dark current originating from thermionic emission can be reduced. Sensitivity of the photomultiplier tube also varies with the temperature. In the ultraviolet to visible region, the temperature coefficient of sensitivity usually has a negative value, while near the long wavelength cut-off it has a positive value. Figure 14 shows temperature coefficients vs. wavelength of typical photomultiplier tubes. Since the temperature coefficient change is large near the long wavelength cutoff, temperature control may be required in some applications.

Figure 14: Typical Temperature Coefficients of Anode Sensitivity



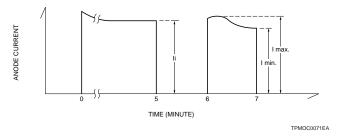
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HYSTERESIS

A photomultiplier tube may exhibit an unstable output for several seconds to several tens of seconds after voltage and light are applied, i.e., output may slightly overshoot or undershoot before reaching a stable level (Figure 15). This instability is called hysteresis and may be a problem in spectrophotometry and other applications.

Hysteresis is mainly caused by electrons being deviated from their planned trajectories and electrostatically charging the dynode support ceramics and glass bulb. When the applied voltage is changed as the light input changes, marked hysteresis can occur. As a countermeasure, many Hamamatsu side-on photomultiplier tubes employ "anti-hysteresis design" which virtually eliminate hysteresis.

Figure 15: Hysteresis Measurement



DRIFT AND LIFE CHARACTERISTIC

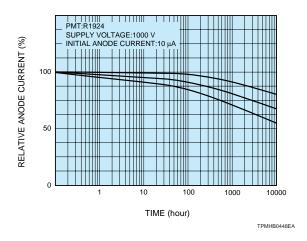
long period, anode output current of the photomultiplier tube may vary slightly with time, although operating conditions have not changed. This change is reffered to as drift or in the case where the operating time is 10³ to 10⁴ hrs it is called life characteristics. Figure 16 shows typical life characteristics.

Drift is primarily caused by damage to the last dynode by

While operating a photomultiplier tube continuously over a

Drift is primarily caused by damage to the last dynode by heavy electron bombardment. Therefore the use of lower anode current is desirable. When stability is of prime importance, the use of average anode current of 1 μA or less is recommended.

Figure 16: Examples of Life



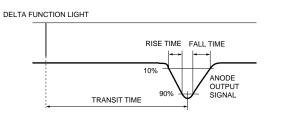
TIME RESPONSE

In the measurement of pulsed light, the anode output signal should reproduce a waveform faithful to the incident pulse waveform. This reproducibility is greatly affected by the electron transit time, anode pulse rise time, and electron transit time spread (TTS).

As illustrated in Figure 17, the electron transit time is the time interval between the arrival of a delta function light pulse (pulse width less than 50ns) at the photocathode and the instant when the anode output pulse reaches its peak amplitude. The anode pulse rise time is defined as the time required to rise from 10% to 90% of the peak amplitude when the whole photocathode is illuminated by a delta function light pulse (pulse width less than 50 ps). The electron transit time has a fluctuation between individual light pulses. This fluctuation is called transit time spread (TTS) and defined as the FWHM of the frequency distribution of electron transit times (Figure 18) at single photoelectron event. The TTS is an important factor in time-resolved measurement.

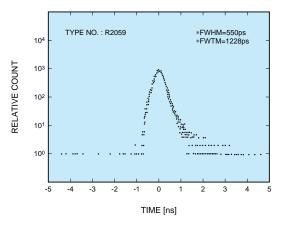
The time response characteristics depend on the dynode structure and applied voltage. In general, tubes of the linear-focused or circular-cage structure exhibit better time response than tubes of the box-and-grid or venetian blind structure. MCP-PMTs, which employ an MCP in place of conventional dynodes, offer better time response than tubes using other dynodes. For example, the TTS can be significantly improved compared to normal photomultiplier tubes because a nearly parallel electric field is applied between the photocathode, MCP and the anode. Figure 19 shows typical time response characteristics vs. applied voltage for types R2059 (51mm dia. head-on, 12-stage, linear-focused type).

Figure 17: Anode Pulse Rise Time and Electron Transit Time



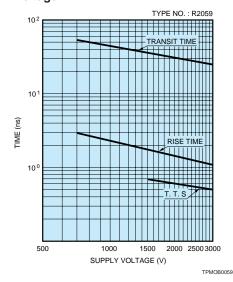
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Figure 18: Electron Transit Time Spread (TTS)



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Figure 19: Time Response Characteristics vs. Supply Voltage



VOLTAGE-DIVIDER CONSIDERATION

Interstage voltages for the dynodes of a photomultiplier tube are usually supplied by a voltage-divider circuits consisting of series-connected resistors. Schematic diagrams of typical voltage-divider circuits are illustrated in Figure 20. Circuit (a) is a basic arrangement (DC output) and (b) is for pulse operations. Figure 21 shows the relationship between the incident light level and the average anode output current of a photomultiplier tube using the voltage-divider circuit (a). Deviation from the ideal linearity occurs at a certain incident level (region B). This is caused by an increase in dynode voltage due to the redistribution of the voltage loss between the last few stages, resulting in an apparent increase in sensitivity. As the input light level is increased, the anode output current begins to saturate near the value of the current flowing through the voltage divider (region C). Therefore, it is recommended that the voltage-divider current be maintained at least at 20 times the average anode output current required from the photomultiplier tube.

Figure 20: Schematic Diagrams of Voltage-Divider Circuits (a) Basic arrangement for DC operation

(b) For pulse operation

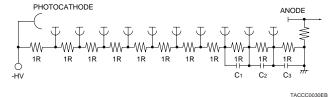
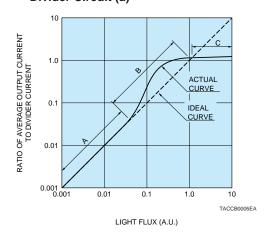


Figure 21: Output Characteristics of a PMT Using Voltage-Divider Circuit (a)



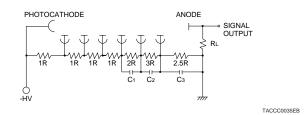
Generally high output current is required in pulsed light applications. In order to maintain dynode potentials at a constant value during pulse durations and obtain high peak currents, large capacitors are used as shown in Figure 20 (b). The capacitor values depend on the output charge. If linearity of better than 1% is needed, the capacitor value should be at least 100 times the output charge per pulse, as follows:

C>100
$$\frac{l \cdot t}{V}$$
 (farads)

where I is the peak output current in amperes, it is the pulse width in seconds, and V is the voltage across the capacitor in volts. In high energy physics applications where a high pulse output is required, as the incident light is increased while the interstage voltage is kept fixed, output saturation will occur at a certain level. This is caused by an increase in the electron density between the electrodes, causing space charge effects which disturb the electron current. As a corrective action to overcome space charge effects, the voltage applied to the last few stages, where the electron density becomes high, should be set at a higher value than the standard voltage distribution so that the voltage gradient between those electrodes is enhanced. For this purpose, a socalled tapered bleeder circuit (Figure 22) is often employed. Use of this tapered bleeder circuit improves pulse linearity 5 to 10 times better than that obtained with normal bleeder circuits (equally divided circuits).

Hamamatsu provides a variety of socket assemblies incorporating voltage-divider circuits. They are compact, rugged, lightweight and ensure the maximum performance for a photomultiplier tube by simple wiring.

Figure 22: Tapered Bleeder Circuit



GROUND POLARITY AND HA COATING

The general technique used for voltage-divider circuits is to ground the anode with a high negative voltage applied to the cathode, as shown in Figure 20. This scheme facilitates the connection of such circuits as ammeters or current-to-voltage conversion operational amplifiers to the photomultiplier tube. However, when a grounded anode configuration is used, bringing a grounded metallic holder or magnetic shield case near the bulb of the tube can cause electrons to strike the inner bulb wall, resulting in the generation of noise. Also, for head-on type photomultiplier tubes, if the faceplate or bulb near the photocathode is grounded, the slight conductivity of the glass material causes a current to flow between the photocathode (which has a high negative potential) and ground. This may cause significant deterioration of the photocathode. For this reason, when designing

the housing for a photomultiplier tube and when using an electrostatic or magnetic shield case, extreme care is required.

In addition, when using foam rubber or similar material to mount the tube in its housing, it is essential that material having sufficiently good insulation properties be used. This problem can be solved by applying a black conductive layer around the bulb and connecting to the cathode potential (called HA Coating), as shown in Figure 23.

As mentioned above, the HA coating can be effectively used to eliminate the effects of external potential on the side of the bulb. However, if a grounded object is located on the photocathode faceplate, there are no effective countermeasures. Glass scintillation, if it occurrs in the faceplate, has a larger influence on the noise. It also causes deterioration of the photocathode sensitivity and, once deteriorated, the sensitivity will never recover to the original level. To solve these problems, it is recommended that the photomultiplier tube be operated in the cathode ground scheme, as shown in Figure 24, with the anode at a positive high voltage. For example, in scintillation counting, since the grounded scintillator is directly coupled to the photomultiplier tube, it is recommended that the cathode be grounded, with a high positive voltage applied to the anode. Using this scheme, a coupling capacitor Cc is used to separate the high positive voltage applied to the anode from the signal, making it impossible to obtain a DC signal output.

Figure 23: HA Coating

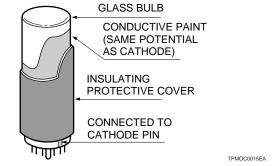
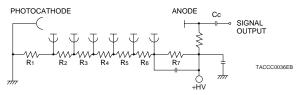


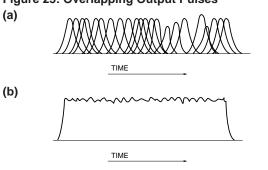
Figure 24: Cathode Ground Scheme



SINGLE PHOTON COUNTING

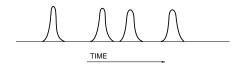
Photon counting is one effective way to use a photomultiplier tube for measuring very low light levels. It is widely used in astronomical photometry and chemiluminescence or bioluminescence measurement. In the usual application, a number of photons enter the photomultiplier tube and create an output pulse train like (a) in Figure 25. The actual output obtained by the measurement circuit is a DC current with a fluctuation as shown at (b).

Figure 25: Overlapping Output Pulses



When the light intensity becomes so low that the incident photons are separated as shown in Figure 26. This condition is called a single photon (or photoelectron) event. The number of output pulses is in direct proportion to the amount of incident light and this pulse counting method has advantages in S/N ratio and stability over the DC method averaging all the pulses. This pulse counting technique is known as the photon counting method.

Figure 26: Discrete Output Pulses (Single Photon Event)

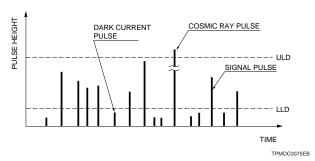


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Since the photomultiplier tube output contains a variety of noise pulses in addition to the signal pulses representing photoelectrons as shown in Figure 27, simply counting the pulses without some form of noise elimination will not result in an accurate measurement. The most effective approach to noise elimination is to investigate the height of the output pulses.

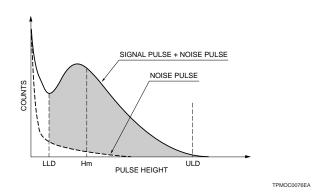
Figure 27: Output Pulse and Discrimination Level



A typical pulse height distribution (PHD) for the output of photomultiplier tubes is shown in Figure 28. In this PHD, the lower level discrimination (LLD) is set at the valley trough and the upper level discrimination (ULD) at the foot where the output pulses are very few. Most pulses smaller than the LLD are noise and pulses larger than the ULD result from cosmic rays, etc. Therefore, by counting pulses between the LLD and ULD, accurate light measurements becomes possible. In the PHD, Hm is the mean height of the pulses. It is recommended that the LLD be set at 1/3 of Hm and the ULD at triple Hm. In most cases, however, the ULD setting can be omitted.

Considering the above, a clear definition of the peak and valley in the PHD is a very significant characteristic for photomultiplier tubes for use in photon counting.

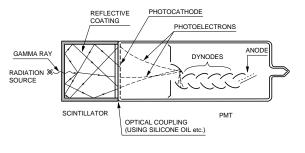
Figure 28: Typical Pulse Height Distribution



SCINTILLATION COUNTING

Scintillation counting is one of the most sensitive and effective methods for detecting radiation. It uses a photomultiplier tube coupled to a transparent crystal called scintillator which produces light by incidence of radiation.

Figure 29: Diagram of Scintillation Detector



In radiation measurements, there are two parameters that should be measured. One is the energy of individual particles and the other is the amount of particles. Radiation measurements should determine these two parameters.

When radiation enters the scintillator, it produce light flashes in response to each particle. The amount of flash is proportional to the energy of the incident racliation. The photomultiplier tube detects individual light flashes and provides the output pulses

which contain information on both the energy and amount of pulses, as shown in Figure 30. By analyzing these output pulses using a multichannel analyzer (MCA), a pulse height distribution (PHD) or energy spectrum is obtained, and the amount of incident particles at various energy levels can be measured accurately. Figure 31 shows typical PHDs or energy spectra when gamma rays (55Fe, 137Cs, 60Co) are detected by the combination of an NaI(TI) scintillator and a photomultiplier tube. For the PHD, it is very important to have distinct peaks at each energy level. This is evaluated as pulse height resolution (energy resolution) and is the most significant characteristic in radiation particle measurements. Figure 32 shows the definition of energy resolution taken with a 137Cs source.

Figure 30: Incident Particles and PMT Output

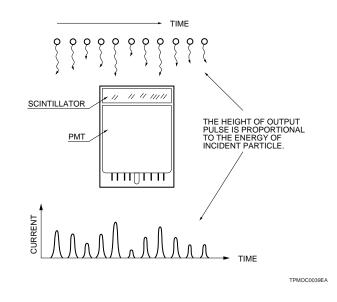
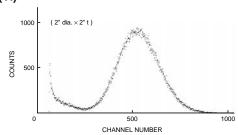
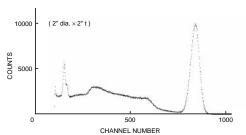


Figure 31: Typical Pulse Height Distributions (Energy Spectra) a) ⁵⁵Fe+Nal (TI)



b) ¹³⁷Cs+NaI (TI)



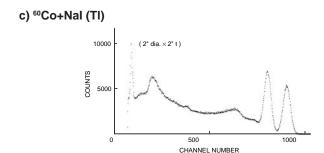


Figure 32: Definition of Energy Resolution

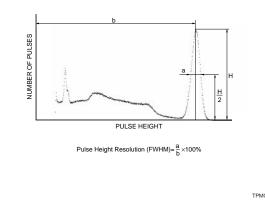
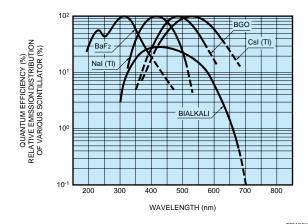


Figure 33: Spectral Response of PMT and Spectral Emission of Scintillators



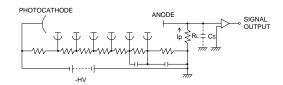
Pulse height resolution is mainly determined by the quantum efficiency of the photomultiplier tube in response to the scintillator emission. It is necessary to choose a tube whose spectral response matches with the scintillator emission. In the case of thallium-activated sodium iodide, or Nal(TI), which is the most popular scintillator, head-on type photomultiplier tube with a bialkali photocathode is widely used.

Connections to External Circuits

LOAD RESISTANCE

Since the output of a photomultiplier tube is a current signal and the type of external circuit to which photomultiplier tubes are usually connected has voltage inputs, a load resistance is used to perform a current-voltage transformation. This section describes considerations to be made when selecting this load resistance. Since for low output current levels, the photomultiplier tube may be assumed to act as virtually an ideal constant-current source, the load resistance can be made arbitrarily large, thus converting a low-level current output to a high-level voltage output. In practice, however, using very large values of load resistance creates the problems of deterioration of frequency response and output linearity described below.

Figure 34: PMT Output Circuit



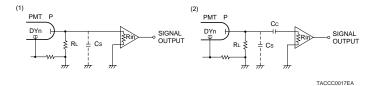
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If, in the circuit of Figure 34, we let the load resistance be RL and the total of the capacitance of the photomultiplier tube anode to all other electrodes, including such stray capacitance as wiring capacitances be C_s , the cutoff frequency f_c is expressed by the following relationship.

$$fc = \frac{1}{2\pi C_s \cdot R_L}$$

From this relationship, it can be seen that, even if the photomultiplier tube and amplifier have very fast response, response will be limited to the cutoff frequency $f_{\rm C}$ of the output circuit. If the load resistance is made large, at high current levels the voltage drop across RL becomes large, affecting a potential difference between the last dynode stage and the anode. As a result, a loss of output linearity (output current linearity with respect to incident light level) may occur.

Figure 35: Amplifier Internal Resistance



In Figure 35, let us consider the effect of the internal resistance of the amplifier. If the load resistance is RL and the input impedance of the amplifier is R_{in} , the combined parallel output resistance of the photomultiplier tube, R_{o} , is given by the following equation.

$$R_0 = \frac{RL \cdot R_{in}}{RL + R_{in}}$$

This value of R_0 , which is less than the value of R_L , is then the effective load resistance of the photomultiplier tube. If, for example, R_L = R_{in} , the effective load resistance is 1/2 that of R_L

alone. From this we see that the upper limit of the load resistance is actually the input resistance of the amplifier and that making the load resistance much greater than this value does not have significant effect. While the above description assumed the load and input impedances to be purely resistive, in practice, stray capacitances, input capacitance and stray inductances influence phase relationships. Therefore, as frequency is increased, these circuit elements must be considered as compound impedances rather than pure resistances.

From the above, three guides can be derived for use in selection of the load resistance:

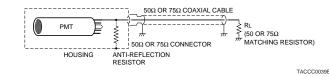
- In cases in which frequency response is important, the load resistance should be made as small as possible.
- 2) In cases in which output linearity is important, the load resistance should be chosen such that the output voltage is below several volts.
- 3) The load resistance should be less than the approximate input impedance of the external amplifier.

HIGH-SPEED OUTPUT CIRCUIT

For the detection of high-speed and pulsed light signals, a coaxial cable is used to make the connection between the photomultiplier tube and the electronic circuit, as shown in Figure 36. Since commonly used cables have characteristic impedances of 50Ω or 75Ω , this cable must be terminated in a pure resistance equivalent to the characteristic impedance to provide impedance matching and ensure distortion-free transmission for the signal waveform. If a matched transmission line is used, the impedance of the cable as seen by the photomultiplier tube output will be the characteristic impedance of the cable, regardless of the cable length, and no distortion will occur in signal waveforms. If proper matching at the signal receiving end is not achieved, the impedance seen at the photomultiplier tube output will be a function of both frequency and cable length, resulting in significant waveform distortion. Such mismatched conditions can be caused by the connectors used as well, so that the connector to be used should be chosen with regard given to the frequency range to be used, to provide a match to the coaxial cable.

When a mismatch at the signal receiving end occurs, all of the pulse energy from the photomultiplier tube is not dissipated at the receiving end, but is partially reflected back to the photomultiplier tube via the cable. While this reflected energy will be fully dissipated at the photomultiplier tube when an impedance match has been achieved at the tube, if this is not the case, because the photomultiplier tube itself acts as an open circuit, the energy will be reflected and, thus returned to the signal-receiving end. Since part of the pulse makes a round trip in the coaxial cable and is again input to the receiving end, this reflected signal is delayed with respect to the main pulse and results in waveform distortion (so called ringing phenomenon). To prevent this phenomenon, in addition to providing impedance matching at the receiving end, it is necessary to provide a resistance matched to the cable impedance at the photomultiplier tube end as well. If this is done, it is possible to virtually eliminate the ringing caused by an impedance mismatch, although the output pulse height of the photomultiplier tube is reduced to one-half of the normal level by use of this impedance matching resistor.

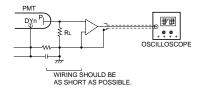
Figure 36: Typical Connections Used to Prevent Ringing



Next, let us consider waveform observation of high-speed pulses using an oscilloscope (Figure 37). This type of operation requires a low load resistance. Since, however, there is a limit to the oscilloscope sensitivity, an amplifier may be required.

For cables to which a matching resistor has been connected, there is an advantage that the cable length does not affect the characteristics of the cable. However, since the matching resistance is very low compared to the usual load resistance, the output voltage becomes too small. While this situation can be remedied with an amplifier of high gain, the inherent noise of such an amplifier can itself be detrimental to measurement performance. In such cases, the photomultiplier tube can be brought as close as possible to the amplifier and a load resistance as large as possible should be used (consistent with preservation of frequency response), to achieve the desired input voltage.

Figure 37: With Ringing Suppression Measures



TACCC0026

It is relatively simple to implement a high-speed amplifier using a wide-band video amplifier or operational amplifier. However, in exchange of design convenience, use of these ICs tends to create problems related to performance (such as noise). It is therefore necessary to know their performance limit and take corrective action.

As the pulse repetition frequency increases, baseline shift creates one reason for concern. This occurs because the DC signal component has been eliminated from the signal circuit by coupling with a capacitor which does not pass DC components. If this occurs, the reference zero level observed at the last dynode stage is not the actual zero level. Instead, the apparent zero level is the time-average of the positive and negative fluctuations of the signal waveform. This will vary as a function of the pulse density, and is known as baseline shift. Since the height of the pulses above this baseline level is influenced by the repetition frequency, this phenomenon is of concern when observing waveforms or discriminating pulse levels.

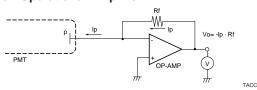
OPERATIONAL AMPLIFIERS

In cases in which a high-sensitivity ammeter is not available, the use of an operational amplifier will enable measurements to be made using an inexpensive voltmeter. This technique relies on converting the output current of the photomultiplier tube to a voltage signal. The basic circuit is as shown in Figure 38, for which the output voltage, Vo, is given by the following relationship.

$$V_0 = -Rf \cdot Ip$$

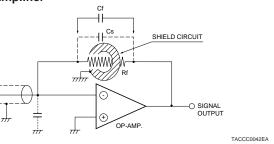
This relationship is derived for the following reason. If the input impedance of the operational amplifier is extremely large, and the output current of the photomultiplier tube is allowed to flow into the input terminal of the amplifier, most of the current will flow through $R_{\rm f}$ and subsequently to the operational amplifier output circuit. Therefore, the output voltage $V_{\rm o}$ is given by the expression -Rf \times Ip. When using such an operational amplifier, it is of course, not possible to increase the output voltage without limit, the actual maximum output being approximately equal to the operational amplifier power supply voltage. At the other end of the scale, for extremely small currents, limitations are placed by the operational amplifier offset current (los), the quality of $R_{\rm f}$, and other factors such as the insulation materials used.

Figure 38: Current-Voltage Transformation Using an Operational Amplifier



If the operational amplifier has an offset current (los), the above-described output voltage becomes Vo = -Rf (Ip + Ios), the offset current component being superimposed on the output. Furthermore, the magnitude of temperature drift may create a problem. In general, a metallic film resistor which has a low temperature coefficient is used for the resistance Rf, and for high resistance values, a vacuum-sealed type is used. Carbon resistors, with their highly temperature-dependent resistance characteristics, are not suitable for this application. When measuring such extremely low level currents as 100 pA and below, in addition to the considerations described above, the materials used in the circuit implementation require care as well. For example, materials such as bakelite are not suitable, and more suitable materials are Teflon, polystyrol or steatite. In addition, low-noise cables should be used, since general-purpose coaxial cables exhibit noise due to mechanical changes. In the measurement of these low level currents, use of an FET input operational amplifier is recommended.

Figure 39: Frequency Compensation of an Operational Amplifier



In Figure 39, if a capacitance Cf (including any stray capacitance) exists in parallel to the resistance Rf, the circuit exhibits a time constant of (Rf \times Cf), so that response speed is limited to this time constant. This is a particular problem if Rf is large. Stray capacitance can be reduced by passing Rf through a hole in a shield plate. When using coaxial signal input cables, since the cable capacitance Cc and Rf are in the feedback loop, oscillations may occur and noise may be amplified. While the method of avoiding this is to connect Cf in parallel to Rf, to reduce gain at high frequencies, as described above, this creates a time constant of Rf \times Cf which limits the response speed.

Selection Guide by Application

Applications	Required Major Characteristics	Applicable PMT
Spectroscopy		
Equipment Utilizing Absorption		
When light passes through a substance, the light energy causes changes in the electron energy of the substance, resulting in partial energy loss. This is called absorption and gives analytical data. In order to determine the amount of the sample substance, it is irradiated while the light wavelength is scanned continuously. The spectral intensities of the light before and after passing through the sample are detected by a photomultiplier tube to measure the amount of absorption.	1) Wide spectral response 2) High stability 3) Low dark current 4) High quantum efficiency 5) Low hysteresis	R6356, R6357 R928, R955, R1477, R3896 R1463 R374, R376
Atomic Absorption Spectrophotometer This is widely used in the analysis of minute quantities of metallic elements. For each element to be analyzed, a special elementary hollow cathode lamp is used to irradiate a sample which is burned for atomization. A photomultiplier tube detects the light passing through the sample to measure the amount of absorption, which is compared with a reference sample measured in advance.	Good polarization characteristic	R928 R955
Equipment Utilizing Emission		
Photoelectric Emission Spectrophotometer When an external energy is applied to a sample, light emission occurs from the sample. By dispersing this emission using a monochromator, into characteristic spectral lines of elements and measuring their presence and intensity simultaneously with photomultiplier tubes, this equipment enables rapid qualitative and quantitative analysis of the elements contained in the sample.	1) High sensitivity	R6350, R6351, R6352 R6354, R6355, R6356, R7311 1P28, R106, R166, R212, R4220 R759, R760
Fluorescence Spectrophotometer The fluorescence spectrophotometer is used in biological science, particularly in molecular biology. When an excitation light is applied, some substances emit light with a wavelength longer than that of the excitation light. This light is known as fluorescence. The intensity and spectral characteristics of the fluorescence are measured by a photomultiplier tube, and the substance is analyzed qualitatively and quantitatively.	1) High sensitivity 2) Low dark current 3) High stability	R6353, R6358 R3788, R4220, R1527 R928
Raman Spectrophotometer When monochromatic light strikes a substance and scatters, Raman scattering also occurs at a different wavelength from the excitation light. Since the wavelength difference is a characteristic of the molecules, the spectral measurement of Raman scattering provides qualitative and quantitative data of the molecules. Raman scattering is extremely weak and a sophisticated optical system is used for measurement, thus the photomultiplier tube is operated in the photon counting mode.	High quantum efficiency Low dark current Single photon discrimination ability	R2949 R1463P, R649 R943-02
Others • Liquid or Gas Chromatography • X-Ray Diffractometer, X-Ray Fluorescence Analyzer • Electron Microscope		R3788 R647-01, R1166, R6095, R580 R647

Applications	Required Major Characteristics	Applicable PMT
Mass Spectroscopy and Solid Surface A	nalysis	
Solid Surface Analysis The composition and structure of a solid surface can be studied by irradiating a narrow beam of electrons, ions, light or X-rays onto the surface and measuring the secondary electrons, ions or X-rays that are produced. With the progress of the semiconductor industry, this kind of technology becomes essential in evaluating semiconductors, including defects, surface analysis, adhesion, and density profile. Electrons, ions, and X-rays are measured with electron multipliers and MCPs.	1) High environmental resistance 2) High stability 3) High current amplification 4) Low dark current	R474, R515, R596, R595 R2362, R5150
Environment Monitoring		
Dust Counter A dust counter measures the density of dust or particles floating in the atmosphere or inside rooms. It makes use of light scattering or absorption of beta-rays by particles.	Low dark noise Low spike noise High quantum efficiency	R6350 R105, R3788 R647-01
Turbidimeter When floating particles are contained in a liquid, light incident on the liquid is absorbed, scattered or refracted by these particles. It looks cloudy or hazy to the human eye. A turbidimeter is a device that numerically measures the turbidity by using light transmission and scattering.	Low dark current Low spike noise High quantum efficiency	R6350 R105 R1924
Others • NOx meters, SOx meters	High quantum efficiency at wavelength of interest Low dark current Good temperature characteristic High stability	NOx= R928 R374, R2228, R5959 R5070 SOx= R6095, R3788, R1527 R2693
Biotechnology		
Cell Sorter The cell sorter is an instrument that selects and collects only specific cells using a fluorescent substance for labeling. The labeled cells are irradiated by laser beam, and a photomultiplier tube is used to detect the resulting fluorescence or scattering.	High quantum efficiency High stability Low dark current	R6353, R6357, R6358 R928, R1477, R3788, R3896
Fluorometer While the ultimate purpose of the cell sorter is to separate cells, the fluorometer is used to analyze cells and chemical substances by measuring the fluorescence or scattered light from a cell or chromosome with regard to such factors as fluorescence spectrum, fluorescence quantum efficiency, fluorescence anisotropy (polarization) and fluorescence lifetime.	4) High current amplification 5) Good polarization characteristic	R2368

Applicat	ions	Required Major Characteristics	Applicable PMT
Medical Applications			
Gamma Camera The gamma camera takes an ideled reagent injected into the abnormalities. This equipmen scanner and has been gradual section uses a large diameter Noguide coupled to an array of ph	body of a patient to locate t starts from a scintillation illy improved. Its detection val(TI) scintillator and light-	High energy resolution Good uniformity High stability Uniform current amplification	R6231-01 R6234-01 R6235-01 R6236-01 R1307-01 R6233-01 R6237-01
Positron CT The positron CT provides tomogonic coincident gamma-ray emission of a positron emitted from 15O, 13N, 18F, etc.) injected into tubes coupled to scintillators gamma-rays.	n accompanying annihila- a tracer radioisotope (¹¹C, the body. Photomultiplier	1) High energy resolution 2) High stability 3) High speed response 4) Compact size	R1635, R5900U-00-C8 R1450 R5800 R1548 R6427
Liquid Scintillation Counter Liquid scintillation counters are age measurement and bioche containing radioisotopes is diss ing an organic scintillator, and i tween a pair of photomultiplier t neously detect the emission of	used for tracer analysis in emical research. A sample solved in a solution contain- t is placed in the center be- ubes. These tubes simulta-	 High quantum efficiency Low noise of thermionic emission Less glass scintillation at the faceplate and bulb Fast response time High pulse linearity 	R331, R331-05
In-Vitro Assay In-vitro assay is used for physical checkups, diagnosis, and evaluation of drug po-	Radioimmunoassay (RIA) Uses radioactive isotopes for labeling.		R647 R1166, R5611-01 R1924
tency by making use of specificity of the antigen/antibody reaction characteristics of tiny amounts of insulin, hormones, drugs and viruses which are contained in blood or urine. Photomultiplier tubes are used to measure optically the amount of antigens labeled by radioisotopes, enzymes, fluorescent chemiluminescent or bioluminescent substances.	Enzymeimmunoassay (EIA) Uses enzymes for labeling and measures resulting chemiluminescence or bioluminescence. Fluoroimmunoassay/ chemiluminescent imunoassay Uses fluorescent or chemiluminescent substances for labeling.	1) High quantum efficiency 2) High stability 3) Low dark current	R6350, R6352, R6353 R6356, R6357 R4220, R928, R3788 R647, R1463 R1925 R6095, R374
Others • X-ray phototimer In X-ray examination, this equip the exposure to an X-ray filr through a subject is converted phor screen. A photomultiplier light and provide an electrical lated electrical signal reaches a tion is shut off, making it possib density.	n. The X-ray transmitting into visible light by a phostube is used to detect this signal. When the accumula preset level, X-ray irradia-	High sensitivity Low dark current High stability	R6350 931A, R105

Applications	Required Major Characteristics	Applicable PMT
Radiation Measurement		
Area Monitor The area monitor is designed to continuously measure a change in environmental radiation levels. It uses a photomutiplier tube coupled to a scintillator, to monitor low-level alpha ray or gamma ray.	Long term stability Low background noise Good plateau characteristic	R1306, R6231 R329-02, R4607-01 R1307, R6233 R877, R877-01
Survey Meter The survey meter measures low-level gamma ray or beta ray using a photomultipliter tube coupled to a scintillator.	Long term stability Low background noise Good plateau characteristic	R1635 R647 R1924 R6095
Resource Inquiry		
Oil Well Logging Oil well logging is used to locate an oil deposit and determine its size. A probe containing a radiation source and a scintillator/photomultiplier tube is lowered into an oil well as it is being drilled. The scattered radiation or natural radiation from the geological formation are detected and analyzed, to determine the type and density of the rock that surrounds the well.	Stable operation at high temperature up to 175 Rugged structure Good plateau characteristic	R4177-01, R1281 R3991 R1288, R1288-01
Industrial Measurement		
Thickness Meter Using a radiation source and a scintillator/photomultiplier tube, a product thickness can be measured on factory production lines for paper, plastic, steel sheet, etc. Beta-rays are used as a radiation source in measurement of products with a small density, such as rubber, plastic, and paper. Gamma-rays are used for products with a large density, like steel sheet. (X-ray fluorescence spectrometers are used in measurement of film thickness for plating, evaporation, etc.)	Wide dynamic range High energy resolution	R647-01, R5800 R6095 R580 R1306, R6231 R329-02
Semiconductor Inspection System This is widely used for semiconductor wafer inspection and pattern recognition such as semiconductor mask alignment. For wafer inspection, the wafer is scanned by a laser beam, and scattered light caused by dirt or defects is detected by a photomultiplier tube.	High quantum efficiency at wavelength of interest Good uniformity Low spike noise	R928, R1477, R3896 R647, R1463
Photography and Printing		
Color Scanner To prepare color pictures and photographs for printing, the color scanner is used to separate the original colors into the three primary colors (RGB) and black. It uses photomultiplier tubes combined with RGB filters, and provides color separation as image data.	 High quantum efficiency at wavelengthes of RGB Low dark noise Fast fall time High stability Good repeatability with change in input signal 	R3788 R3810, R3811 R647, R1463 R1924, R1925

Applications	Required Major Characteristics	Applicable PMT
ligh Energy Physics Collision Experiment		
Hodoscope Photomuliplier tuubes are coupled to the ends of long, thin plastic scintillators arranged orthogonally in two layers. They measure the time and position at which charged particles pass through the scintillators.	N =	R1635 (H3164-10) R647-01 (H3165-10) R1450 (H6524) R1166 (H6520)
TOF Counter TOF counters consisting of plastic scintillators and photomultiplier tubes are arranged along paths of secondary particles which are generated by collision reactions. Velosities of these particles are measured by time differences between collision time and detection times.	Fast time response Compact size Immunity to magnetic fields	R5800 R1635 (H3164-10) R1450 (H6524) R4998 (H6533), R5505 (H6152-01) R1828-01 (H1949-51), R2083 (H2431-50) R5924 (H6614-01)
Cherenkov Counter A Cherenkov counter identifies secondary particles which generated by collision reactions. Cherenkov lights emitted from a charged particle which has energy more than a constant level and goes through a radiator like gas or silicon aerogel are detected. A velocity of a charged particle is mesured by an angle of its cherenkov lights.	1) High Quantum efficiency 2) Good single photon defectivity 3) High current amplification 4) Fast time response 5) Immunity to magnetic fields	R2256-02 (H6521) R5113-02 (H6522) R2059 (H3177-51) R1584 (H6528) R5924 (R6614-01)
Calorimeter The calorimeter measures the accurate direction and energy of secondary particles emitted from the collision reaction of electrons and positrons.	High pulse linearity High energy resolution High stability Immunity to magnetic fields	R580 (H3178-51) R329-02 (H6410) R5924 (H6614-01) R6091 (H6559)
— Neutrino and Proton Decay Experiment, Cosmic	Ray Detection ——	
Neutrino Experiment A research of solar neutrinos or particle astrophysics is performed in a neutrino experiment. Its observation system consists of a large size radiator surrounded by a number of large-diameter photomultiplier tubes. Cherenkov light which occurs from interactions of neutrinos or other particles and a radiator are detected. The directions and energies of the particles are measured.		R5912
Neutrino and Proton Decay Experiment In the neutrino and proton decay experiment which is performed at KAMIOKA in Japan, 11200 of 20" dimeter photomultiplier tubes are set covering all directions of a huge tank storing around 50000t of pure water. Cherenkov light emitted by solar neutrino or proton decay are measured.	1) Large photocathode area 2) Fast Time Response 3) High stability 4) Low dark count	R3600-02 (R3600-06)
Air Shower Counter When cosmic rays collide with the earth's atmosphere, secondary particles are created by the interaction of the cosmic rays and atmospheric atoms. These secondary particles generate more secondary particles, which continue to increase in a geometrical progression. This is called an air shower. The gamma rays and Cherenkov light emitted in this air shower is detected by photomultiplier tubes lined up in a lattice array on the ground.		R1166 (H6520) R580 (H3178-51) R329-02 (H6410) R1828-01 (H1949-51) R6091 (H6559) R1250 (H6527)

The assembly type is given in parentheses.

Applications	Required Major Characteristics	Applicable PMT
erospace		
Measurement of X-rays from Outer Space X-rays from outer space include information on the enigmas of space. As an example, the X-ray observation satellite "Asuka", developed by a group of the ISAS (Institute of Space and Astronomical Science - Japan), uses a gas-scintillation proportional counter coupled to a position-sensitive photomultiplier tube, to measure X-rays from supernovas, etc.	High energy resolution Rugged structure	R2486
Measurement of Scattered Light from Fixed Stars and Interstellar Dust Ultraviolet rays from space contain a lot of information about the surface temperature of the stars and interstellar substances. However, these ultraviolet rays are absorbed by the earth's atmosphere, so it is impossible to measure them from the earth surface. Photomultiplier tubes are mounted in rockets or artificial satellites, to measure ultraviolet rays with wavelengthes shorter than 300nm.	1) Rugged structure 2) Sensitivity in VUV to UV range (solar blind response: see page 4 for Cs-Te, Cs-I photocathodes)	R1080, R976 R6834, R6835, R6836
asers		
Laser Radar		D290011 Corios D504611 Corio
The laser radar is used in such applications as atmospheric measurement which uses a highly-accurate range finding or aerosol scattering.	Fast response time	R3234-01, R3237-01
measurement which uses a highly-accurate range finding or	Fast response time Low dark count High current amplification	R3809U Series, R5916U Serie R3234-01, R3237-01 R3809U Series, R5916U Serie
measurement which uses a highly-accurate range finding or aerosol scattering. Fluorescence Lifetime Measurement The laser is used as an excitation light for fluorescence lifetime measurement. The molecular structure of a substance can be studied by measuring temporal intensity changes in	2) Low dark count	R3234-01, R3237-01

22 23

the purpose of impurity and ion control.

Side On Type Photomultiplier Tubes

(at 25°C)

R6358

(Unit: mm)

A		Spe	ctral Respo	nse	0	D	•	•	©	Maximum	Ratings	Cathode S	Sensitivity
		₿		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	Range	10/	0	Window Material	line	No. of	Socket	Cathode Voltage	0	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
42 //	1/2"\ Dia Tymas												

13mm (1/2'	') Dia. ˈ	Types
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	(., _ ,)												
R6350	For UV to visible range, general purpose	350U (S-5)	185 to 650	340	Sb-Cs	U	0	CC/9	E678-11U*/1	1250	0.01	20	40
R6351	Synthetic silica window type of R6350	350S	160 to 650	340	Sb-Cs	Q	2	CC/9	E678-11U*/	1250	0.01	20	40
R6352	High sensitivity variant of R6350	452U	185 to 750	420	ВА	U	0	CC/9	E678-11U*/	1250	0.01	80	120
R6353	Low dark current bialkali photo- cathode	456U	185 to 680	400	LBA	U	0	CC/9	E678-11U*/	1250	0.01	30	70
R6355	For UV to near IR range, general purpose	550U	185 to 850	530	MA	U	0	CC/9	E678-11U*/1	1250	0.01	80	150
R6356	High sensitivity variant of R6355	560U	185 to 900	600	MA	U	0	CC/9	E678-11U*/	1250	0.01	140	250
R6357	High sensitivity variant of R6356, Meshless type	_	185 to 900	450	MA	U	3	CC/9	E678-11U*/	1250	0.01	350	500
R6358	Low dark current multialkali photo- cathode	561U	185 to 830	530	MA	U	0	CC/9	E678-11U*/	1250	0.01	140	200

13mm (1/2") Dia Subminiaturo Typos

PHOTO-CATHODE

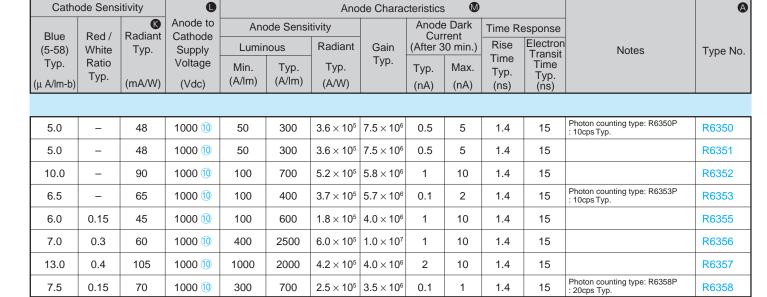
13111111 (1/2) Dia. Subinii	liatur	e rypes	>									
R3810	For UV to visible range, general purpose	350U (S-5)	185 to 830	340	Sb-Cs	U	4	CC/9	E678-11U*/1	1250	0.01	20	40
R3811	Multialkali photocathode variant of R3810	550U	185 to 830	530	MA	U	4	CC/9	E678-11U*/1	1250	0.01	50	150

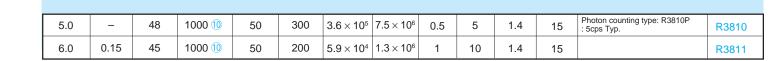
 ϕ 13.5 \pm 0.8

4 MIN.

UV WINDOW

DIRECTION OF LIGHT





 ϕ 13.5 \pm 0.8

4 MIN.

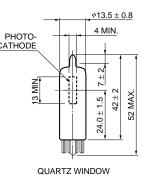
UV WINDOW

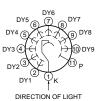
 $2.5 \times 10^5 \ | \ 3.5 \times 10^6 \ | \ 0.1$

1 R6350, R6352, R6353 etc.











0.15

7.5

3 R6357

70

1000 10

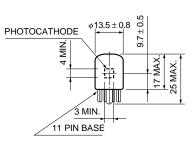
300

РНОТО-

4 R3810, R3811



1.4



Side On Type Photomultiplier Tubes

Transmission-mode bialkali photocathode 430U 185 to 650 375

A		Spe	ctral Respo	nse	0	0	(3	•	G	Maximum	Ratings	Cathode S	Sensitivity
		₿		Peak	Photo-	\	Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve	Range	Wave- length	cathode Material	Window Material		No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
28mm (1-1/8") Dia. Types	with	UV to	Visib	le Sei	nsitivi	ty						
931A	For visible range, general purpose	350K (S-4)	300 to 650	400	Sb-Cs	К	1	CC/9	E678-11A 1/2 3	1250	0.1	25	40
931B	Bialkali photocathode, high stability	453K	300 to 650	400	ВА	К	1	CC/9	E678-11A 1/2 3	1250	0.1	30	60
1P21	Low dark current variant of R105	350K			Sb-Cs	К	1	CC/9	E678-11A 1/2 3	1250	0.1	25	40
R105	High gain and low dark current variant of 931A	(S-4)	300 to 650	400	Sb-Cs	K	1	CC/9	E678-11A 1/2 3	1250	0.1	25	40
1P28	For UV to visible range, general purpose	350U	405 to 050	0.40	Sb-Cs	U	1	CC/9	E678-11A 1/23	1250	0.1	25	40
R212	High gain and low dark current variant of 1P28	(S-5)	185 to 650	340	Sb-Cs	U	0	CC/9	E678-11A 1/2 3	1250	0.1	25	40
R1527	Low dark current bialkali photocath- ode	456U	185 to 680	400	LBA	U	1	CC/9	E678-11A 1/2 3	1250	0.1	40	60
R4220	High sensitivity variant of R1527	456U	185 to 710	410	LBA	U	1	CC/9	E678-11A 1/2 3	1250	0.1	80	100
R106	Variant of R212 with synthetic silica window	350S (S-19)	160 to 650	340	Sb-Cs	Q	1	CC/9	E678-11A 1/23	1250	0.1	25	50
R3788	High sensitivity variant of R212	452U	185 to 750	420	ВА	U	1	CC/9	E678-11A 1/2 3	1250	0.1	100	120

CC/9 E678-11A / 2 3

931A, 931B, 1P28, R3788, etc.

PHOTOCATHODE

TPMS

(at 25°C)

Catho	de Sens	itivity	•			And	de Chara	cteristics	; Ø				
Blue (5-58)	Red / White	Radiant Typ.	Anode to Cathode Supply	And Lumir	ode Sensi nous	tivity Radiant	Gain		e Dark rent 80 min.)	Rise	esponse Electron Transit	Notes	Type N
Typ. μ A/lm-b)	Ratio Typ.	(mA/W)	Voltage (Vdc)	Min. (A/lm)	Typ. (A/lm)	Typ. (A/W)	Тур.	Typ.	Max. (nA)	Time Typ. (ns)	Time Typ. (ns)		1,70011
5.0	-	48	1000 10	50	400	4.8 × 10 ⁵	1.0 × 10 ⁷	5	50	2.2	22		931A
7.1	-	60	1000 10	50	600	6.6 × 10 ⁵	1.0 × 10 ⁷	5	50	2.2	22	UV glass window type: R1516	931B
5.0	-	48	1000 10	50	250	3.0 × 10 ⁵	6.25×10^{6}	1	5	2.2	22		1P21
5.0	-	48	1000 10	50	400	4.8 × 10 ⁵	1.0 × 10 ⁷	1	10	2.2	22	High gain type: R105UH	R105
5.0	-	48	1000 10	20	400	4.8 × 10 ⁵	1.0 × 10 ⁷	5	50	2.2	22		1P28
5.0	-	48	1000 10	50	300	3.6 × 10 ⁵	7.5 × 10 ⁶	1	10	2.2	22	High gain type: R212UH	R212
6.4	-	60	1000 10	200	400	4.0 × 10 ⁵	6.7 × 10 ⁶	0.1	2	2.2	22	Photon counting type: R1527P : 10cps Typ.	R1527
8.0	-	70	1000 10	1000	1200	8.4 × 10 ⁵	1.2 × 10 ⁷	0.2	2	2.2	22	Photon counting type: R4220P : 10cps Typ.	R4220
6.5	_	48	1000 10	100	400	3.6 × 10 ⁵	8.0 × 10 ⁶	1	10	2.2	22	High gain type: R106UH	R106
10.0	0.01	90	1000 10	500	1200	9.0 × 10 ⁵	1.0 × 10 ⁷	5	50	2.2	22	Synthetic silica window type : R4332	R3788
7.0	_	62	1000 10	100	300	3.7 × 10 ⁵	6.0 × 10 ⁶	0.5	5	1.2	18	Photon counting type: R2693P : 15cps Typ.	R2693

Side On Type Photomultiplier Tubes

A		Spe	ctral Respo	nse	0	Ð	•	•		Maximum	Ratings	Cathode S	Sensitivity
		B		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	3	Wave-	cathode Material	Material	line No.	No. of	Socket	Cathode	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)

28mm (1-1/8") Dia. Types with UV to Near IR Sensitivity

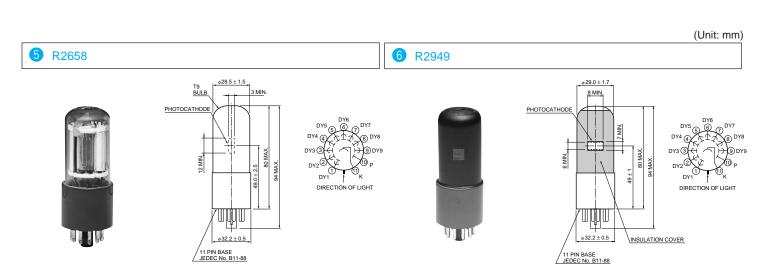
R2368	Transmission-mode multialkali photocathode	500U	185 to 850	420	MA	U	0	CC/9	E678-11A 1/2 3	1250	0.1	80	150
R928	For UV to near IR range, high sensitivity	562U	185 to 900	400	MA	U	3	CC/9	E678-11A 1/2 3	1250	0.1	140	250
R2949	For UV to near IR range, low dark count	552U	185 to 900	400	MA	U	6	CC/9	E678-11A 1/2 3	1250	0.1	140	200
R1477-06	High sensitivity variant of R928	554U	185 to 900	450	MA	U	3	CC/9	E678-11A 1/2 3	1250	0.1	350	375
R3896	High sensitivity variant of R1477-06	555U	185 to 900	450	MA	U	3	CC/9	E678-11A 1/2 3	1250	0.1	475	525
R4632	High sensitivity in 400 to 700nm range, low dark count	556U	185 to 850	430	MA	U	3	CC/9	E678-11A 1/2 3	1250	0.1	140	200
R636-10	GaAs photocathode, high quantum efficiency	650U	185 to 930	300 to 800	GaAs(Cs)	U	4	CC/9	E678-11A 1/2 3	1500	0.001	400	550
R2658	InGaAs photocathode, for UV to 1010nm range	850U	185 to 1010	400	InGaAs (Cs)	U	5	CC/9	E678-11A 1/2 3	1500	0.001	50	100
R5108	For near IR range	700K (S-1)	400 to 1200	800	Ag-O-Cs	K	2	CC/9	E678-11A 1/23	1500	0.1	10	25





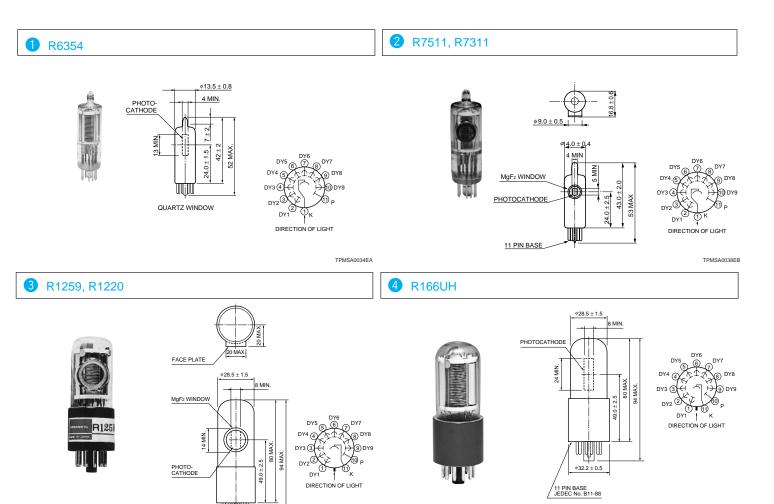
(at 25°C)

Catho	de Sens	itivity	•			Ano	de Chara	cteristics	M				A
Blue	Red /	Radiant	Anode to Cathode	And	de Sensi	tivity		Anode Cur		Time R	esponse		
(5-58)	White	Тур.	Supply	Lumir	ious	Radiant	Gain		0 min.)	Rise	Electron	Notes	Type No.
Тур.	Ratio Typ.		Voltage	Min.	Тур.	Тур.	Тур.	Тур.	Max.	Time Typ.	Time Typ.		
(μ A/lm-b)	тур.	(mA/W)	(Vdc)	(A/lm)	(A/lm)	(A/W)		(nA)	(nA)	(ns)	(ns)		
_	0.15	64	1000 10	50	200	8.3 × 10 ⁴	1.3 × 10 ⁶	5	50	1.2	18		R2368
8.0	0.3	74	1000 10	400	2500	7.4 × 10 ⁵	1.0 × 10 ⁷	3	50	2.2	22	Synthetic silica window type: R955	R928
7.5	0.3	68	1000 10	1000	2000	6.8 × 10 ⁵	1.0 × 10 ⁷	300 [®]	500 [®]	2.2	22		R2949
10.0	0.35	80	1000 10	1000	2000	4.2 × 10 ⁵	5.3 × 10 ⁶	3	50	2.2	22		R1477-06
15.0	0.4	90	1000 10	3000	5000	8.6 × 10 ⁵	9.5 × 10 ⁶	10	50	2.2	22		R3896
7.5	0.15	80	1000 10	300	700	2.8 × 10 ⁵	3.5 × 10 ⁶	50 [®]	100 [®]	2.2	22		R4632
9.0	0.53	62	1250 10	100	250	2.8 × 10 ⁴	4.5 × 10 ⁵	0.1 [®]	2 ^(f)	2.0	20	Synthetic silica window type : R758-10	R636-10
4.5	0.4	1 (at 1μ m)	1250 10	5	16	1.6 × 10 ²	1.6 × 10 ⁵	1	10	2.0	20	Photon counting type: R2658P	R2658
_	_	2.2	1250 10	3.5	7.5	6.6 × 10 ³	3.0 × 10 ⁵	350 [®]	1000 [®]	1.2	18		R5108



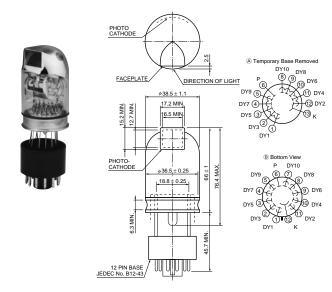
Side-On and Dormer Window Type Photomultiplier Tubes

A		Spe	ectral Respo	nse	0	0	•	•	G	Maximum	Ratings	Cathode	Sensitivity
		B Curve		Peak	Photo-	Window	Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Code	Range	Wave- length	cathode Material	Material		No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
13mm ((1/2") Dia. Compa	ct Ty	pes wit	h So	lar Bli	nd Re	sp	onse					
R7511	For VUV range, MgF2 window	150M	115 to 195	130	Cs-I	MF	2	CC/9	E678-11U	1250	0.01	-	_
R6354	For UV range	250S	160 to 320	200	Cs-Te	Q	1	CC/9	E678-11U*/1	1250	0.01	-	_
R7311	For UV range, MgF2 window	250M	115 to 320	200	Cs-Te	MF	2	CC/9	E678-11U	1250	0.01	_	_
28m1-1	/8") Dia. Types wi	ith So	olar Blir	nd Re	spon	se							
R1259	For VUV range, MgF2 window	150M	115 to 195	120	Cs-I	MF	3	CC/9	E678-11A■	1250	0.1	_	_
R166UH	For UV range	250S	160 to 320	200	Cs-Te	Q	4	CC/9	E678-11A 1/23	1250	0.1	_	-
R1220	For UV range, MgF ₂ window	250M	115 to 320	200	Cs-Te	MF	3	CC/9	E678-11A■	1250	0.1	_	-
38mm ((1-1/2") Dia. Dorm	er W	indow	Гуре	S								
R1923	Multialkali photocathode, temporary base	558K	300 to 800	530	MA	К	6	CC/10	E678-12A■	2000	0.1	200	300



(at 25°C) Anode Characteristics Anode to (3) Anode Dark Time Response Anode Sensitivity Current (After 30 min.) Radiant Cathode Red / Electron Transit Time Radiant Gain (5-58)White Тур. Supply Notes Type No. Time Тур. Ratio Voltage Min. Тур. Тур. Тур. Max. Тур. Typ. Тур. (A/lm) (A/lm) (mA/W) (Vdc) (A/W) μ A/lm-b) (nA) (nA) (ns) 1000 10 $5.2 \times 10^{48} \ 2.0 \times 10^{6} \ 0.3$ 1.4 R7511* 1000 10 1.4 15 1.5×10^{5} 2.5×10^{6} R6354 40⁶ 1000 10 2.8×10^{5} 7.0×10^{6} 1.4 R7311* 1000 10 $3.1 \times 10^{48} \, 1.2 \times 10^{6}$ R1259 26^a 10 Direct replacement for Burle 4526. R166UH 40^b 1000 10 4.0×10^{5} 1.0×10^{7} 10 2.2 22 40^b 1000 10 4.0×10^{5} 1.0×10^{7} 10 2.2 22 R1220 0.12 89 1250 16 5 $4.4 \times 10^3 | 5.0 \times 10^4 |$ 10 2.2 22 R1923

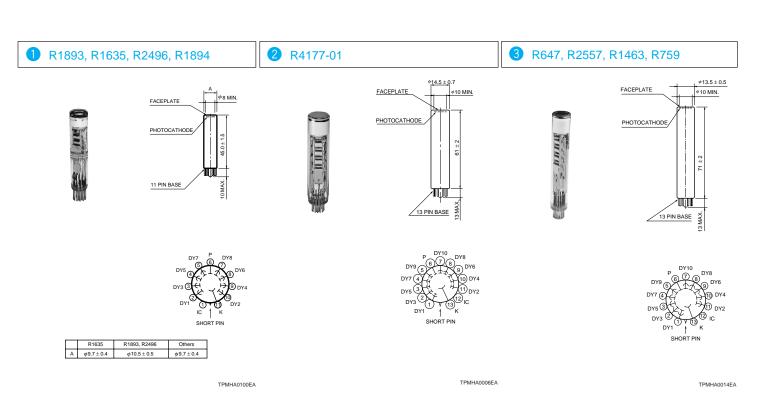


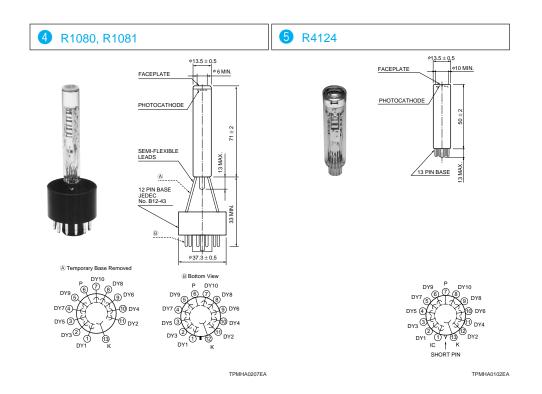


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A		Spe	ectral Respo	nse	0	0	•	•	G	Maximum	Ratings	Cathode	Sensitivity
		В		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	Range	Wave-	cathode Material	Window	line	No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
0mm ((3/8") Dia. Types												
R1893	Subminiature size, for UV range	200S	160 to 320	240	Cs-Te	Q	0	L/8	E678-11N*/4	1500	0.01	_	_
R1635	For visible range and scintillation counting	400K	300 to 650	420	ВА	K	0	L/8	E678-11N*/4	1500	0.03	60	95
R2496	For UV to visible range, fast time response	400S	160 to 650	420	ВА	Q	0	L/8	E678-11N*/5	1500	0.03	60	95
R1894	For UV to near IR range, general purpose	500K (S-20)	300 to 850	420	MA	К	0	L/8	E678-11N*/4	1500	0.03	80	120
 3mm (1/2") Dia. Types	<u>'</u>			<u>'</u>				<u> </u>				
R1081	For VUV range, MgF ₂ window	100M	115 to 200	140	Cs-I	MF	4	L/10	E678-12A*	2250	0.01	-	_
R1080	For UV range, MgF ₂ window	200M	115 to 320		Cs-Te	MF	4	L/10	E678-12A*	1250	0.01	_	-
R759	For UV range	200S	160 to 320	240	Cs-Te	Q	3	L/10	E678-13A*/7	1250	0.01	_	-
R647	For visible range and scintillation counting				ВА	K	3	L/10	E678-13A*/	1250	0.1	40	100
R4124	For visible range, fast time response	400K		420	ВА	K	6	L/10	E678-13A*/9	1250	0.03	40	95
R2557	Low noise bialkali photocathode	402K	300 to 650		LBA	K	3	L/10	E678-13A*/8	1500	0.03	25	40
R4177-01	High temperature, ruggedized type	401K		375	НВА	K	2	L/10	E678-13A*/	1800	0.02	20	40
R1463	Multialkali photocathode for UV to	500U	185 to 850	420	MA	U	3	L/10	E678-13A*/7	1250	0.03	80	120

Catho	de Sens	itivity	•			Ano	de Chara	cteristics	M				
Blue (5-58)	Red / White	Radiant Typ.	Anode to Cathode Supply	And	de Sensi	tivity Radiant	Gain	Cur	e Dark rent 80 min.)	Rise	esponse	Notes	Type No
Typ. (μ A/lm-b)	Ratio Typ.	(mA/W)	Voltage (Vdc)	Min. (A/lm)	Typ. (A/lm)	Typ. (A/W)	Тур.	Typ.	Max. (nA)	Time Typ. (ns)	Transit Time Typ. (ns)		Турсти
-	-	24 ^b	1250 ①	1.2 × 10 ³ b (A/W)	-	3.6 × 10 ³	1.5 × 10 ⁵	0.5	2.5	0.8	7.8		R1893
9.5	_	76	1250 ①	30	100	8.0 × 10 ⁴	1.1 × 10 ⁶	1	50	0.8	9.0	Photon counting type: R1635P UV glass window type: R3878	R1635
9.5	_	76	1250 5	30	100	8.0 × 10 ⁴	1.1 × 10 ⁶	2	50	0.7	9.0		R2496
-	0.2	51	1250 ①	10	50	2.1 × 10 ⁴	4.2 × 10 ⁵	2	20	0.8	7.8		R1894
		•									<u>'</u>		
_	_	9.8®	2000 13	2 × 10 ² (a)	_	9.8 × 10 ²	1.0 × 10 ⁵	0.03	0.05	1.8	18		R1081
_	_	28 ⁶	1000 13	4 × 10 ³ b (A/W)	-	1.4×10 ⁴	5.0 × 10 ⁵	0.3	1	2.5	24		R1080
-	_	28 ^b	1000 13	4 × 10 ³ b (A/W)	_	1.4×10 ⁴	5.0 × 10 ⁵	0.3	1	2.5	24		R759
9.5	_	76	1000 13	30	100	7.6 × 10 ⁴	1.0 × 10 ⁶	1	15	2.5	24	Photon counting type: R647P UV glass window type: R960 Synthetic silica window type: R760	R647
9.5	_	76	1000 19	30	100	8.0 × 10 ⁴	1.1 × 10 ⁶	1	15	1.1	12	UV glass window type: R4141	R4124
5.5	_	50	1250 16	50	200	2.5 × 10 ⁵	5.0 × 10 ⁶	10 [®]	30 [®]	2.2	22		R2557
6.0	_	50	1500 13	10	20	2.5 × 10 ⁴	5.0 × 10 ⁵	0.5	10	2.0	20		R4177-0
_	0.2	51	1000 13	30	120	5.1 × 10 ⁴	1.0 × 10 ⁶	4	20	2.5	24	Photon counting type: R1463P	R1463



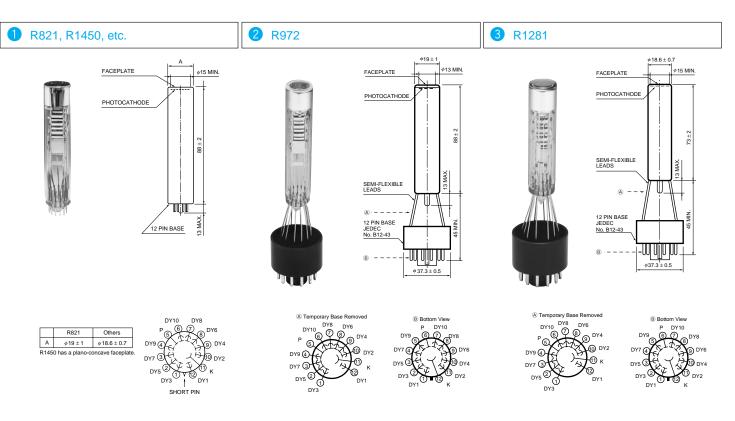


(Unit: mm)

(at 25°C)

A		Spe	ectral Respo	nse	0	0	3	9	©	Maximum	Ratings	Cathode S	Sensitivity
		В		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve	Range	Wave- length	cathode Material	Window Material		No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
19mm (3/4") Dia. Types												
R972	For VUV range, MgF ₂ window	100M	115 to 200	140	Cs-I	MF	2	L/10	E678-12A*	2250	0.01	_	_
R821	For UV range, synthetic silica window	200S	160 to 320	240	Cs-Te	Q	•	L/10	E678-12L*/131415	1250	0.01	-	_
R1166	For visible range and scintillation counting	400K		420	ВА	К	0	L/10	E678-12L*/131415	1250	0.1	70	105
R2801	Low noise bialkali photocathode	402K		375	LBA	K	1	L/10	E678-12L*/131415	1500	0.1	30	45
R1450	Small TTS, for scintillation counting				ВА	K	0	L/10	E678-12L*/17	1800	0.1	70	115
R3478	For visible range, fast time response	400K	300 to 650	420	ВА	K	6	L/8	E678-12L*/1112	1800	0.1	70	115
R5611-01	For visible range, low profile				ВА	K	5	CC/10	E678-12A*	1250	0.1	60	90
R3991	High temperature, ruggedized type, low profile	40414		375	НВА	K	5	CC/10	E678-12A*	1800	0.02	20	40
R1281	High temperature photocathode	401K		3/3	НВА	K	3	L/10	E678-12A*	1800	0.02	20	40
R1617	Multialkali photocathode for visible to near IR range	500K (S-20)	300 to 850		MA	К	0	L/10	E678-12L*/131415	1250	0.1	80	120
R1464	Multialkali photocathode for UV to near IR range	500U	185 to 850	420	MA	U	0	L/10	E678-12L*/131415	1250	0.1	80	120
R1878	For photon counting in visible to near IR range	500K (S-20)	300 to 850		MA	K	4	L/10	E678-12L*/16	1500	0.1	80	120
R632-01	For near IR range, QE=0.05% Typ. at 1.06 μm	700K (S-1)	400 to 1200	800	Ag-O-Cs	K	0	L/10	E678-12L*/131415	1500	0.01	10	20

Catho	de Sens	itivity	•			Ano	de Charac	cteristics	S				A
Blue	Red /	Radiant	Anode to Cathode		de Sensi			Cur	e Dark rent		esponse		
(5-58)	White	Тур.	Supply	Lumir		Radiant	Gain Typ.	(After 3	30 min.)	Rise Time	Transit	Notes	Type No.
Typ. (μ A/lm-b)	Ratio Typ.	(mA/W)	Voltage (Vdc)	Min. (A/lm)	Typ. (A/lm)	Typ. (A/W)	ryp.	Typ. (nA)	Max. (nA)	Typ.	Time Typ. (ns)		
								,	, ,		1 (-7		
_	_	9.8	2000 15	2×10 ² (A/W)	-	9.8 × 10 ²	1.0 × 10 ⁵	0.03	0.05	1.6	17	Cs-Te photocathode type: R976	R972
_	_	28 ^b	1000 15	4 × 10 ³ b (A/W)	_	1.0 × 10 ⁴	3.6 × 10 ⁵	0.3	0.5	2.5	27		R821
10.5	-	85	1000 15	10	100	8.1 × 10 ⁴	9.5 × 10 ⁵	1	5	2.5	27	Synthetic silica window type: R762 UV glass window type: R750	R1166
6.0	-	55	1250 15	50	300	3.7 × 10 ⁵	6.7 × 10 ⁶	15 [®]	45 ⁶	2.2	25		R2801
11.0	-	88	1500 ⑰	100	200	1.5 × 10 ⁵	1.7 × 10 ⁶	3	50	1.8	19		R1450
11.0	ı	88	1700 6	100	200	1.5 × 10 ⁵	1.7 × 10 ⁶	10	300	1.3	14	Synthetic silica window type: R2076	R3478
10.5	-	85	1000 18	10	50	4.7 × 10 ⁴	5.5 × 10 ⁵	3	20	1.5	17	Button stem type: R5611	R5611-01
6.0	_	51	1500 18	5	15	1.9 × 10 ⁴	3.75×10^{5}	0.1	10	1.0	13		R3991
6.0	-	50	1500 15	20	50	6.5 × 10 ⁴	1.3 × 10 ⁶	0.5	10	1.9	21	Button stem type: R1281-02	R1281
_	0.2	51	1000 15	30	120	5.1 × 10 ⁴	1.0 × 10 ⁶	4	20	2.5	27		R1617
_	0.2	51	1000 15	30	120	5.1 × 10 ⁴	1.0 × 10 ⁶	4	20	2.5	27	Synthetic silica window type: R2027	R1464
_	0.2	51	1000 16	30	150	6.1 × 10 ⁴	1.2 × 10 ⁶	100 [®]	250 [®]	1.7	24	Bialkali photocathode type: R2295	R1878
-	0.14 ^d	1.9	1250 15	5	10	9.5×10^{2}	5.0 × 10 ⁵	800 [®]	2000	2.2	25		R632-01



(at 25°C)

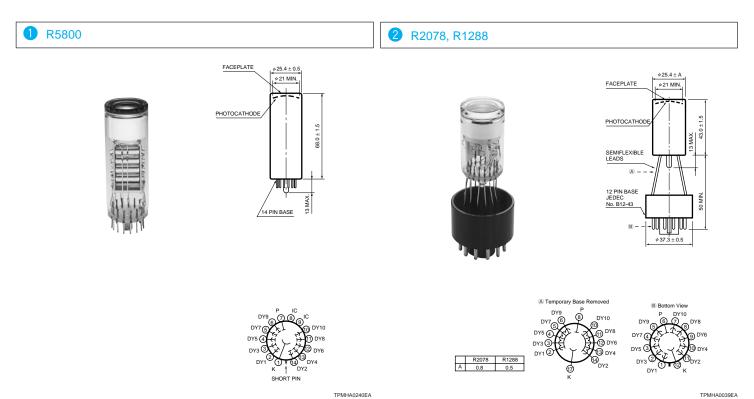
Type No.

R5800 R4998

R2078 R1924 R3550 R1288 R1925 R5070

(Unit: mm)

(Sp	ectral Resp	onse	0	0		•		Maximum	Ratings	Cathode	Sensitivity	Catho		athode	Sensitivit	ity	•			An	ode Chara	cteristic	s M)		
Type No.	Remarks	B Curve Code	Range	Peak Wave-	Photo- cathode Material	Window	Out-	Dynode Structure		Anode to Cathode		Lum Min.	Typ.	Blue (5-58)				adiant Typ.	Anode to Cathode Supply		ode Sen nous	sitivity Radiant	Gain	Cu	de Dark Irrent 30 min.)	Time R	esponse Electror Transit	-
		Code	(nm)	length (nm)	Material	I	INO.	No. of Stages	Socket Assembly	Voltage (Vdc)	Current (mA)		(μ A/lm)	Typ. (μ A/lm-b)			tio p. (m	nA/W)	Voltage (Vdc)	Min. (A/lm)	Typ. (A/lm)	Typ. (A/W)	Тур.	Typ.	Max. (nA)	Time Typ. (ns)	Time Typ. (ns)	
25mm	(1") Dia. Types																											
R5800	For scintillation counting	40016	200 to 650	400	ВА	K	1	L/10	E678-14C*/181920	1800	0.1	70	95	11.0	1	0	-	88	1250 18	_	190	2.3 × 10 ⁵	2.0 × 10 ⁶	2	15	1.7	22	
R4998	For visible range, fast time response	400K	300 to 650	420	ВА	K	4	L/10	E678-12A*	2500	0.1	60	70	9.0	9)	-	72	2250 22	100	400	4.1 × 10 ⁵	5.7 × 10 ⁶	100	800	0.7	10	Synthetic silica wi : R5320 TTS: 16
25mm	(1") Dia. Low Pro	file T	ypes		<u>'</u>	·						•																
R2078	For UV range	201S	160 to 320	240	Cs-Te	Q	2	CC/10	E678-12A*	2000	0.015	_	_	_			- 2	29 ^b	1500 18	4 × 10 ³ b (A/W)	_	1.5 × 10 ⁴	5.0 × 10 ⁵	0.015	0.1	1.5	14	Dark count: 5cps
R1924	For visible range	400K		420	ВА	К	3	CC/10	E678-14C*/181920	1250	0.1	60	90	10.5	1	5	-	85	1000 18	20	100	9.3 × 10	1.1 × 10 ⁶	3	20	2.0	19	Photon counting to Button stem type:
R3550	Low noise bialkali photocathode	402K	300 to 650		LBA	К	3	CC/10	E678-14C*/181920	1250	0.1	30	50	6.5	6	5	-	50	1000 18	20	100	1.2 × 10	2.0 × 10 ⁶	20 [®]	60 [®]	2.0	19	
R1288	High temperature, ruggedized type	401K	1	375	НВА	К	2	CC/10	E678-12A*	1800	0.02	20	40	6.0	6)	-	51	1500 18	8	15	1.9 × 10	3.8 × 10 ⁵	0.1	10	1.5	14	Synthetic silica wi : R1926
R1925	For visible to near IR range	500K (S-20)	300 to 850		MA	K	3	CC/10	E678-14C*/181920	1250	0.1	80	120	_		(.2	60	1000 18	10	30	1.3 × 10	2.5 × 10 ⁵	3	20	2.0	19	
R5070	Prismatic window, multialkali photocathode with high sensitivity	502K	300 to 900	420	MA	K	3	CC/10	E678-14C*/181920	1250	0.1	130	230	_		0	25	65	1000 18	20	100	2.8 × 10	4.3 × 10 ⁵	3	20	2.0	19	



3 R1924, R1925, R3550, R5070

PACEPLATE 228.41

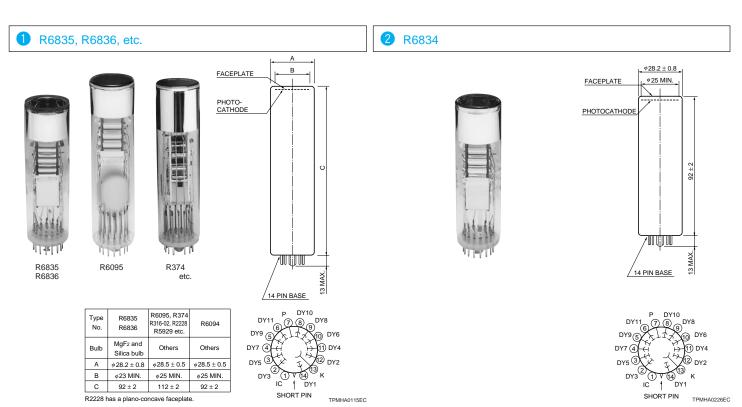
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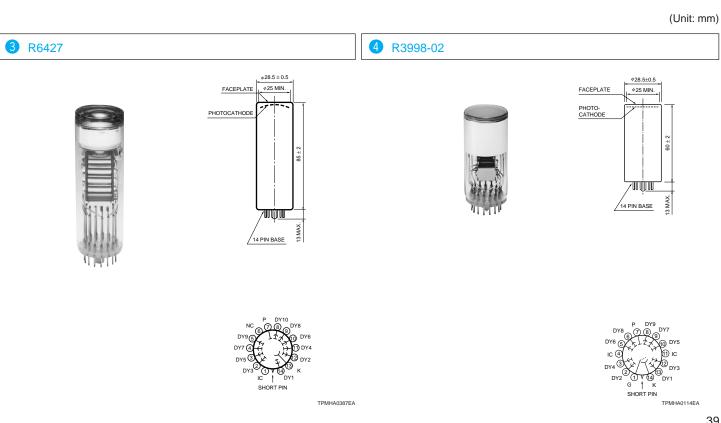
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(at 25°C)

A		Spe	ectral Respo	nse	0	0	•	9	©	Maximum	Ratings	Cathode	Sensitivity
		B		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	Range		cathode Material	uviateriai		No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
28mm (1-1/8") Dia. Types	5											
R6835	For VUV range, MgF2 window	100M	115 to 200	140	Cs-I	MF	0	B + L/11	E678-14C*	2500	0.01	_	-
R6836	For UV range, MgF ₂ window	200M	115 to 320	240	Cs-Te	MF	0	B + L/11	E678-14C*	1500	0.01	_	-
R6834	For UV range, low profile	200S	160 to 320		Cs-Te	Q	2	B + L/11	E678-14C*/2425	1500	0.01	_	_
R6095	For visible range and scintillation counting	40016	2224 252		ВА	К	0	B + L/11	E678-14C*/2425	1500	0.1	60	95
R6427	For visible range, fast time response	400K	300 to 650		ВА	К	3	L/10	E678-14C*/2223	2000	0.2	60	95
R374	Multialkali photocathode for UV to near IR range	500U	185 to 850	420	MA	U	0	B/11	E678-14C*/2425	1500	0.1	80	150
R5929	Prismatic window, high cathode sensitivity	502K	200 to 000		MA	К	0	B/11	E678-14C*/2425	1500	0.1	130	230
R2228	Extended red multialkali photo- cathode	501K	300 to 900	600	MA	K	0	B/11	E678-14C*/2425	1500	0.1	100	200
R316-02	For near IR range, QE=0.06% Typ. at 1.06 μm	700K (S-1)	400 to 1200	800	Ag-O-Cs	K	0	B/11	E678-14C*/2425	1500	0.01	10	20
28mm	(1-1/8") Dia. Low	Profi	le Type										
R3998-02	For visible range and scintillation counting	400K	300 to 650	420	ВА	K	4	B + L/9	E678-14C*	1500	0.1	60	90

Catho	ode Sens	itivity	•			And	de Chara	cteristics	S				(
Blue	Red /	Radiant	Anode to Cathode	And	de Sensi	tivity			e Dark rent		esponse		
(5-58)	White	Тур.	Supply	Lumin	nous	Radiant	Gain		30 min.)	Rise	Electron Transit	Notes	Type No
Typ. (μ A/lm-b)	Ratio Typ.	(mA/W)	Voltage (Vdc)	Min. (A/lm)	Typ. (A/lm)	Typ. (A/W)	Тур.	Typ. (nA)	Max.	Time Typ. (ns)	Time Typ. (ns)		
						1		()			(- /		
-	-	12 ^a	2000 26	-	-	1.2 × 10 ³	1.0 × 10 ⁵	0.03	0.05	2.8	22		R6835
-	-	28 ^b	1000 26	4 ~103 b (A/W)	-	1.4 × 10 ⁴	5.0 × 10 ⁵	0.3	1	4	30		R6836
-	_	28 ^b	1000 26	4 ~103 b (A/W)	-	1.4 × 10 ⁴	5.0 × 10 ⁵	0.3	1	4	30		R6834
11.0	_	88	1000 26	50	200	1.8 × 10 ⁵	2.1 × 10 ⁶	2	10	4	30	Low profile type : R6094	R6095
11.0	_	88	1500 21	-	475	4.4 × 10 ⁵	5.0 × 10 ⁶	10	200	1.7	16	UV glass window type: R7056 Synthetic silica window type: R7057	R6427
-	0.2	64	1000 26	20	80	3.4 × 10 ⁴	5.3 × 10 ⁵	3	15	15	60	Synthetic silica window type: R376 High gain type: R1104	R374
-	0.25	65	1000 26	30	180	5.1 × 10 ⁴	7.8 × 10 ⁵	5	25	15	60		R5929
-	0.3	40	1000 26	20	150	3.0 × 10 ⁴	7.5 × 10 ⁵	8	30	15	60		R2228
-	0.14 [@]	1.9	1250 26	5	10	9.5 × 10 ²	5.0 × 10 ⁵	2000 [®]	5000 [®]	10	50		R316-02
10.5	_	85	1000 11	50	120	1.1 × 10⁵	1.3 × 10 ⁶	2	10	3.4	23		R3998-02

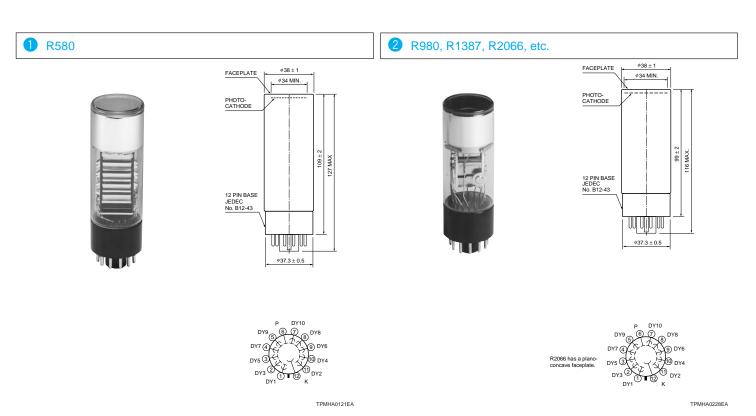


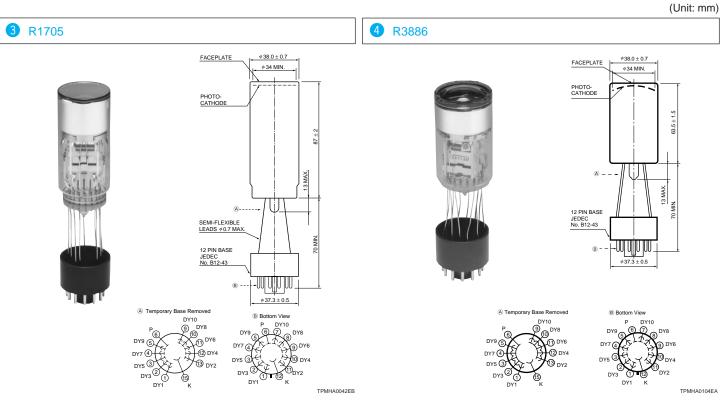


(at	25	°C

A		Spe	ectral Respo	onse	•	•	•	•	G	Maximum	Ratings	Cathode	Sensitivity
		B		Peak	Photo-		Out-	Dynode Structure	Sockot	Anode to	Average		inous
Type No.	Remarks	Curve Code	Range	Wave-	cathode Material	IIVIaterial	line	No. of	Socket	Cathode Voltage	Anode Current	Min	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
88mm	(1-1/2") Dia. Type:	s											
R980	For visible range and scintillation counting				ВА	K	2	CC/10	E678-12A*/2728	1250	0.1	70	100
R3886	For scintillation counting, low pro- file	400K		420	ВА	K	4	CC/10	E678-12A*/2728	1250	0.1	70	90
R580	For scintillation counting, fast time response		300 to 650		ВА	K	0	L/10	E678-12A*/2728	1750	0.1	70	95
R1705	High temperature, ruggedized type	401K		375	НВА	K	3	CC/10	E678-12A*/2728	1800	0.02	20	40
R1387	Multialkali photocathode for visible to near IR range	500K (S-20)	300 to 850	420	MA	K	2	CC/10	E678-12A*/2728	1250	0.2	80	150
R2066	Extended red multialkali photocathode	501K	300 to 900	600	MA	К	2	CC/10	E678-12A*/2728	1500	0.2	120	200
R1767	For near IR range,	700K	400 to 1200	800	An-O-Cs	K	2	CC/10	F678-12A*/27 28	1500	0.01	10	25

Catho	ode Sens	itivity	•			And	de Chara	cteristics	s M				A
Blue	Red /	Radiant	Anode to Cathode	And	ode Sensi	itivity			e Dark rent	Time R	esponse		
(5-58)	White	Тур.	Supply	Lumir	nous	Radiant	Gain		30 min.)	Rise	Electron Transit	Notes	Type No.
Тур.	Ratio		Voltage	Min.	Тур.	Тур.	Тур.	Тур.	Max.	Time Typ.	Time Typ.		
$(\mu \text{ A/Im-b})$	Тур.	(mA/W)	(Vdc)	(A/lm)	(A/lm)	(A/W)		(nA)	(nA)	(ns)	(ns)		
11.5	-	90	1000 16	10	35	3.3 × 10 ⁴	3.7 × 10 ⁵	3	5	2.8	40	Synthetic silica window type: R189	R980
10.5	_	85	1250 16	10	45	4.3 × 10 ⁴	5.0 × 10 ⁵	3	5	2.5	32		R3886
11.0	_	88	1250 16	10	100	9.7 × 10 ⁴	1.1 × 10 ⁶	3	20	2.7	37		R580
6.0	_	50	1500 16	5	20	2.5×10^{4}	5.0 × 10 ⁵	0.5	10	2.0	35		R1705
_	0.2	64	1000 16	10	50	2.1 × 10 ⁴	3.3 × 10 ⁵	4	25	2.8	40	UV glass window type: R1508 Synthetic silica window type: R1509	R1387
_	0.3	40	1000 16	20	50	1.0 × 10 ⁴	2.5 × 10 ⁵	8	30	2.8	40		R2066
_	0.14 ^d	2.4	1250 16	1	5	4.8 × 10 ²	2.0 × 10 ⁵	7000 [®]	20000®	2.2	37		R1767

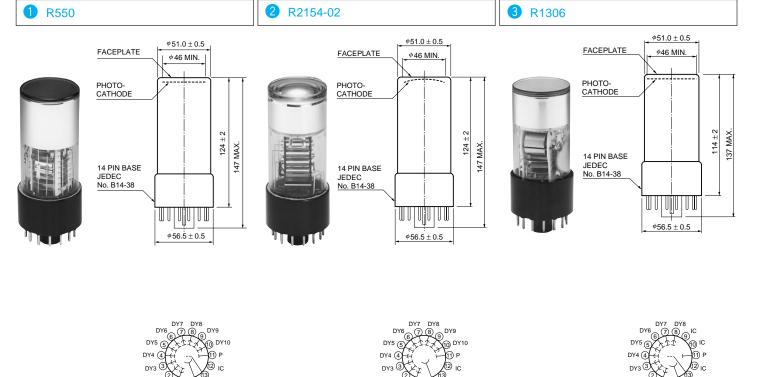


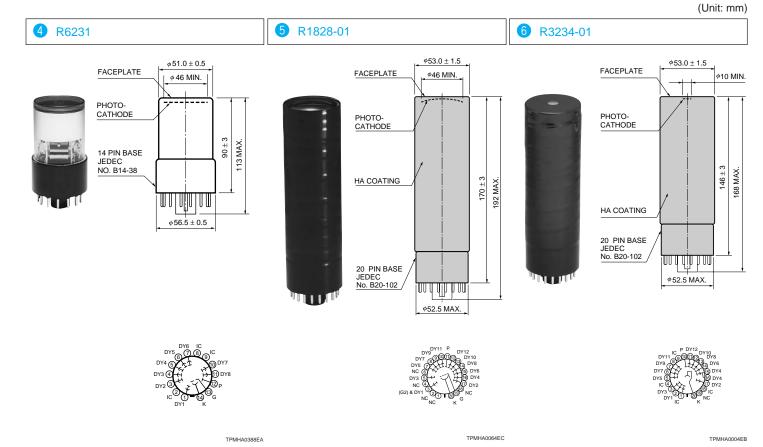


(at	25	°C.

A		Spe	ectral Respo	nse	0	0	3	9	6	Maximum	Ratings	Cathode	Sensitivity
		₿		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	Range	Wave-	cathode Material	\M/indow/	line	No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
51mm ((2") Dia. Types wi	th Pl	astic Ba	ase									
R6231	For visible range and scintillation counting, low profile type				ВА	K	4	B + L/8	E678-14A	1500	0.1	80	110
R1306	For visible range and scintillation counting				ВА	K	3	B/8	E678-14A 1/30	1500	0.1	80	110
R2154-02	For visible range and scintillation counting	400K	300 to 650	400	ВА	K	2	L/10	E678-14A 1/31	1750	0.1	60	90
R1828-01	For visible range, fast time response			420	ВА	K	6	L/12	E678-20A*/36	3000	0.2	60	90
R3234-01	For photon counting, fast time response				BA	К	6	L/12	E678-20A*	2500	0.1	60	80
R550	For visible to near IR range	500K (S-20)	300 to 850		MA	K	0	B/10	E678-14A 1/29 32	1500	0.3	100	150

Catho	de Sens	itivity	•			Ano	de Charac	cteristics	M				A
Blue	Red /	Radiant	Anode to Cathode	And	de Sensi	tivity			e Dark rent	Time R	esponse		
(5-58)	White	Тур.	Supply	Lumir	nous	Radiant	Gain		0 min.)	Rise Time	Electron Transit	Notes	Type No.
Тур.	Ratio Typ.		Voltage	Min.	Typ.	Тур.	Тур.	Тур.	Max.	Тур.	Time Typ.		
(μ A/lm-b)	. , p.	(mA/W)	(Vdc)	(A/lm)	(A/lm)	(A/W)		(nA)	(nA)	(ns)	(ns)		
12.0	-	95	1000 8	3	30	2.6 × 10 ⁴	2.7 × 10 ⁵	2	20	5.0	48	For gamma cameras: R6231-01	R6231
12.0	-	95	1000 ②	3	30	2.6 × 10 ⁴	2.7 × 10 ⁵	2	20	7.0	60	Synthetic silica window type : R2220	R1306
10.5	-	85	1250 16	20	90	8.5 × 10 ⁴	1.0 × 10 ⁶	5	20	3.4	31	Multialkali photocathode type : R3256	R2154-02
10.5	-	85	2500 32	200	1800	1.7 × 10 ⁶	2.0 × 10 ⁷	50	400	1.3	28	Synthetic silica window type : R2059	R1828-01
9.0	-	72	2000 ③7	500	2000	2.0 × 10 ⁶	2.5×10^{7}	1	10	1.3	28	Synthetic silica type: R3235-01 Multialkali type: R3237-01	R3234-01
	0.2	64	1000 14	20	100	4.3 × 10 ⁴	6.7 × 10 ⁵	10	30	9.0	70		R550





For visible range, fast time response

A		Spe	ctral Respo	nse	0	0	•	•	6	Maximum	Ratings	Cathode S	Sensitivity
		B Curve		Peak	Photo-	Window	Out-	Dynode Structure	Socket	Anode to	0	Lumi	nous
Type No.	Remarks	Code	Range		cathode Material	Material	No.	No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
51mm	(2") Dia. Types wi	th GI	ass Bas	se									
R464	For photon counting in visible range				ВА	К	4	B/12	E678-21A*/3537	1500	0.01	30	50
R329-02	For visible range and scintillation counting				ВА	K	2	L/12	E678-21A*/343840	2700	0.2	60	90
R331-05	For visible range and liquid scintillation counting	400K		420	ВА	K	3	L/12	E678-21A*/343840	2500	0.2	60	90
R2083	For visible range, fast time response		300 to 650		ВА	K	0	L/8	E678-19C*	3500	0.2	60	80

HBA

MA

^{500K} (S-20) 300 to 850 420

6

L/10

B/12

E678-19A*

E678-21A*/35 37

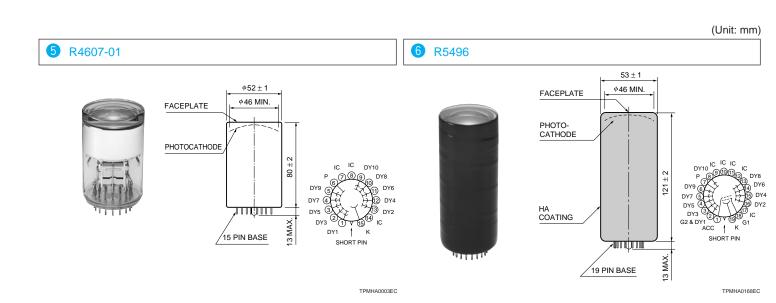
CC/10 E678-15A*

0.2

0.02

1 R2083		2 R329-02	
ntth & n	PHOTO-CATHODE HA COATING HA COATING PHOTO-CATHODE NC NC NC DY8 DY8 DY8 DY9		PHOTO-CATHODE HA COATING HA
3 R331-05		4 R464, R649	
	PHOTO-CATHODE HA COATING PHOTO-CATHODE PHOTO-CAT		## DY11 C DY10 DY8 ## DY11 C DY10 DY8 ## DY11 C DY10 DY8 ## DY11 C DY10 ##

(at 25°C)													
A				M	cteristics	de Chara	Ano			•	itivity	ode Sens	Catho
		esponse	Time Re	Dark	Anode Cur		tivity	ode Sensi	And	Anode to Cathode	Radiant	Red /	Blue
Type No.	Notes	Electron Transit	Rise		(After 3	Gain	Radiant	nous	Lumir	Supply	Typ.	White	(5-58)
		Time	Time Typ.	Max.	Тур.	Тур.	Тур.	Тур.	Min.	Voltage		Ratio	Тур.
		Typ.	(ns)	(nA)	(nA)		(A/W)	(A/lm)	(A/lm)	(Vdc)	(mA/W)	Тур.	(μ A/lm-b)
R464	Synthetic silica window type: R585	70	13	15 [®]	5 [®]	6.0×10^{6}	3.0 × 10 ⁵	300	100	1000 35	50	_	-
R329-02	UV glass window type: R5113-02 Synthetic silica window type: R2256-02	48	2.6	40	6	1.1 × 10 ⁶	9.4×10 ⁴	100	30	1500 34	85	_	10.5
R331-05	Synthetic silica window type: R331	48	2.6	25 [®]	18 [®]	1.3×10 ⁶	1.1 × 10 ⁵	120	30	1500 34	85	_	10.5
R2083	Use of PMT assembly (H2431-50) is recommended. (See P.75)	16	0.7	800	100	2.5×10^6	2.0 × 10 ⁵	200	50	3000 ③	80	_	10.0
R5496	TTS: 270ps	24	1.5	800	100	1.3×10^7	1.0×10 ⁶	1000	100	2500 22	80	_	10.0
R4607-01		29	2.5	50	3	5.0 × 10 ⁵	2.5 × 10 ⁴	20	5	1500 16	50	_	6.0
R649		70	13	350 [®]	200 [®]	6.7 × 10 ⁶	3.4×10 ⁵	800	100	1000 35	51	0.2	-



(at 25°C)

Δ		Spe	ectral Respo	nse	•	O	•	•	G	Maximum	Ratings	Cathode \$	Sensitivity
		₿		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	Range			Window	lina	No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
R375	(2") Dia. Types wind Multialkali photocathode for UV to near IR range	th Gla	160 to 850	420	MA	Q	0	B/10	E678-15A*/41	1500	0.1	80	150
R669	Extended red multialkali photocathode	501K	300 to 900	600	EMA	K	0	B/10	E678-15A*/41	1500	0.1	140	230
R943-02	GaAs photocathode for UV to 930nm range	650S	160 to 930	300 to 800	GaAs(Cs)	Q	3	L/10	(Note) E678-21C*/3339	2200	0.001	300	600
R3310-02	InGaAs photocathode for 300 to 1040nm range	851K	300 to 1040	400	InGaAs	K	3	L/10	(Note) E678-21C*/33 39	2200	0.001	80	150
	1								L070-2107555				

2 L/12 E678-21A*/293440

0.2

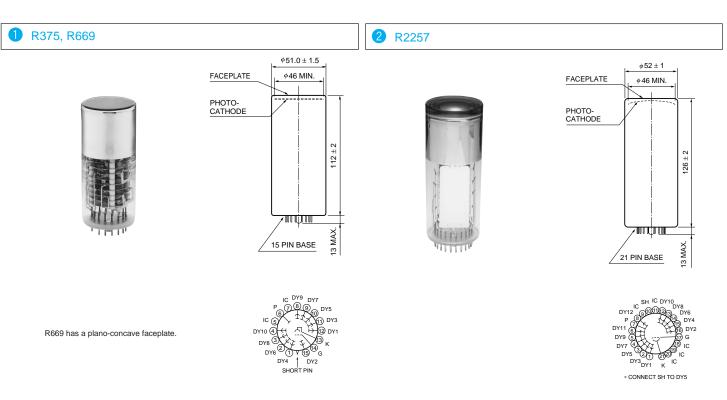
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230

 $(Note)\ For\ cooling\ operation,\ another\ ceramic\ socket,\ type\ number\ E678-21D\ (option)\ is\ recommended.$

501K 300 to 900 600 EMA

Catho	de Sensi	itivity	•			Ano	de Chara	cteristics	M				A
Blue (5-58)	Red / White	Radiant Typ.	Anode to Cathode Supply	And	ode Sensi	tivity Radiant	Gain		e Dark rent 0 min.)		esponse	Notes	Type No.
Typ. (μ A/lm-b)	Ratio Typ.	(mA/W)	Voltage (Vdc)	Min. (A/lm)	Typ. (A/lm)	Typ. (A/W)	Тур.	Typ.	Max.	Time Typ. (ns)	Transit Time Typ. (ns)	140103	туре но.
_	0.2	64	1000 14	20	80	4.3×10^4	5.3 × 10 ⁵	5	20	9.0	70		R375
-	0.35	50	1000 14	20	75	1.7 × 10 ⁴	3.3 × 10 ⁵	7	15	9.0	70		R669
-	0.58	71	1500 20	150	300	3.6 × 10 ⁴	5.0 × 10 ⁵	20 ^①	50 ¹	3.0	23		R943-02
-	0.4	9.4 (at 852.1nm)	1500 20	15	50	3.1 × 10 ³ (at 852.1nm)	3.3 × 10 ⁵	30 ^①	150 ^①	3.0	23		R3310-02
-	0.35	50	1500 34	15	100	2.2 × 10 ⁴	4.3 × 10 ⁵	30	100	2.6	48		R2257



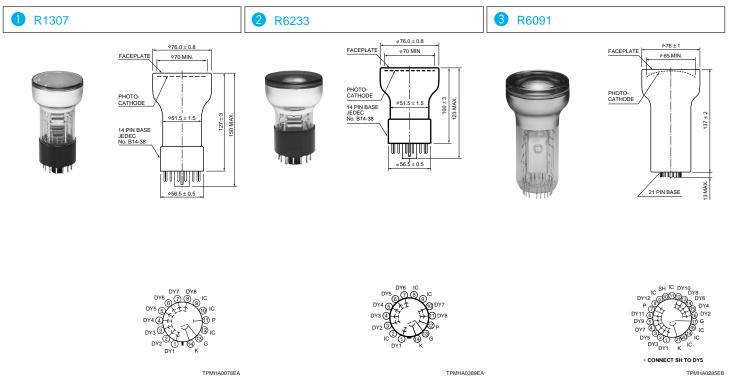


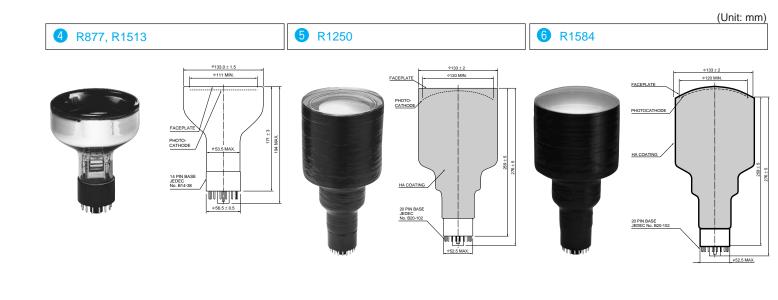
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(at 25°C)
A

A		Spe	ctral Respo	nse	0	O	•	G	(G	Maximum	Ratings	Cathode	Sensitivity
		B		Peak	Photo-	Window	Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	Range		cathode Material	Material	No.	No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)					Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
76mm (3") Dia. Types												
R1307	For scintillation counting, 8-stage dynodes				ВА	K	0	B/8	E678-14A 1/30	1500	0.1	80	110
R6233	For scintillation counting, low profile type	400K	300 to 650	420	ВА	K	2	B + L/8	E678-14A■	1500	0.1	80	110
R6091	For scintillation counting, 12-stage dynodes				ВА	K	3	L/12	E678-21A*	2500	0.2	60	90
127mm	(5") Dia. Types												
R877	For scintillation counting, 10-stage dynodes	40016	200 +- 050		ВА	К	4	B/10	E678-14A / 29 32	1500	0.1	60	80
R1250	For scintillation counting, 14-stage dynodes, fast time response	400K	300 to 650	400	ВА	K	5	L/14	E678-20A*/43/44	3000	0.2	55	70
R1513	For visible to near IR, variant of R877 with venetian blind dynodes	500K (S-20)	300 to 850	420	MA	К	4	VB/10	E678-14A / 29 32	2000	0.1	100	150
* R1584	For scintillation counting,14-stage dynodes, fast time response	400U	300 to 850		ВА	К	6	L/14	E678-20A*	3000	0.2	55	70

Catho	ode Sens	itivity	•			Ano	de Charac	cteristics	• •				A
Blue	Red /	Radiant	Anode to Cathode	And	ode Sensi	itivity			e Dark rent	Time Re	esponse		
(5-58)	White	Typ.	Supply	Lumir	nous	Radiant	Gain		0 min.)	Rise	Electron	Notes	Type No.
Тур.	Ratio Typ.		Voltage	Min.	Typ. (A/lm)	Тур.	Тур.	Тур.	Max.	Time Typ.	Time Typ.		
(μ A/lm-b)	71	(mA/W)	(Vdc)	(A/lm)	(A/IIII)	(A/W)		(nA)	(nA)	(ns)	(ns)		
12.0	_	95	1000 ②	3	30	2.6 × 10 ⁴	2.7 × 10 ⁵	2	20	8.0	64	K-free borosilicate glass type: R1307-07 For gamma cameras: R1307-01	R1307
12.0	_	95	1000 8	3	30	2.6 × 10 ⁴	2.7 × 10 ⁵	2	20	6.0	52	For gamma cameras: R6233-01	R6233
10.5	_	85	1500 34	50	450	4.3 × 10 ⁵	5.0 × 10 ⁶	10	60	2.6	48		R6091
10.0	-	80	1250 14	20	40	4.0 × 10 ⁴	5.0 × 10 ⁵	10	50	10.0	90	K-free borosilicate glass type: R877-01	R877
9.0	_	72	2000 40	300	1000	1.0 × 10 ⁶	1.4×10^{7}	50	300	2.5	54	8-stage dynode type: R4144	R1250
1	0.2	64	1500 14	10	50	2.1 × 10 ⁴	3.3 × 10 ⁵	30	150	7.0	82		R1513
9.0	_	72	2000 40	300	1000	1.0 × 10 ⁶	1.4×10^{7}	50	300	2.5	54		R1584*





Hemispherical Envelope Photomultiplier Tubes

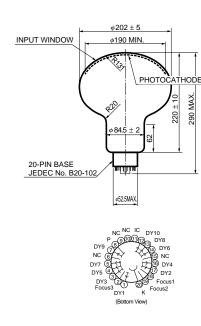
A		Spe	ctral Respo	nse	•	0	•	•	G	Maximum	Ratings	Cathode S	Sensitivity
		B		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumii	nous
Type No.	Remarks	Curve Code	Range	Wave- length	Photo- cathode Material	Window Material	line No.	No. of	Socket	Cathode Voltage	Anode	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/Im)

Hemispherical Envelope Types

	<u> </u>												
R5912	For high energy physics research, 8" dia.	4001/	200 +- 050	400	ВА	K	1	B + L/10	E678-20A*	1800	0.1	-	70
R3600-02	For high energy physics research, 20" dia.	400K	300 to 650	420	ВА	K	2	VB/11	E678-20A*	2500	0.1	_	60

1 R5912





Notes Type No.

(at 25°C)

(5-58)	Тур.	Supply	Lumi	nous	Radiant	Gain	(After 3	30 min.)	Rise	Transit	Notes	Type No.
Тур.		Voltage	Min.	Тур.	Тур.	Тур.	Тур.	Max.	Time Typ.	Time Typ.		
(μ A/lm-b)	(mA/W)	(Vdc)	(A/lm)	(A/lm)	(A/W)		(nA)	(nA)	(ns)	(ns)		
								_				
9.0	72	1500 25	_	700	7.2 × 10 ⁵	1.0 × 10 ⁷	50	700	3.8	55		R5912
8.0	65	2000 29	_	600	6.5 × 10 ⁵	1.0 × 10 ⁷	200	1000	10	95		R3600-02

Anode Characteristics M

Gain

Anode Dark Current (After 30 min.)

Time Response

Electron

Rise

(Unit: mm)

2 R3600-02

Blue

Radiant

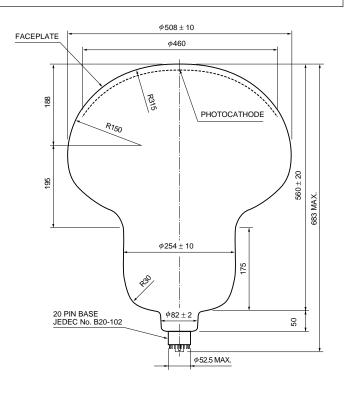
Anode to

Cathode



Anode Sensitivity

Luminous

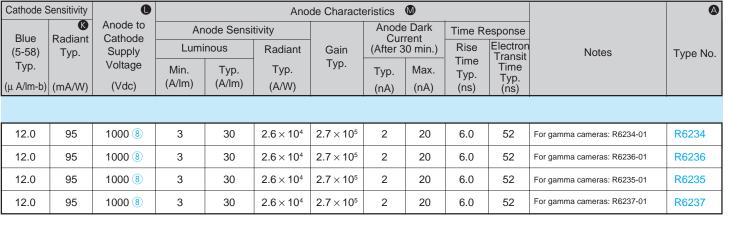


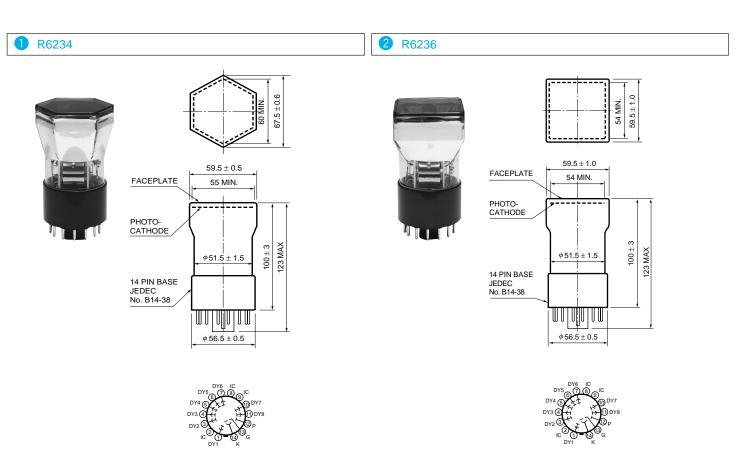


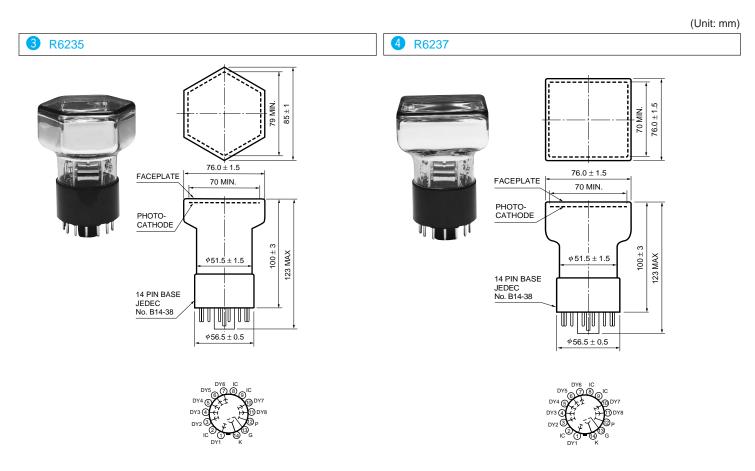
Special Envelope Photomultiplier Tubes

(at	25	٥(

A		Spe	ctral Respo	nse	0	0	(3	•	G	Maximum	Ratings	Cathode S	Sensitivity
		₿		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumii	nous
Type No.	Remarks	Curve Code	Range Wave-	cathode Material	II\/latarial		No. of	Socket	Cathode Voltage	de Anode	Min.	Тур.	
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
R6234	For scintillation counting, 60mm dia. hexagonal faceplate, low profile				ВА	K	•	B + L/8	E678-14A	1500	0.1	80	110
R6236	For scintillation counting, 60 × 60mm square faceplate, low profile	4001/	200 to 650	420	ВА	K	2	B + L/8	E678-14A■	1500	0.1	80	110
R6235	For scintillation counting, 76mm dia. hexagonal faceplate	400K	300 to 650	420	ВА	K	3	B + L/8	E678-14A■	1500	0.1	80	110
R6237	For scintillation counting, 76 × 76mm square faceplate, low profile				ВА	K	4	B + L/8	E678-14A■	1500	0.1	80	110



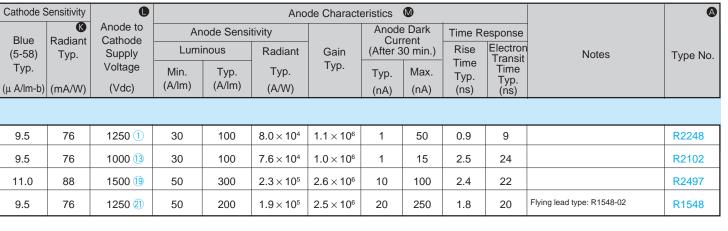


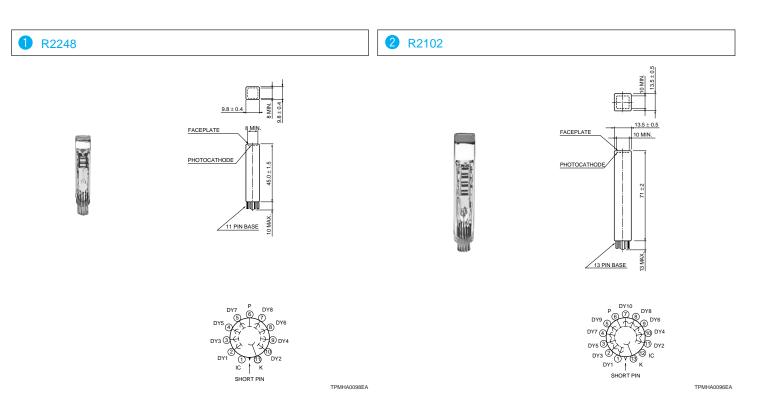


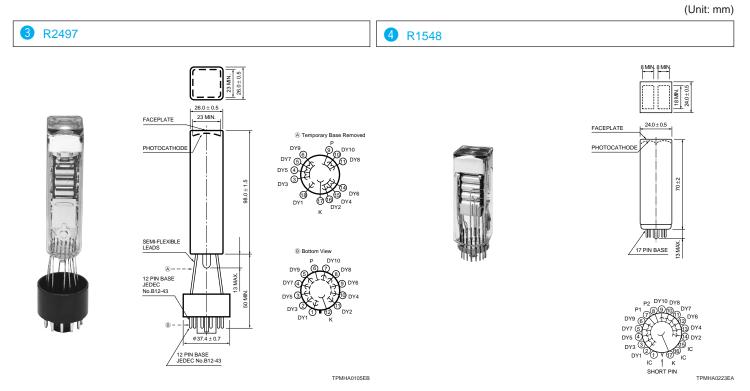
Special Envelope Photomultiplier Tubes

(at 25°C)

A		Spe	ctral Respo	nse	0	O	•	•	©	Maximum	Ratings	Cathode S	Sensitivity
		₿		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumi	nous
Type No.	Remarks	Curve Code	Range	Wave-	cathoda	Window Material	line	No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
R2248	10 × 10mm square envelope				ВА	K	0	L/8	E678-11N*/4	1500	0.03	60	95
R2102	13 × 13mm square envelope	40016	000 1 - 050	400	ВА	К	2	L/10	E678-13A*/7	1250	0.1	40	100
R2497	25 × 25mm square envelope	400K	300 to 650	420	ВА	К	3	L/10	E678-12A*	1800	0.1	70	115
R1548	Rectangular dual structure in single envelope				ВА	К	4	L/10	E678-17A*	1750	0.1	60	80







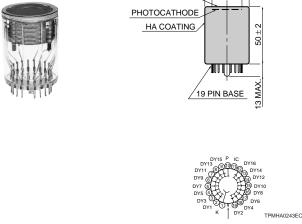
Tubes for Highly Magnetic Environments

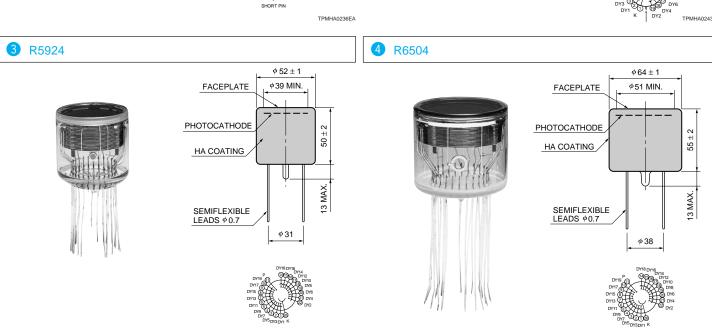
A			S	pectral Respo	nse	•	©	Maximun	n Ratings 🕕	Cathode	Sensitivity
Type No.	Tube Diameter	Outline No.	Curve code	Range	Peak Wave- length	Dynode Structure No. of	Socket	Anode to Cathode Voltage	Average Anode Current		Luminous Typ.
	mm (inch)			(nm)	(nm)	Stages	Assembly	(V)	(mA)	(%)	(μ A/lm)
High G	ain Types										
R5505	25/(1)	1				FM/15	E678-17A*/45	2300	0.01	23	80
R5946	38/(1.5)	2				FM/16	E678-19D	2300	0.01	23	80
R5924	51/(2)	3	400K	300 to 650	420	FM/19	_	2300	0.1	22	70
R6504	64/(2.5)	4				FM/19	_	2300	0.1	22	70
R5542	78/(3)	6				FM/19	_	2300	0.1	22	70

These tubes use fine mesh dynodes and offer excellent pulse linearity and TTS characteristics. UV glass window type R5506 (1"), R6148 (1.5"), R6608 (2"), R6505 (2.5"), R5543 (3") are available.

2 R5946 **1** R5505 FACEPLATE PHOTOCATHODE HA COATING

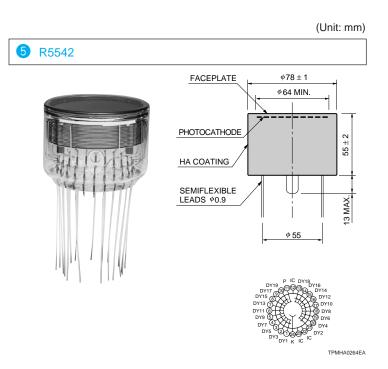






(at 25°C)

Cathode S	Sensitivity	•				Anoc	le Characte	ristics M				A
Blu	ie	Anode to Cathode	Anode		Gain		Anode Da	ark Current	Time R	esponse		
Min.	Typ.	Supply Voltage (V)	Luminous Sensitivity Typ. (A/lm)	at 0 tesla Typ.	at 0.5 tesla Typ.	at 1.0 tesla Typ.	Typ.	30 min.) Max. (nA)	Rise Time Typ. (ns)	Electron Transit Time Typ. (ns)	Notes	Type No.
											Assembly Type	
_	9.5	2000 41	40	5 × 10 ⁵	2.3 × 10⁵	1.8 × 10 ⁴	5	30	1.5	5.6	:H6152-01	R5505
-	9.5	2000 42	80	1 × 10 ⁶	4.3×10 ⁵	2.9 × 10 ⁴	5	30	1.9	7.2	Assembly Type :H6153-01	R5946
-	9.0	2000 43	700	1 × 10 ⁷	4.1×10 ⁶	2.5 × 10 ⁵	30	200	2.5	9.5	Assembly Type :H6614-01	R5924
_	9.0	2000 43	700	1 × 10 ⁷	4.1 × 10 ⁶	2.0 × 10 ⁵	50	300	2.7	11.0		R6504
_	9.0	2000 43	600	1 × 10 ⁷	3.0 × 10 ⁶	1.7×10 ⁵	80	400	2.9	12.3	Assembly Type :H6155-01	R5542



Position-Sensitive Photomultiplier Tubes

400K 300 to 650 420

Cross-wire anode type, 78 × 78mm square envelope

Cross-wire anode type, 130mm

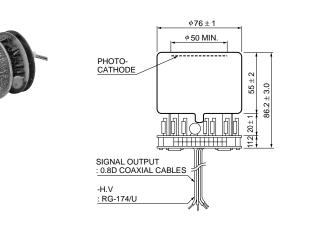
A			ctral Respo	onse	No. of	Effective		Dvnode	Maximum F			
Type No.	Remarks	Curve Code	Range (nm)	Peak Wave- length (nm)	Anode Wires or Anode Marixes	Area	Out- line No.	Structure No. of Stages	Anode to Cathode Voltage (Vdc)	Average Anode Current (mA)	Lumi Min. (μ A/lm)	Тур.
Positio	n-Sensitive Photo		iplier T	ubes								
R2486-02	Cross-wire anode type, 76mm dia.				16(X) + 16(Y)	φ50	0	CM/12	1300	0.1	50	80

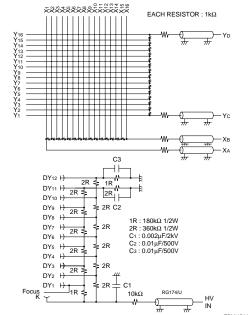
 $18(X) + 16(Y) | 60(X) \times 55(Y)$

φ100

1 R2486-02

28(X) + 28(Y)





CM/12

CM/12

1300

1300

40

50

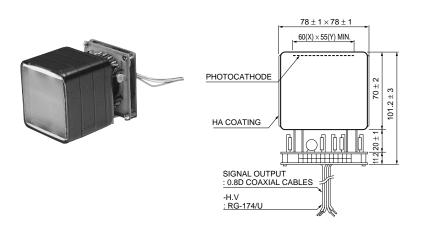
80

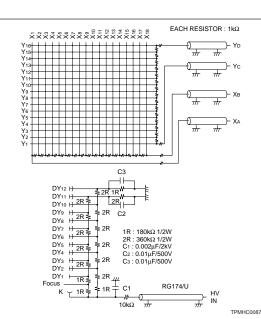
80

0.1

0.1

2 R2487-02





(at 25°C) Cathode Sensitivity Anode Characteristics Anode Dark Time Response Anode to Anode Sensitivity Radiant Cathode Current Blue Red / Electron Rise (After 30 min.) Luminous Gain (5-58)White Тур. Supply Radiant Notes Type No. Time Voltage Тур. Тур. Ratio Тур. Min. Тур. Time Max. Тур. Тур. Typ. (ns) Тур. (mA/W) (A/ ℓ m) (A/ ℓ m) (A/W) μ A/lm-b) (Vdc) (nA) (nA) (ns) 9.0 72 1250 39 5.0 8.0 7.2×10^3 1 × 10⁵ 20 17 R2486-02 5.5 72 1250 39 17 R2487-02 9.0 3.0 7.2×10^{3} 5.5

 1×10^5

40

150

6.0

 7.2×10^{3}

(Unit: mm)

R3292-02

3 R3292-02

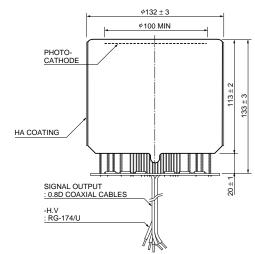
9.0

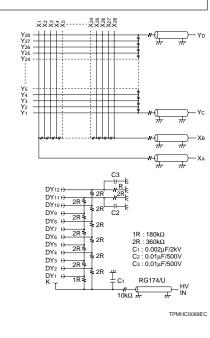


72

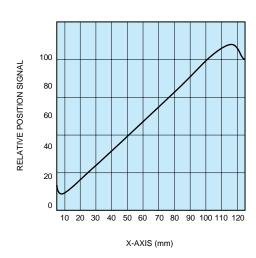
1250 39

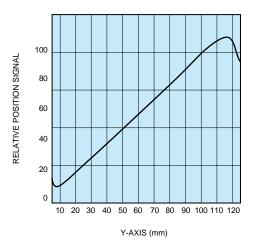
5.0





R3292-02 Position Signal Linearity





Microchannel Plate-Photomultiplier Tubes (MCP-PMTs)

A		Spe	ectral Respo	nse	0	O	•		Max	kimum Rati	ngs 📳	Term	inals
Type No.	Remarks	B Curve Code	Range	Peak Wave- length	Photo- cathode Material	Material	Out- line No.	No. of MCP Stage	Supply Voltage	Anode (-HV Input	Signal Output
			(nm)	(nm)					(Vdc)	(nA)	(mA)		

Standard Types (Effective Photocathode Area: 11mm Dia.)

R3809U-50	For UV to near IR range	500S	160 to 850	430	MA	Q	0							
R3809U-51	For UV to near IR range (Extended red multialkali)	501S	160 to 910	600	EMA	Q	0							
R3809U-52	For UV to visible range	403K	160 to 650	400	ВА	Q	1	2	-3400	100	350	SHV-R	SMA-R	
R3809U-57	For UV range	201M	115 to 320	230	Cs-Te	MgF ²	1		-3400	100	330	3117-10	SIVIA-IX	
R3809U-58	For UV to near IR range	500M	115 to 850	430	MA	MgF ²	0							
R3809U-59	For visible to IR range	700M	400 to 1200	800	Ag-O-Cs	K	1							

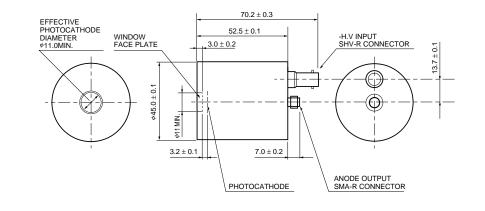
Gated Type (Effective Photocathode Area: 10mm Dia.)

	R5916U-50	High-speed gate operation of less than 5ns	500S	160 to 850	430	MA	Q	2						
	R5916U-51	High-speed gate operation of less than 5ns	501S	160 to 910	600	EMA	Q	2	2	-3400	100	350	SHV-R	SMA-R
Ì		High-speed gate operation of less than 5ns	403K	160 to 650	400	BA	Q	2						

To improve the S/N ratio in low light level detection, an exclusive cooler unit (C4878/E3059-500) for R3809U MCP-PMT is available. The R5916U has a series of types in the same suffixes as R3809U series. But an exclusive cooler unit shall be made upon custom order only. High speed amplifier C5594 series (Gain: 36dB Typ., Frequency Bandwidth: 50kHz to 1.5GHz) are avairable.

1 R3809U-50 Series

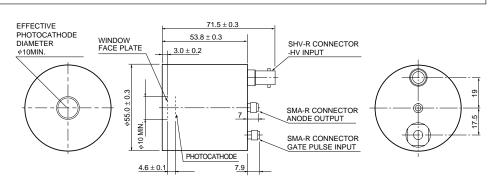




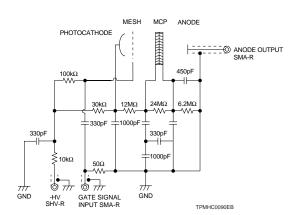
Catho	ode Sensitivi	ty			А	node Ch	aracteri	stics 0			A
0	Lumi	inous	Anode to	Anode		Anode	e Dark	Ti	me Respons	se	
Quantum Efficiency	B.A.	T	Cathode Supply	Sensitivity Luminous	Gain	Cur	rent	Rise Time	Electron Transit	TTS	Type No.
Lilicition	Min.	Тур.	Voltage	Тур.	Тур.	Тур.	Max.	Тур.	Time Typ.	110	
(%)	(μ A/lm)	(μ A/lm)	(Vdc)	(A/Im)		(nA)	(nA)	(ns)	(ns)	(ps)	
17	100	150		30		_	10				R3809U-50
8.3	240	350		70		_	10				R3809U-51
19	20	50	-3000	10	2 × 10 ⁵	_	0.5	0.15	0.55	25	R3809U-52
11	_	_	-3000	_	2 × 10	_	0.1	0.15	0.55	25	R3809U-57
17	100	150		30		_	10				R3809U-58
0.16	12	25		5		_	10				R3809U-59
14	100	150		30		_	10	0.49	1.0		R5916U-50
7.6	200	300	-3000	60	2×10 ⁵	_	10	0.18	1.0	90	R5916U-51
17	20	45		9		_	0.5	0.15	0.55		R5916U-52

2 R5916U-50 Series





(Unit: mm)



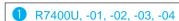
Metal Package Photomultiplier Tubes

A		Spe	ctral Respo	nse	0	O	3	•	G	Maximum	Ratings ①	Cathode S	Sensitivity
		B			Dhata		04	Dynode Structure	Socket		0	Lumii	
Type No.	Remarks	Curve Code	Range		Photo- cathode Material				Socket	Anode to Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)	Materiai		INO.	Stages	Assembly	(Vdc)		(u. A/lm)	(u. A/lm)

R7400U Series

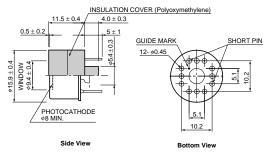
*R7400U	For UV to visible range	400K	300 to 650	420	ВА	K	0	MC/8	E678-12M ⁴ /47	1000	0.1	40	70
*R7400U-01	Multialkali photocathode for visible to near IR range	_	300 to 850	400	MA	K	0	MC/8	E678-12M ⁴ /47	1000	0.1	80	150
*R7400U-02	Multialkali photocathode for visible to near IR range	_	300 to 880	500	MA	K	1	MC/8	E678-12M ⁻ /47	1000	0.1	150	250
*R7400U-03	For UV to visible range	400U	185 to 650	420	ВА	U	1	MC/8	E678-12M ⁴ /47	1000	0.1	40	70
*R7400U-04	Multialkali photocathode for visible to near IR range	_	185 to 850	400	MA	U	0	MC/8	E678-12M ⁻ /47	1000	0.1	80	150
*R7400U-06	For UV to visible range	400S	160 to 650	420	ВА	Q	2	MC/8	E678-12M ⁴ /47	1000	0.1	40	70
*R7400U-09	Solar blind	_	160 to 320	240	Cs-Te	Q	2	MC/8	E678-12M ⁴ /47	1000	0.1	_	_
*R7401	With lens	400K	300 to 650	420	ВА	K	3	MC/8	E678-12M ⁴ /47	1000	0.1	40	70
*R7402	With lens	400K	300 to 850	400	MA	К	3	MC/8	E678-12M ⁴ /4	1000	0.1	80	150

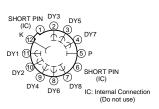
(at 25°C) Cathode Sensitivity Anode Characteristics Anode to (3) Anode Dark Time Response Anode Sensitivity Blue Red / Radiant Cathode Current (After 30 min.) Luminous (5-58)White Тур. Supply Radiant Notes Type No. Transit Time Тур. Ratio Voltage Time Min. Тур. Max. Тур. Typ. (ns) (mA/W) Тур. (A/lm) (A/lm) (μ A/lm-b) (Vdc) (A/W) (nA) (nA) (ns) 8.0 $|4.3 \times 10^4 | 7.0 \times 10^5 | 0.2$ 2 R7400U * 800 (Photon counting type : R7400P-01 200 60 800 (15 75 $3.0 \times 10^4 |5.0 \times 10^5| 0.4$ 4 0.78 R7400U-01 250 58 800 (9 15 $1.7 \times 10^4 \ 3.0 \times 10^5 \ 2.0$ 20 0.78 R7400U-02 Photon counting type: R7400P-03 8.0 62 800 9 10 50 $|4.3 \times 10^4 | 7.0 \times 10^5 | 0.2$ 2 0.78 5.4 R7400U-03 _ Photon counting type : R7400P-04 200 800 9 4 R7400U-04 60 15 $3.0 \times 10^4 |5.0 \times 10^5| 0.4$ 0.78 5.4 Photon counting type : R7400P-06 8.0 62 800 9 10 50 $|4.3 \times 10^4 | 7.0 \times 10^5 | 0.2$ 2 0.78 5.4 R7400U-06 _ 800 9 R7400U-09 22^b 1100° $|5.0 \times 10^{4}|$ 0.0250.5 0.78 5.4 800 (9 5.4 Photon counting type : R7401P R7401 * 62 10 2 0.78 8.0 50 $|4.3 \times 10^4 | 7.0 \times 10^5 | 0.2$ _ Photon counting type : R7402P R7402 * 200 60 800 9 15 $3.0 \times 10^4 | 5.0 \times 10^5 | 0.4$ 0.78 5.4



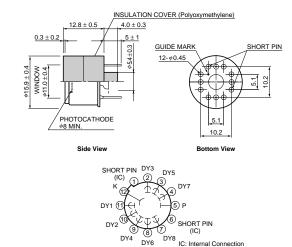








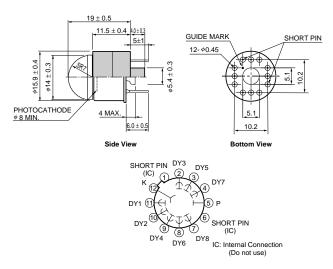




TPMHA04108

3 R7401, R7402



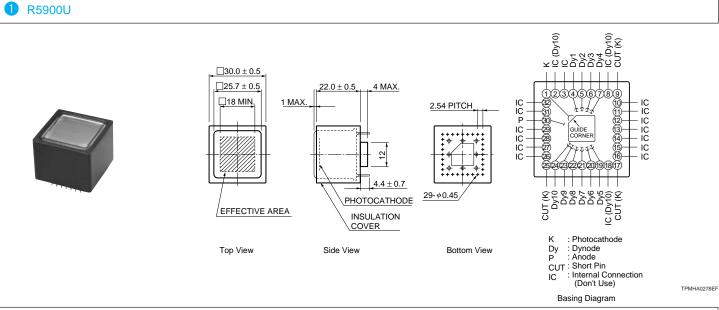


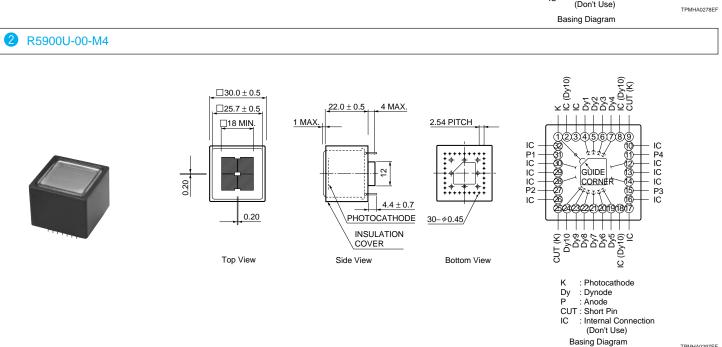
TPMHA0415EB

(Unit: mm)

Metal Package Photomultiplier Tubes

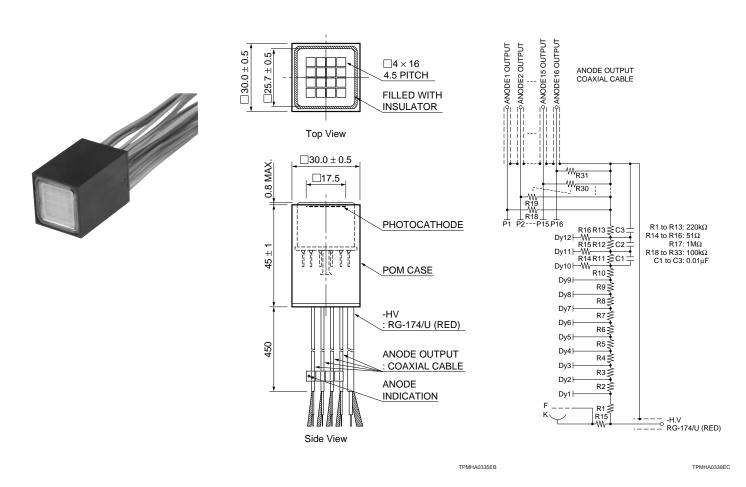
A		Spe	ctral Respo	nse	0	0	•	•	G	Maximum	Ratings	Cathode S	Sensitivity
		₿		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumii	nous
Type No.	Remarks	Curve Code	Range	Wave-	cathoda	Material	lina	No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
R5900U	l Series												
R5900U	For visible range Single anode				ВА	K	0	MC/10	E678-32B 48	900	0.1	50	70
R5900U-00-M4	For visible range 2 × 2 Multianode	400K	300 to 650	420	ВА	K	2	MC/10	E678-32B 49	900	0.1	50	70
H6568	For visible range 4 × 4 Multianode				ВА	K	3	MC/12	_	1000	0.16	_	70





(at 25°C) Cathode Sensitivity Anode Characteristics Anode to (3) Anode Dark Time Response Anode Sensitivity Red / Radiant Cathode Current Electron (After 30 min.) (5-58)White Тур. Supply Luminous Radiant Notes Type No. **Transit** Time Тур. Ratio Voltage Тур. Time Min. Тур. Тур. Max. Тур. Typ. (ns) Тур. (mA/W) (A/lm) (A/lm) (Vdc) (A/W) μ A/lm-b) (nA) (nA) (ns) 2.0×10^{6} 64 800 23 140 20 1.5 R5900U 8.0 _ 72 800 24 25 140 2.0×10^{6} 0.5 1.2 _ R5900U-00-M4 8.0 72 800 39 230 3.3×10^{6} 0.83 H6568

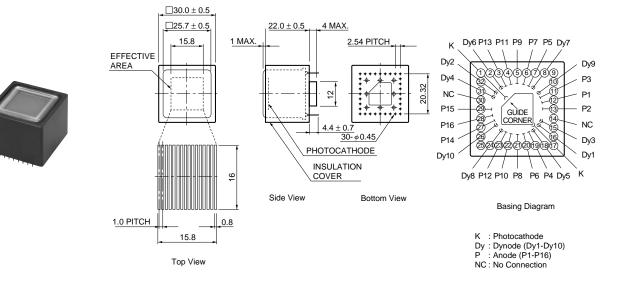
3 H6568



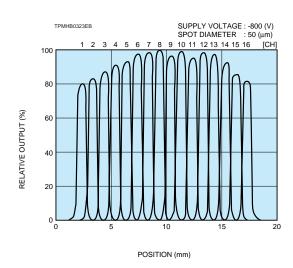
Metal Package Photomultiplier Tubes

A		Spe	ctral Respo	nse	0	0	•	•	G	Maximum	Ratings	Cathode S	Sensitivity
		₿		Peak	Photo-		Out-	Dynode Structure	Socket	Anode to	Average	Lumii	nous
Type No.	Remarks	Curve Code	Range		cathode Material			No. of	Socket	Cathode Voltage	Anode Current	Min.	Тур.
			(nm)	(nm)				Stages	Assembly	(Vdc)	(mA)	(μ A/lm)	(μ A/lm)
R5900U	J Series												
R5900U-00-L16	For visible range 16 Linear Multianode	400K	300 to 650	420	ВА	К	0	MC/10	E678-32B ⁻ /50	900	0.01	50	70
R5900U-00-C8	For visible range 4 + 4 Cross plate anode	400K	300 10 630	420	ВА	K	2	MC/11	E678-32B ¹ /51	900	0.1	_	70

1 R5900U -00 -L16

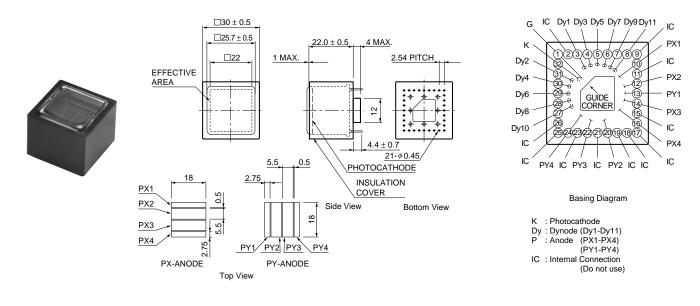


R5900U -00 -L16 Anode Uniformity

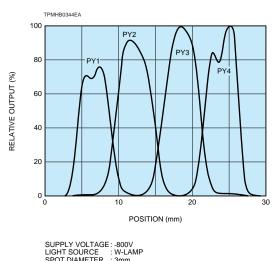


(at 25°C) Cathode Sensitivity Anode Characteristics Anode to 0 Anode Dark Time Response Anode Sensitivity Red / Radiant Cathode Current (After 30 min.) (5-58)White Тур. Supply Luminous Radiant Gain Notes Type No. Transit Time Тур. Тур. Ratio Voltage Тур. Time Min. Тур. Тур. Max. Тур. Typ. (ns) (mA/W) Тур. (A/lm) (A/lm) (Vdc) (A/W) μ A/lm-b) (nA) (nA) (ns) 2.0×10^{6} 0.2 8.0 800 (13 50 140 2 0.6 R5900U-00-L16 8.0 800 28 50 7.0 × 10⁵ 1.4 R5900U-00-C8

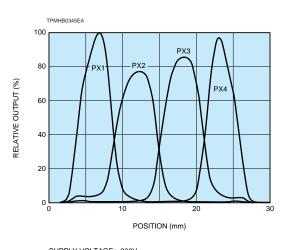
2 R5900U -00 -C8



R5900U -00 -C8 Uniformity



SUPPLY VOLTAGE: -800V LIGHT SOURCE : W-LAMP SPOT DIAMETER : 3mm



SUPPLY VOLTAGE: -800V LIGHT SOURCE : W-LAMP SPOT DIAMETER : 3mm

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Photosensor Module

(at 25°C)

Type No.	Spectral Response			Radiant	Anode	Anode	Supply	Recommended	Max.	Max.	
	Range	Peak Wavelength λp	Out-	at 420nm	Dark Current	Pulse Rise Time	Voltage	Control Voltage Range	Supply Voltage	Output	Configuration
	(nm)	(nm)		(Note1)	(Note2)	(ns)	(Vdc)	(V)	(Vdc)	(Note 3)	

H6779	300 to 650			43	0.2						
H6779-01	300 to 820			30	0.4						DO hazard
H6779-03	185 to 650	420	0	43	0.2	0.78	+11.5 to +15.5	+0.25 to +0.95	+18	100	PC-board mounting type
H6779-04	185 to 820			30	0.4	_					
H6779-06	185 to 650			43	0.2						
H6780	300 to 650	420	2	43	0.2	0.78	+11.5 to +15.5	+0.25 to +0.95	+18	100	Cable output type
H6780-01	300 to 820			30	0.4						
H6780-03	185 to 650			43	0.2						
H6780-04	185 to 820			30	0.4						
H6780-06	185 to 650			43	0.2						
H5784	300 to 650			43	±3						
H5784-01	300 to 820			30	±3						Oakla autout tona
H5784-03	185 to 650	420	3	43	±3	_	±11.5 to ±15.5	±0.25 to ±0.95	±18	10	Cable output type DC to 20kHz
H5784-04	185 to 820			30	±3						
H5784-06	185 to 650			43	±3						

Note1: H6779/H6780 series ... (μA/nW) Note2: H6779/H6780 series ... (nA) Note3: H6779/H6780 series ... (μA)

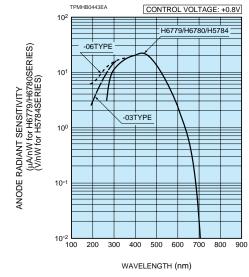
H5784 series ... (V/nW) H5784 series ... Output Offset (mV) H5784 series ... (V) There are the other types of much lower current consumption modules which are H5773 and H5783 series.

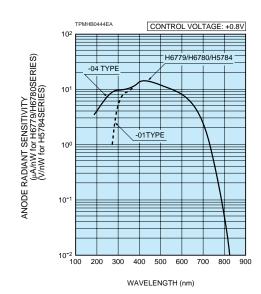
When the system with the photosensor will require the current consumption low, H5773 and

when the system with the photoserisor will require the current consumption low, H3773 and H5783 series are suitable modules, although these types have rather higher ripple noise (current) and longer settling time than new series.

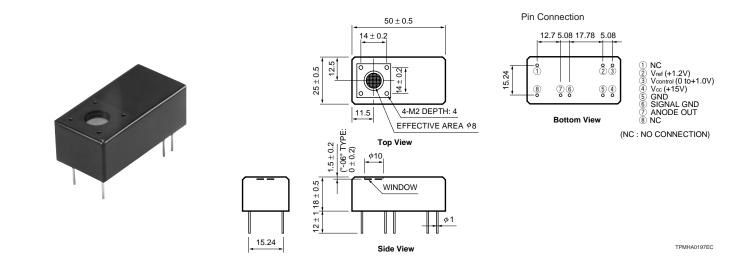
The H6779 / H6780 / H5784 series are light sensor modules including a compact photomultiplier tube (Metal Package PMT) and operating power supply. The H6779 series are on-board types which facilitates mounting directly on a printed circuit board and H6780 series have a cable output. The H5784 series have a low noise amplifier with a cable output.

H6779/H6780/H5784 Series Typical Spectral Response

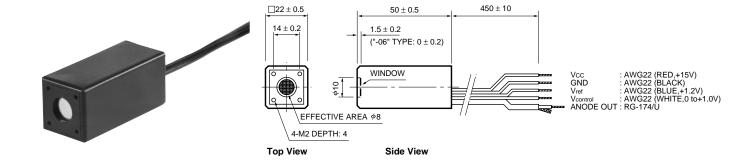




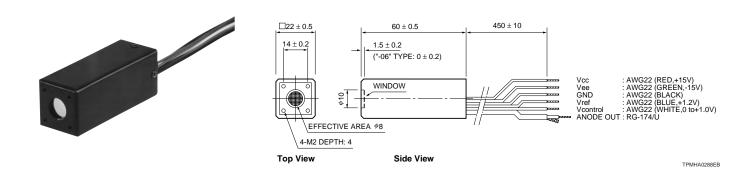
1 H6779 Series (Unit: mm)



2 H6780 Series



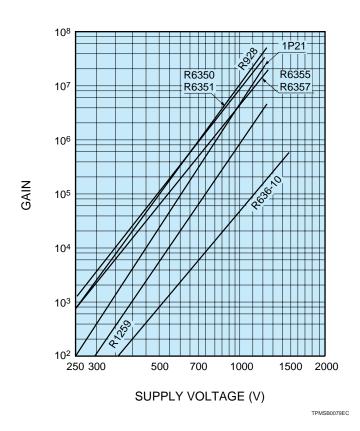




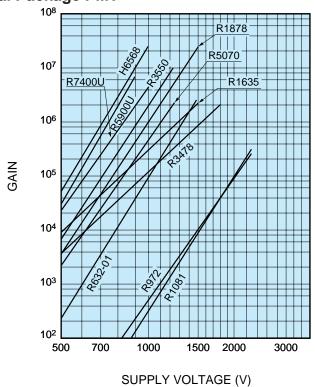
Gain

(For tubes not listed here, please consult our sales office)

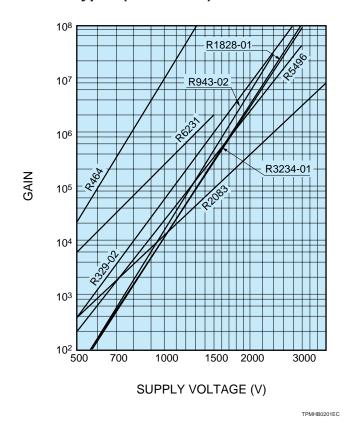
Side-On Types



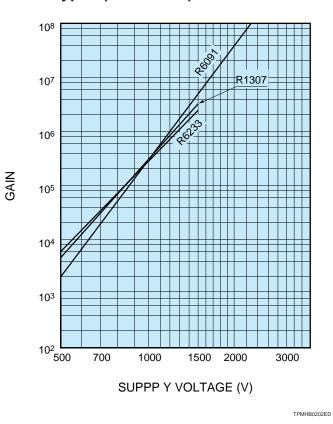
Head-On Types (10 - 25mm Dia.) Metal Package PMT



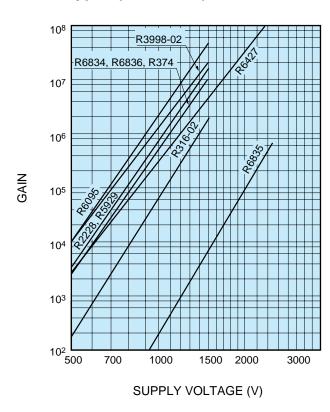
Head-On Types (51mm Dia.)



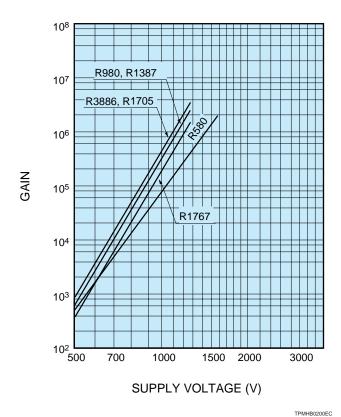
Head-On Types (76mm Dia.)



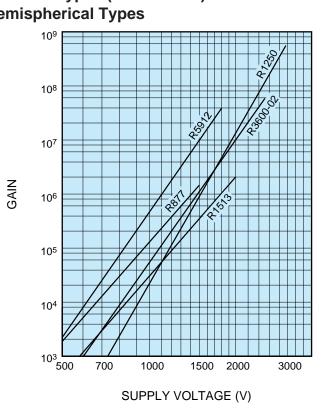
Head-On Types (28mm Dia.)



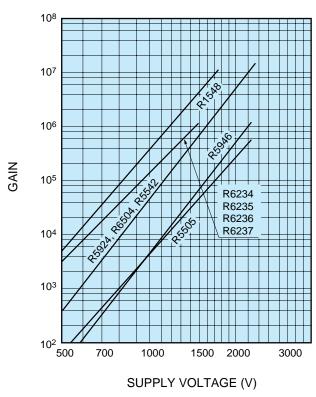
Head-On Types (38mm Dia.)



Head-On Types (127mm Dia.) Hemispherical Types



Special Types



TPMHB0203ED

TRMOROOZEED

Voltage Distribution Ratio

The characteristic values tabulated in the catalog for the individual tube types are measured with the voltage-divider networks having the voltage distribution ratio shown below.

Distribution Ratio Codes	Number of Stage	Voltage Distribution Ratio K: Photocathode Dy: Dynode P: Anode G: Grid F: Focus
	8	K G Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Acc Dy7 Dy8 P
1		2 - 2 1 1 1 1 - 1 1
2		1 1 1 1 1 1 1 1 1 1
3		1.3 4.8 1.2 1.8 1 1 1 0.5 3 2.5
<u>(4)</u>		3 - 1.5 1 1 1 1 - 1 1
(5)		3 - 1.5 1.5 1 1 1 1 - 1 1
6		7 - 1 1.5 1 1 1 - 1 1
7		4 0 1 1.4 1 1 1 1 - 1 1
8		2 2 1 1 1 1 1 1 - 1 1
9		1 — 1 1 1 1 1 — 1 0.5
	9	K G1 G2 G3 Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 P
10	· ·	1 1 1 1 1 1 1 1 1
111		3 1 — — 1 1 1 1.5 1 1 1
12		5 0 3 0 1 1 1 1 1 1 1
	10	K G Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 P
13		1 — 1 1 1 1 1 1 1 1
14		1 1 1 1 1 1 1 1 1 1
15		1.5 — 1 1 1 1 1 1 1 1
16		2 — 1 1 1 1 1 1 1 1 1
17)		2 — 1 1.5 1 1 1 1 1 1 0.75
18		3 — 1 1 1 1 1 1 1 1 1
19		3 — 1 1.5 1 1 1 1 1 1 1
20		3 — 1.5 1 1 1 1 1 1 1 1
21)		4 — 1 1.5 1 1 1 1 1 1 1
22		1.3 4.8 1.2 1.8 1 1 1 1 1.5 3 2.5 (Note 2)
23		1.5 — 1.5 1.5 1 1 1 1 1 1 0.5
24		1.5 — 1.5 1.5 1 1 1 1 1 1 1
		K Dy1 F2 F1 F3 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 P
25		11.3 0 0.6 0 3.4 5 3.33 1.67 1 1 1 1 1
	11	K G Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 Dy11 P
26		
27		8 0.05 1 1 1 1 1 1 1 1 1 1
28		0.5 1.5 2 1 1 1 1 1 1 1 0.5
		K F2 F1 F3 Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 Dy11 P
29	40	5 1 2 0.02 3 1 1 1 1 1 1 1 1 1 1
20	12	K G Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 Dy11 Dy12 P
30 31)		3 — 3 3 1 1 1 1 1 1 1 2 5 1 1 1 1 1 1 1 1 1 1 1
32		
33		1.2 2.8 1.2 1.8 1 1 1 1 1 1.5 1.5 3 2.5 2 — 1 1 1 1 1 1 1 1 1 1 1 1
34		
35		
36		4 0 2.5 1.5 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
37)		4 0 1.2 1.8 1 1 1 1 1 1 1 1 1 1 1
38		6 0 1 1.4 1 1 1 1 1 1 1 1 1
39		1 - 1 1 1 1 1 1 1 1 1 1
	14	K G1 G2 Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 Dy11 Dy12 Dy13 Dy14 P
40		2.5 7.5 0 1.2 1.8 1 1 1 1 1 1 1 1 1.5 1.5 3 2.5
	15	K Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 Dy11 Dy12 Dy13 Dy14 Dy15 P
4 1)		2 1 1 1 1 1 1 1 1 1 1 1 1 1
	16	K Dy1 Dy2 Dy3 Dy4 Dy5 Dy6 Dy7 Dy8 Dy9 Dy10 Dy11 Dy12 Dy13 Dy14 Dy15 Dy16 P
42		2 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
	19	K Dy1 Dy2 Dy3 · · · · · · · · · · · Dy17 Dy18 Dy19 P
43		2 1 1 1
Note 1 : The sl	hield pin should be c	connected to Dy5.

Replacement Information

- * : The same dimensional outline, base connection and electric characteristics.
 ** : The similar electric characteristics and the same dimensional outline and has

	The similar	electric char	actensucs	and the s	ame dim	iensionai	outline and	base	connectio
***	The similar	electric but a	different dir	mensional	outline :	and/or dif	ferent base	sonne	ection

BURLE	Hamamatsu			
Side-On Types	5			
1P21	1P21* R105** R105UH**			
1P28	1P28*			
1P28/V1	R212* 1P28**			
1P28A	1P28A*			
1P28A/V1	R372**			
1P28B	R1516*			
4473	R372**			
4526	R1923*			
4832	R636-10***			
4840	R446*			
931A, 931VA	931A*			
931B	931B* R105**			
C31004, C31004A	R406*			

Head-On Typ	es
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4501/V3	R331-05*
4516	R1166*** R1450*** R3478***
4856	R2154-02***
4900	R1307***
4903	R1387***
5819	R2154-02***
6199	R980***
6342A	R2154-02***
6342A/V1	R2154-02***
6655A	R2154-02***
8575	R329-02**
8644	R1617***
8850	R329***
C31000AJ ⁴	R4607-01***
C31000AP4	R4607-01***
C31000AJ-175 ⁵	R4607-01***
C31000AP-175 ⁵	R4607-01***
C31000M	R2256***
C31016G4	R1288***
C31016H ⁵	R1288***
C31034	R943-02***
C31034-02	R943-02***
C31034-06	R943-02***
C31034A	R943-02***
C31034A-02	R943-02***
C31034A-05	R943-02***
S83006E	R877***
S83010E	R980***
S83010EM1	R3886***
S83049F	R1307**
S83050E	R980***
S83050EM1	R3886***
S83054F	R1306**
S83068E	R6427***
9661B	1P28* 931A** 1P21**

ETL	Hamamatsu
Side-On Types	
07000	4 DOOH+ 004 A++ 4 DO4++

9780B	1P28** 931A** 1P21**
9781B	1P28** R212**
9781R	1P28A** R3788**
9783B	R106** R106UH** R4332**
9785B	R446*
9785QB	R456*

Head-On Types

Head-On Types	
9078B	R1166**
9082B	R1450**
9102KB, 9902KB 9903KB	R580**
9110BFL	R1288**
9111B, 9112B	R1924**
9113B	R1925**
9124B, 9125B, 9128B	R6095** R6094**
9135B	R5800***
9207B	R4607-01***
9214KB	R1828-01***
9250KB, 9257KB, 9266KB	R2154-02**
9330KB, 9390KB	R877**
9353B	R5912***
9524B, 9766B, 9924B	R6095**
9530KB, 9791KB	R877***
9558B	R375***
9659B	R669***
9734B	R6095***
9758KB	R1307***
9789B, 9844B	R464***
9792KB	R877***
9798B	R374**
9807KB, 9813KB	R1828-01***
9814B	R329-02***
9815B	R5496***
9820QB	R331***
9821B, 9921B	R6091***
9822B	R6091***
9823KB	R1250**
9826B	R1450*** R3478***
9828B	R5929**
9829B, 9849B	R331-05*
9829QB, 9849QB	R331*
9865B	R649***
9881B	R1450*** R3478***
9882B	R1617***
9884B, 9887B	R329-02***
9893KB/350	R3234-01***
9899B	R331-05***
9972KB, 9973KB	R1387**

PHOTONIS	Hamamatsu
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XP1911 R1166** R1450* R3478*** XP1918 R2076*** R762** XP2012B, XP2072B R580** XP2013B R1387*** XP2015B R1767*** XP2017B R2066*** XP2020 R1828-01* XP2020/Q R2059* XP2050 R877*** XP2052B R980** XP202B R2154-02** XP203B R3256**	
XP2012B, XP2072B R580** XP2013B R1387*** XP2015B R1767*** XP2017B R2066*** XP2020 R1828-01* XP2020/Q R2059* XP2050 R877*** XP2052B R980** XP2020B R2154-02** XP203B R3256**	
XP2013B R1387*** XP2015B R1767*** XP2017B R2066*** XP2020 R1828-01* XP2020/Q R2059* XP2050 R877*** XP2052B R980** XP2028 R2154-02** XP203B R3256**	
XP2015B R1767*** XP2017B R2066*** XP2020 R1828-01* XP2020/Q R2059* XP2050 R877*** XP2052B R980** XP202B R2154-02** XP203B R3256**	
XP2017B R2066*** XP2020 R1828-01* XP2020/Q R2059* XP2050 R877*** XP2052B R980** XP202B R2154-02** XP203B R3256**	
XP2020 R1828-01* XP2020/Q R2059* XP2050 R877*** XP2052B R980** XP202B R2154-02** XP203B R3256**	
XP2020/Q R2059* XP2050 R877*** XP2052B R980** XP202B R2154-02** XP203B R3256**	
XP2050 R877*** XP2052B R980** XP202B R2154-02** XP2203B R3256**	
XP2052B R980** XP2202B R2154-02** XP2203B R3256**	
XP2202B R2154-02** XP2203B R3256**	
XP2203B R3256**	
XP2206B R4607-01***	
XP2262B R329-02***	
XP2282B R2083***	
XP2312B R6091***	
XP2802 R1166***	
XP2971, XP2972 R6427**	
XP2978 R7057**	
XP3462B R6091***	
XP4500B R1584***	
XP4500B R1584***	
XP4512B R1250***	

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e 1: The shield pin should be connected to Dy5. 2: Acc to be connected to Dy7 except R4998

Photomultiplier Tube Assemblies

Photomultiplier tube assemblies integrate a photomultiplier tube and a D-type or DP-type socket assemby (see page 78 for socket assemblies) into a matching magnetic shields. The D-type photomultiplier tube assemblies require a high-voltage power supply, while the DP-type includes a DC-DC converter high-voltage power supply and can be operated by simply supplying +15V.



▲Photomultiplier Tube Assemblies

D-Type PMT Assemblies (with a Head-on Type PMT)

		Built-in PMT Maximum Ratings						Dimensions		
Type No.	Diameter (mm)	Type No.	Photo- Cathode	Window Material	Gain	Supply Voltage (V)	Supply Voltage (V)	Bleeder Current (mA)	(mm)	
H3164-10	10	R1635	BA	К	1.1×10^{6}	1250	-1500	0.41	φ10.5 × 95	
H3695-10	10	R2496	BA	Q	1.1 × 10 ⁶	1250	-1500	0.37	φ11.3×95	
H3165-10	13	R647	BA	К	1.0 × 10 ⁶	1000	-1250	0.34	φ14.3×116	
H6520	19	R1166	BA	К	9.5 × 10 ⁵	1000	-1250	0.33	ф23.5 × 130	
H6524	19	R1450	BA	К	1.7 × 10 ⁶	1500	-1800	0.43	ф23.5 × 130	
H6152-01	25	R5505	BA	К	5.0 × 10 ⁵	2000	-2300	0.41	φ31.0×75	
H6533	25	R4998	BA	К	5.7 × 10 ⁶	2250	-2500	0.36	ф31.0 × 120	
H3690-03	28	R1355	BA	К	2.1 × 10 ⁶	1500	-1900	0.65	ф33.0 × 140	
H3171-04	28	R1398	BA	U	2.1×10^{6}	1500	-1900	0.65	ф33.0 × 140	
H3173-03	28	R1668	BA	Q	8.4 × 10 ⁵	1500	-1900	0.57	ф33.0 × 140	
H3178-51	38	R580	BA	К	1.1 × 10 ⁶	1500	-1750	0.63	φ47.0 × 162	
H6153-01	38	R5946	BA	К	1.1 × 10 ⁶	2000	-2300	0.39	ф45.0×80	

			Built-i	n PMT	Maximu				
Type No.	Diameter (mm)	Type No.	Photo- Cathode	Window [®] Material	Gain	Supply Voltage (V)	Supply Voltage (V)	Bleeder Current (mA)	Dimensions (mm)
H6410	51	R329-02	ВА	К	3.0 × 10 ⁶	2000	-2700	0.67	φ60.0 × 200
H6521	51	R2256-02	ВА	Q	3.0 × 10 ⁶	2000	-2700	0.67	φ60.0 × 200
H6522	51	R5113-02	ВА	U	3.0 × 10 ⁶	2000	-2700	0.67	φ60.0 × 200
H1949-51	51	R1828-01	ВА	К	2.0 × 10 ⁷	2500	-3000	0.70	φ60.0 × 235
H3177-51	51	R2059	ВА	Q	2.0 × 10 ⁷	2500	-3000	0.70	φ60.0 × 235
H2431-50	51	R2083	ВА	К	2.5 × 10 ⁶	3000	-3500	0.61	φ60.0 × 200
H3378-50	51	R3377	ВА	Q	2.5 × 10 ⁶	3000	-3500	0.61	φ60.0 × 200
H6614-01	51	R5924	ВА	К	1.0×10^{7}	2000	-2300	0.33	ф60.0×80
H6156-50	51	R5496	ВА	K	1.3 × 10 ⁷	2500	-3000	0.71	φ60.0×215
H6559	76	R6091	ВА	K	1.0 × 10 ⁷	2000	-2500	0.62	ф83.0×218
H6527	127	R1250	ВА	К	1.4 × 10 ⁷	2000	-3000	1.02	φ142.0 × 360
H6528	127	R1584	ВА	U	1.4 × 10 ⁷	2000	-3000	1.02	φ142.0 × 360
R3600-06	508	R3600-02	ВА	K	1.0 × 10 ⁷	2000	-2500	0.44	φ508.0 × 695

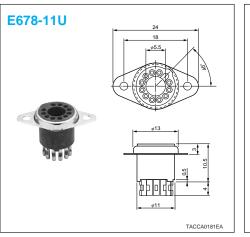
DP-Type PMT Assemblies (with a Side-on Type PMT and Built-in HV Power Supply)

Type No.		Built-in PMT	Input Voltage Range (V)	Maximum Input Current (mA)	Power Supply Output Voltage Range (V)	Power Supply Output Voltage Programming	Dimensions (mm)
	H957-01	R212				Resistance	32.0 dia. × 100 L
	H957-06	931B	+15 ± 0.5	150	-400 to 900	(0 to 10kΩ) or	
L	H957-08	R928				Voltage (0 to 4V)	
	H7318	R3896	+15 ± 1	45	0 to -1250	50kΩ Potentiometer or Voltage (0 to 5V)	35.4 dia. × 113 L

74 75

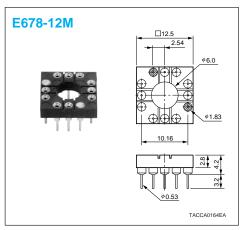
ACCESSORIES FOR PHOTOMULTIPLIER TUBES

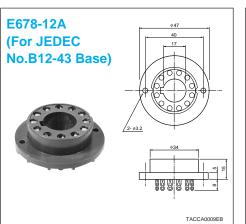
E678 Series Sockets

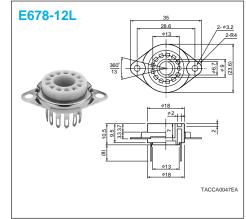


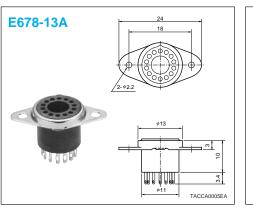


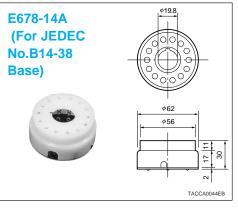


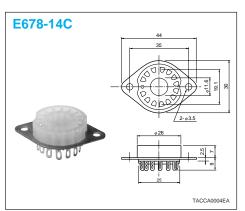


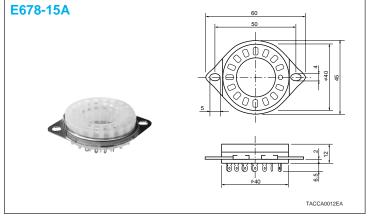


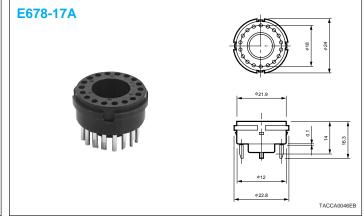


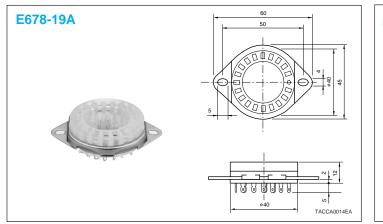


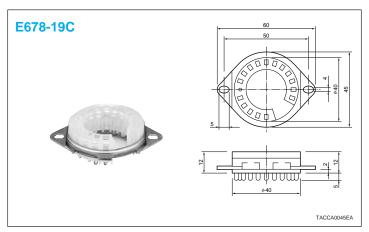


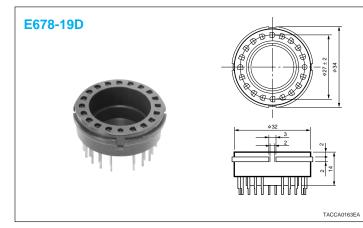


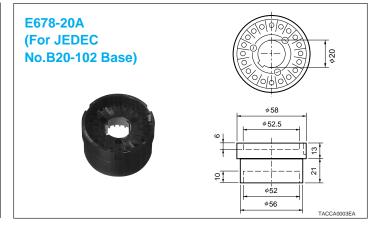


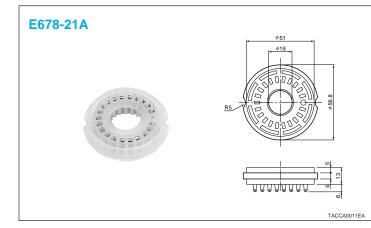


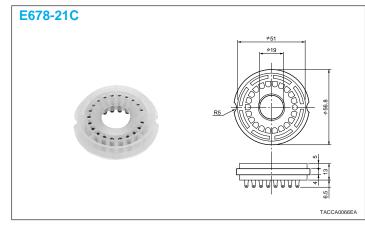


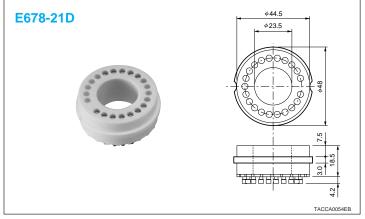


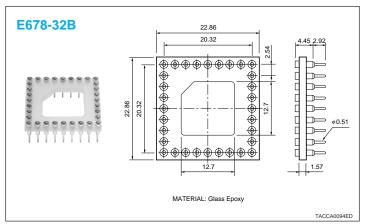












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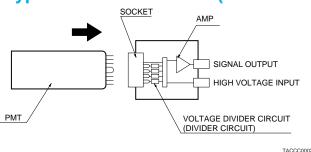
Socket Assemblies

(For further information, a detailed catalog is available.)

Operating a photomultiplier tube requires a voltage-divider circuit (divider circuit). For easier handling and operation of photomultiplier tubes, Hamamatsu provides a complete line of socket assemblies which are carefully engineered to integrate a socket and optimum voltage-divider circuit into a compact case. In addition, socket assemblies which further include a preamplifier or high-voltage power supply are available.

The socket assemblies are classified into three types by their functions as described below.

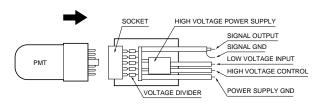
DA-Type Socket Assemblies (with built-in voltage divider and amplifier)



The DA-type socket assemblies incorporate a current-to-voltage conversion amplifier in addition to a voltage-divider circuit. High voltage (for PMT) and low voltage (for amplifier) power supplies are required. Since the high impedance output of the photomultiplier tube is connected to the amplifier at a minimum distance, the problem of external noise induced in connecting cables can be eliminated. Two families of DA-type socket assemblies are available: the C1556 series for a bandwidth from DC to 10kHz and the C1053 series from DC up to 5MHz. Both families are designed for use with 28mm (1-1/8 inch)diameter side-on and head-on photomultiplier tubes.

Type No.		C1556-50	C1556-51	C1556-03	C1053-50	C1053-51	C1053-03		
Applicable PMT		28mm (1-1/8") dia. 28mm (1-1/8") dia.		BNC Connector	28mm (1-1/8") dia. 28mm (1-1/8") dia.		BNC Connector		
		Head-on	Side-on	Input	Head-on Side-on		Input		
Max. Supply Voltage to Voltage	ge Divider	-150	0Vdc	_	-150	_			
Supply Voltage to Amplific	er		±12 to 15Vdc		±12 to 15 Vdc				
Current-to-Voltage Conversion	on Factor	0.3 V / μΑ			0.3V / μA				
Max. Input Signal Current	DC	12.5 μΑ	15 μΑ	33 μΑ	12.5 μΑ 15 μΑ		33 μΑ		
(at -1000V, 10V output)	Pulse		33 μΑ		33 μA(DC to 2.5	33 μA(DC to 2.5MHz) 6.6 μA(DC to 5MHz, 2V output)			
Max. Output Voltage (Unterminated)		10V peak (10 kHz)			10V peak (2.5MHz), 2V peak (5MHz)				
Frequency Bandwidth			DC to 10 kHz		DC to 5MHz				

DP-Type Socket Assemblies (with built-in voltage divider and power supply)



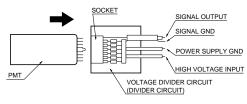
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The DP-type socket assemblies feature a built-in voltage divider and compact high-voltage power supply. By applying a +15 V supply to the power supply, easy operation of a photomultiplier tube is possible. As standard products, the C956 series assemblies are provided for use with 28mm (1-1/8 inch) diameter side-on and head-on photomultiplier tubes.

TACCC0003EB

Type No.	C6270	C956-07		
Applicable PMT	28mm (1-1/8") dia. side-on	28mm (1-1/8") dia. head-on		
Input Voltage	+15 ± 1 Vdc			
Input Current	45 mA Max.	140mA Max.		
Output Voltage Range	0 to -1250 Vdc Typ.	-200 to -1250 Vdc Typ.		
Input Regulation	±0.01% Typ. (at + 15 ± 1 Vdc)	±0.05% Max. (at + 15 ± 1 Vdc)		
Maximum PMT Signal Output at -1000V	100 μΑ Тур.	15mA μA Typ.		

D-Type Socket Assemblies



For Side-On Photomultiplier Tubes

	or order our motormaniphor rapoc										
Code	Socket Assembly Type No.	Applicable PMT Diameter	Grounded Electrode/ Supply Voltage Polarity	Output Signal							
1	E850 -13	13mm(1/2")	Anode/-	DC/Pulse							
2	E717 -63	28mm(1-1/8")	Anode/-	DC/Pulse							
3	-35		Anode/- · Cathode/+	DC/Pulse							

For Head-On Photomultiplier Tubes

	LCODE ASSEMBLY · ·		Applicable PMT Diameter	Grounded Electrode/ Supply Voltage Polarity	Output Signa	
	4	E1761	-04		Anode/-	DC/Pulse
	5		-05	10mm(3/8")	Anode/-	DC/Pulse
	6		-21		Anode/-	DC/Pulse
	7 E8 8 9	E849	-35		Anode/-	DC/Pulse
			-52	13mm(1/2")	Anode/-	DC/Pulse
			-68	1311111(1/2)	Anode/-	DC/Pulse
			-90		Anode/-	DC/Pulse
	11	E2253	-08		Cathode/+	Pulse
	12 13 E97 14		-05		Anode/-	DC/Pulse
		E974	-13		Anode/-	DC/Pulse
			-14	19mm(3/4")	Cathode/+	Pulse
			-17		Anode/-	DC/Pulse
	16		-18		Anode/-	DC/Pulse
	17		-22		Anode/-	DC/Pulse
	18	E2924			Anode/-	DC/Pulse
	19		-500	05 (411)	Anode/-	DC/Pulse
	20		-05	25mm(1")	Cathode/+	Pulse
	21	E2624	-500		Anode/-	DC/Pulse
	22	E2624			Anode/-	DC/Pulse
	23		-05		Cathode/+	Pulse
	24	E990	-07	28mm(1-1/8")	Anode/-	DC/Pulse
	25		-08		Cathode/+	Pulse
	26		-28		Anode/-	DC/Pulse
	27	E2183	-502	38mm(1-1/2")	Cathode/+	Pulse
	28		-500	33/11/1(17/2)	Anode/-	DC/Pulse

NOTE) Please consult our sales office when you use a photomultiplier tube in a vacuum.

The D-type socket assemblies incorporate a socket and voltagedivider circuit. A high voltage power supply and a current/electric charge signal processing circuit are required. The following four types are available according to the grounded electrode, supply voltage polarity and output signal form.

- 1. Anode ground, DC output
- 2. Anode ground, DC/pulse output
- 3. Cathode ground, pulse output
- 4. Anode or cathode ground, DC/pulse output

Code	Socket Assembly Type No.	Applicable PMT Diameter	Grounded Electrode/ Supply Voltage Polarity	Output Signal
29	E1198 -23		Cathode/+	Pulse
20	-05		Anode/-	DC/Pulse
31	-07		Anode/-	DC/Pulse
32	-22		Anode/-	DC/Pulse
33	E2380 -501		Anode/-	DC/Pulse
34	-502		Anode/-	DC/Pulse
35	-503	-	Anode/-	DC/Pulse
36	E2979 -500		Anode/-	DC/Pulse
37	E4512 -503	[76mm(3")]	Cathode/+	Pulse
38	-504	[127mm(5")]	Cathode/+	Pulse
39	-505		Cathode/+	Pulse
40	E934 -503		Anode/-	DC/Pulse
41	E1435 -02		Anode/-	DC/Pulse
42	E4229 -501		Anode/-	DC/Pulse
43	E1458 -501		Anode/-	DC/Pulse
44	-502		Cathode/+	Pulse
45	E6133 -03	25mm(1") For highly magnetic environments	Anode/-	DC/Pulse
46	E6132-02	51mm(2") For highly magnetic environments	Anode/-	DC/Pulse

Metal Package Photomultiplier Tubes

			•	
Code	Socket Assembly Type No.	Applicable PMT	Grounded Electrode/ Supply Voltage Polarity	Output Signal
47	E5780	R7400U	Anode/-	DC/Pulse
48	E5996	R5900U	Anode/-	DC/Pulse
49	E7083	R5900U-00-M4	Anode/-	DC/Pulse
50	E6736	R5900U-00-L16	Anode/-	DC/Pulse
51	E6669	R5900U-00-C8	Anode/-	DC/Pulse

High-Voltage Power Supplies

The output of a photomultiplier tube is extremely sensitive to the applied voltage. Even small variations in applied voltage greatly affect measurement accuracy. Thus a highly stable source of high voltage is required. (See page 8.) Hamamatsu regulated high-voltage power supplies are designed for precision measurement using a photomultiplier tube and manufactured with careful consideration given to high stability and low ripple. To meet various needs, they are available in a wide range of configurations and performances, including unit types for PC board mounting, bench-top types and a 5kV output type for MCP-PMTs.



▲C3830

Type No.	Output Voltage Range (Vdc)	Maximum Output Current (mA)	Input Voltage	Dimensions (W×H×D) (mm)	Weight
Unit Types					
C4710	-240 to -1500	1	+15Vdc	65 × 27.5 × 45	105g
C4710-01	-240 to -1500	1	+12Vdc	65 × 27.5 × 45	105g
C4710-02	-240 to -1500	1	+24Vdc	65 × 27.5 × 45	105g
C4710-50	+240 to +1500	1	+15Vdc	65 × 27.5 × 45	105g
C4710-51	+240 to +1500	1	+12Vdc	65 × 27.5 × 45	105g
C4710-52	+240 to +1500	1	+24Vdc	65 × 27.5 × 45	105g
C4900	0 to -1250	0.6	+15Vdc	46 × 24 × 12	31g
C4900-01	0 to -1250	0.5	+12Vdc	46 × 24 × 12	31g
C4900-50	0 to +1250	0.6	+15Vdc	46 × 24 × 12	31g
C4900-51	0 to +1250	0.5	+12Vdc	46 × 24 × 12	31g

Bench-Top Types

C2633	±200 to ±3071	5	100/120/230Vac	280 × 110 × 350	8.5kg
C3350	0 to ±3000	10	100/115/220/230Vac	$220\times120\times350$	8kg
C3360	0 to -5000	1	100-120/220-240Vac	$210\times99\times273$	3.5kg
C3830	-200 to -1500/±5/±15	1/500/200	100/120/220/230Vac	255 × 54 × 230	2.8kg
C4720	+200 to +1500/±5/±15	1/500/200	100/115/220/240Vac	255 × 54 × 230	2.8kg

Thermoelectric Coolers

(For more information, a detailed catalog is available.)

The thermionic electron emission from a photocathode and dynodes is a major factor that determines the dark current of the photomultiplier tube. (See page 8.) Cooling the photomultiplier tube can efficiently reduce the dark current and improve the S/N ratio, resulting in an significant enhancement in the detection limit. Hamamatsu provides a variety of thermoelectric coolers specifically designed for photomultiplier tubes to meet various needs.



▲C4877

		_0.07	•	
Type No.	Applicable PMT	Input Voltage (Vac)	Cooling Temperature (°C)*	Remarks
C659-70 Series	28mm (1-1/8") Dia. Side-on	100/115/220	Approx15	
C659-50 Series	28mm (1-1/8"),38mm (1-1/2") Dia. Head-on	100/115/220	Approx20	
C4877 Series	38mm (1-1/2") ,51mm (2") Dia. Head-on	100/120/230	Approx30	Temperature controllable
C4878 Series	MCP-PMT	100/120/230	Approx30	Temperature controllable

^{*} With +20°C coolant.

Socket assemblies and holders are sold separately.

Magnetic Shield Cases

Photomultiplier tubes are generally very susceptible to magnetic fields. Even terrestrial magnetism will have a detrimental effect on the photomultiplier tube output. (See page 9.) Hamamatsu E989 series magnetic shield cases are designed to protect photomultiplier tubes from magnetic field effects. Since the E989 series magnetic shield cases are made of permalloy which has high permeability (about 10⁵), the magnetic field strength within the shield case with respect to the external magnetic field strength (the reciprocal of this is called shielding factor) can be greatly attenuated down to 1/1000 to 1/10000, thus ensuring stable output from photomultiplier tubes even operating in magnetic fields.



▲ Magnetic Shield Cases

Appli	cable PMT Diameter	Type No.	Internal Diameter (mm)	Thickness (mm)	Length (mm)	Weight (g)
Side-on	13 mm (1/2")	E989-10	14.5	0.5	47 ± 0.5	10
	28 mm (1-1/8")	E989	33.6 ± 0.8	0.8	80 ± 1	66
Head-on	ead-on 10 mm (3/8") E		12 ± 0.5	0.5	48 ± 0.5	9
	13 mm (1/2")	E989-09	16 ± 0.5	0.8	75 ± 0.5	28
	19 mm (3/4")	E989-02	23 ± 0.5	0.8	95 ± 1	50
	25 mm (1")	E989-39	29 ± 0.5	0.8	48 ± 0.5	32
	28 mm (1-1/8")	E989-03	32 ± 0.5	0.8	120 ± 1	90
	38 mm (1-1/2")	E989-04	44 +1	0.8	100 ± 1	102
	51 mm (2")	E989-05	60 +1	0.8	130 ± 1	180
	76 mm (3")	E989-15	80 +1.5	0.8	120 ± 1	200
	127 mm (5")	E989-26*	138 ±1.5	0.8	170 ± 1	600

* With mounting tabs.

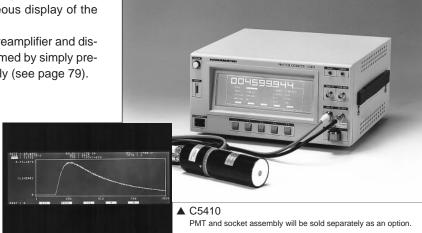
Photon Counters and Related Products

Recently, photon counting has become widely used as an effective technique for detecting very low light levels in various fields such as biology, chemistry and medicine. As a leading manufacturer of photomultiplier tubes, Hamamatsu provides a variety of photon counters and related products. Our product line includes the C5410 Photon Counter that allows time-resolved photometry and the C3866 Photon Counting Units that integrate only essential functions into a compact case. Please feel free to contact Hamamatsu sales offices for further information. Photon counting modules, photon counting head, photon counting unit and prescaler, are also available.

Photon Counter C5410 Series

The C5410 is a time-resolved photon counter with a large-screen liquid crystal display (640 \times 200 dots) enabling an instantaneous display of the measured waveform as well as numerical count rates.

The C5410 also includes a high-voltage power supply, preamplifier and discriminator. High-precision photon counting can be performed by simply preparing a photomultiplier tube and D-type socket assembly (see page 79).



▲ Instantaneous display of the measured

Photon Counting Modules Photon Counting Heads

H6180 · H5920 · H6240 Series

The H6180, H5920 and H6240 series are compact photon counting heads comprising a low noise PMT, a high speed photon counting circuit, and a high voltage power supply. The operation only requires connecting with a +5Vdc (±5Vdc for H5920-01) power supply and a pulse counter. No discrimination level or high voltage adjustment are required of the user. The H5920 series employs a 1/10 prescaler for higher count rate operations.

H3460 Series

The Photon Counting Heads integrating a photomultiplier tube and a preamplifier/discriminator into a compact case. Photon counting with a high S/N ratio is done by simply making connections to the external high-voltage power supply for the photomultiplier tube, power supply for the preamplifier/ discriminator, and pulse counter.

Photon Counting Unit C3866

The C3866 converts the photoelectron pulses of the photomultiplier tube into 5V digital signals by the built-in amplifier/discriminator. Use of a high-speed electronic circuit permits light measurements with excellent linearity up to a maximum count rate of 10⁷ cps.

Prescaler C3589

The C3589 Prescaler divides the ECL output pulses from the H3460 series Photon Counting Heads by 10 and converts them into TTL level signals. The C3589 allows photon counting operations over a wide dynamic range without using a high-speed counter.



▲ LEFT: H6240 RIGHT: H6180-01/H5920-01 with optional mounting flange



▲ H3460



▲ LEFT: C3866 RIGHT: C3589

ELECTRON MULTIPLIER TUBES

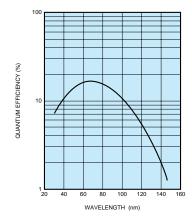
Electron multipliers (also called ion multipliers) are specially designed for the detection and measurement of electrons, charged particles such as ions, VUV radiations and soft X-rays. Hamamatsu electron multipliers have high gain and low noise, making them suitable for the detection of very small or low energy particles by using the counting method. They are well suited for mass spectroscopy, field ion microscopy, and electron or VUV spectroscopy such as Auger spectroscopy, AES and ESCA.

Each type has Cu-BeO dynodes connected by built-in divider resistors (1M Ω per stage) and is supplied in an evacuated glass bulb. The first dynode can be replaced by a photocathode of Cs-I, K-Br, etc. for use in VUV photometry.

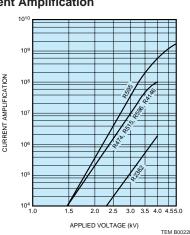
In such applications as ICP-MASS where electron multipliers are used in harsh atmosphere, use of the R5150 with superior environmental resistance is recommended. Also, for TOF-MASS applications, use of the R2362 with mesh dynodes is recommended.

A			Dy	node		Ch	aracteri	stics	Anode		Maximum Ratings				
Type. No.	Out - line	Number of Stages	Structure	Material	Radiation Opening (mm)	Supply Voltage (Vdc)	Gain Typ.	Rise Time Typ.	to all Other Electrode Capacitance (pF)	Anode to First Dynode Voltage (Vdc)	Anode to Last Dynode Voltage (Vdc)	Average Anode Current (μ A)	Operating Vacuum Level (Pa)		
Head-	Head-On Types														
R474	1	16	Box-and-grid	Cu-BeO	8×6	2400	1 × 10 ⁶	9.3	5.0	4000	350	10	133 × 10 ⁻⁴		
R515	2	16	Box-and-grid	Cu-BeO	8×6	2400	1 × 10 ⁶	9.3	4.0	4000	350	10	133 × 10 ⁻⁴		
R596	3	16	Box-and-grid	Cu-BeO	12×10	2400	1 × 10 ⁶	10	9.0	4000	400	10	133 × 10 ⁻⁴		
R595	4	20	Box-and-grid	Cu-BeO	12×10	3000	4 × 10 ⁷	12	9.0	5000	400	10	133 × 10 ⁻⁴		
R2362	6	23	Mesh	Cu-BeO	20dia.	3450	5 × 10 ⁵	3.5	23	4000	350	10	133 × 10 ⁻⁴		
R5150	6	16	Box-and-line	Cu-BeO	9×8	2400	1 × 10 ⁶	1.7	4.0	3500	300	10	133 × 10 ⁻⁴		

Typical Spectral Response of Cu-BeO Used for Dynodes



• Typical Current Amplification



Unit: mm

PY1

ANODE (P)

P 20

RESISTORS
(HML) 15PCS)

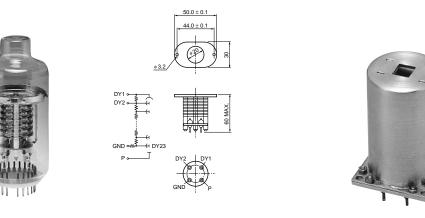
ANODE (P)

\$\text{R596}\$

4 R595

A R596

4 R595



ANODE 32.0 ± 0.5 DY1

0009EA

TYPICAL PHOTOCATHODE SPECTRAL RESPONSE

/ WARNING



Take sufficient care to avoid an electric shock hazard

A high voltage used in photomultiplier tube operation may present a shock hazard. Photomultiplier tubes should be installed and handled only by qualified personnel that have been instructed in handling of high voltages. Designs of equipment utilizing these devices should incorporate appropriate interlocks to protect the operator and service personnel.

The metal housing of the Metal Package PMT R5600 series is connected to the photocathode (potential) so that it becomes a high voltage potential when the product is operated at a negative high voltage (anode grounded).

PRECAUTIONS FOR USE

Handle tubes with extreme care

Photomultiplier tubes have evacuated glass envelopes. Allowing the glass to be scratched or to be subjected to shock can cause cracks. Extreme care should be taken in handling, especially for tubes with graded sealing of synthetic silical

Keep faceplate and base clean

Do not touch the faceplate and base with bare hands. Dirt and fingerprints on the faceplate cause loss of transmittance and dirt on the base may cause ohmic leakage. Should they become soiled, wipe it clean using alcohol.

Do not expose to strong light

Direct sunlight and other strong illumination may cause damage to the photocathode. They must not be allowed to strike the photocathode, even when the tube is not operated.

Handling of tubes with a glass base

A glass base (also called button stem) is less rugged than a plastic base, so care should be taken in handling this type of tube. For example, when fabricating the voltage-divider circuit, solder the divider resistors to socket lugs while the tube is inserted in the socket.

Cooling of tubes

When cooling a photomultiplier tube, the photocathode section is usually cooled. However, if you suppose that the base is also cooled down to -30°C or below, please consult our sales office in advance.

Helium permeation through silica bulb

Helium will permeate through the silica bulb, leading to an increase in noise. Avoid operating or storing tubes in an environment where helium is present.

Data and specifications listed in this catalog are subject to change due to product improvement and other factors. Before specifying any of the types in your production equipment, please consult our sales office.

WARRANTY

All Hamamatsu photomultiplier tubes and related products are warranted to the original purchaser for a period of 12 months following the date of shipment. The warranty is limited to repair or replacement of any defective material due to defects in workmanship or materials used in manufacture.

- A: Any claim for damage of shipment must be made directly to the delivering carrier within five days.
- B: Customers must inspect and test all detectors within 30 days after shipment. Failure to accomplish said incoming inspection shall limit all claims to 75% of invoice value.
- C: No credit will be issued for broken detectors unless in the opinion of Hamamatsu the damage is due to a bulb crack or a crack in a graded seal traceable to a manufacturing defect.

- D: No credit will be issued for any detector which in the judgment of Hamamatsu has been damaged, abused, modified or whose serial number or type number have been obliterated or defaced.
- E: No detectors will be accepted for return unless permission has been obtained from Hamamatsu in writing, the shipment has been returned prepaid and insured, the detectors are packed in their original box and accompanied by the original data sheet furnished to the customer with the tube, and a full written explanation of the reason for rejection of each detector.
- F: When products are used at a condition which exceeds the specified maximum ratings or which could hardly be anticipated, Hamamatsu will not be the guarantor of the products.

Curve Codes		Photocathode Materials	Window Materials	Peak Wavelength		elength				
				Range	Radiant	Q.E.	PMT Examples			
					Sensitivity					
				(nm)	(nm)	(nm)				
Semitransparent Photocathode										
\circ	100M	Cs-I	MgF ₂	115 to 200	140	130	R972, R1081, R6835			
0	200M	Cs-Te	MgF ₂	115 to 320	240	240	R1080, R6836			
	201M	Cs-Te	MgF ₂	115 to 320	220	220	R3809U-57			
0	200S	Cs-Te	Synthetic silica	160 to 320	240	240	R759, R821, R1893, R6834			
	201S	Cs-Te	Synthetic silica	160 to 320	240	220	R2078			
0	400K	Bialkali	Borosilicate	300 to 650	420	390	R329-02, R331-05, R464, R5496, R1635, R647, R1166, R2486-02, R2154-02, R3998-02, R5800, R6427, R6091, R5924, R5946, R6095, R580, R1828-01, R5611-01, R4998, R1924, R3234-01, R7400U, R5900U			
	400U	Bialkali	UV	185 to 650	420	390	R7400U-03,R1584			
\circ	400S	Bialkali	Synthetic silica	160 to 650	420	390	R2496, R7400U-06			
0	401K	High temp. bialkali	Borosilicate	300 to 650	375	360	R1281, R1288, R1705, R3991, R4177-01, R4607-01			
Ö	402K	Low noise bialkali	Borosilicate	300 to 650	375	360	R2557, R2801, R3550			
\mathbb{Z}	403K	Bialkali	Synthetic Silica	160 to 650	400	420	R3809U-52, R5916U-52			
$\overline{\mathcal{P}}$	430U	Bialkali	UV	185 to 650	375	300	R2693			

430

420

420

420

420

600

600

800

800

115 to 850

300 to 850

160 to 850

185 to 850

300 to 900

160 to 910

300 to 900

400 to 1200

400 to 1200

360

360

280

290

400

590

580

780

780

R3809U-58

R5070, R5929

R3809U-59

R375, R3809U-50, R5916U-50

R374, R1463, R1464, R2368

R669, R2066, R2228, R2257

R316-02, R632-01, R1767, R5108

R3809U-51 R5916U-51

R550, R649, R1387, R1513, R1617, R1878, R1894, R1925

Spectral Response

Reflection mode Photocathode 115 to 195 120 120 R1259, R7511 250S Cs-Te Synthetic silica 160 to 320 200 190 R166UH, R6354 250M Cs-Te MgF₂ 115 to 320 200 R1220, R7311 350K(S-4) Sb-Cs Borosilicate 300 to 650 400 350 R105, 1P21, 931A R212, R3810, R6350, 1P28 UV 350U(S-5) Sb-Cs 185 to 650 340 Sb-Cs 350S(S-19) Synthetic silica 160 to 650 340 453K Bialkali Borosilicate 300 to 650 400 360 931B Low noise Bialkali UV 185 to 680 400 300 R1527, R4220, R6353 Bialkali 185 to 750 420 R3788, R6352 Multialkali Borosilicate 300 to 800 510 R1923 Multialkali UV 185 to 830 530 300 R6358 Multialkali UV 185 to 850 430 R4632 Multialkali UV 185 to 850 R3811, R6355 Multialkali UV 185 to 850 430 280 R3896 UV 185 to 900 400 260 R2949 UV Multialkali 185 to 900 400 260 R928 UV Multialkali 185 to 900 450 370 R1477-06 GaAs(Cs) UV 185 to 930 300 to 800 300 R636-10 650S GaAs (Cs) Synthetic silica 160 to 930 300 to 800 280 R943-02 InGaAs(Cs) 185 to 1010 400 330 R2658 InGaAs(Cs) 300 to 1040 350 R3310-02

Multialkali

Multialkali

Multialkali

Multialkali

Multialkali

Multialkali

Aa-O-Cs

Ag-O-Cs

502K (Super S20) Multialkali

MqF₂

UV

Borosilicate

Borosilicate

Borosilicate

Borosilicate

Borosilicate

Synthetic silica

Synthetic silica

500M

500S

500L

501S

501K

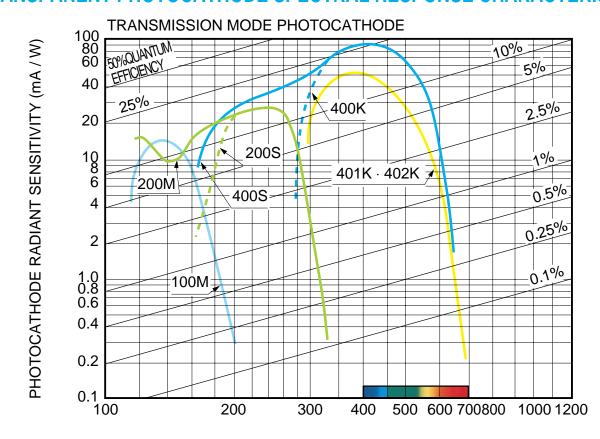
700M

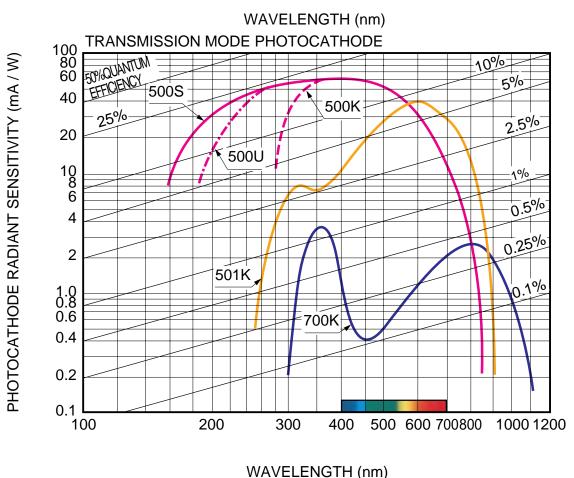
700K(S-1)

500K(S-20)

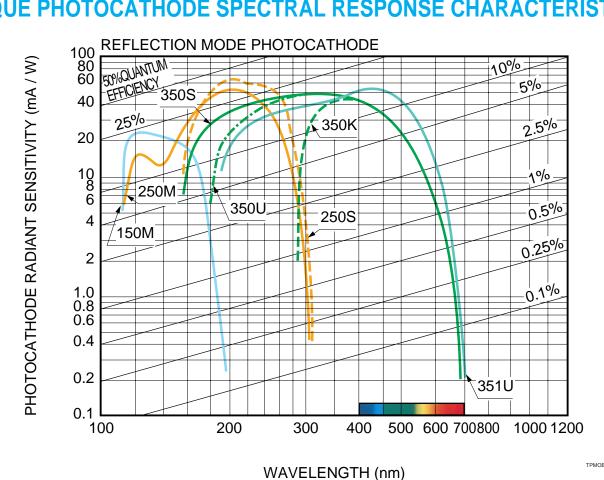
[:] Spectral response curves are shown on page 88, 89

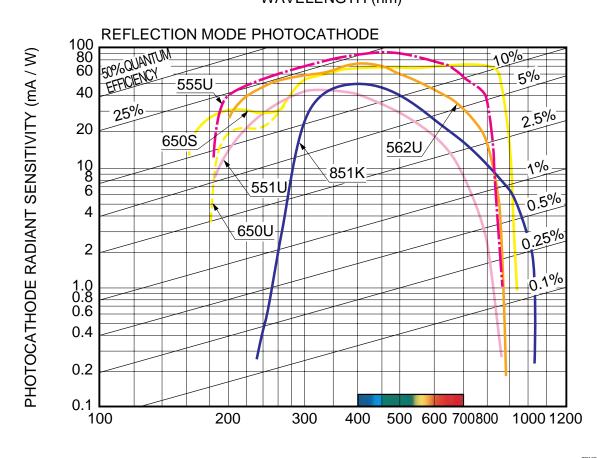
SEMITRANSPARENT PHOTOCATHODE SPECTRAL RESPONSE CHARACTERISTICS





OPAQUE PHOTOCATHODE SPECTRAL RESPONSE CHARACTERISTICS





WAVELENGTH (nm)

89

88

NOTES

- A *: Newly listed in this catalog.
- Refer to pages 88 and 89 for typical spectral response charts.
- Photocathode materials

BA: Bialkali

LBA : Low dark current bialkali HBA: High temperature bialkali

: Multialkali MA

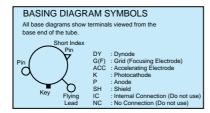
EMA : Extended red multialkali

Window materials

MF : MgF₂
Q : Synthetic silica : Borosilicate glass

U : UV glass

Basing diagram



- Dynode structure
 - B : Box-and-grid VB : Venetian blind CC : Circular-cage : Linear-focused
 - B+L : Box and linear focused
 - FM: Fine Mesh CM : Coarse Mesh MC : Metal Channel
- **⑥** ★: A socket will be supplied with the tube.
 - ■: Sockets may be available from electronics supply houses or our sales office. (See pages 76 and 77.)
- ♠ The maximum ambient temperature range is -80 to +50°C except the following tubes using a high temperature bialkali photocathode which withstands from -80 up to +175°C. When a tube is operated below -30°C see page 86, "PRECAUTIONS FOR USE"

Diameter	Type No.	Diameter	Type No.
13mm (1/2")	R4177-01	38mm (1-1/2")	R1705
19mm (3/4")	R1281,R3991	51mm (2")	R4607-01
25mm (1")	R1288	_	_

- Averaged over any interval of 30 seconds maximum.
- Measured at the peak wavelength.
- Refer to page 72 for voltage distribution ratios.
- M Anode characteristics are measured with the supply voltage and voltage distribution ratio specified by Note L.
- Anode characteristics are measured with the specified anode-to-cathode supply voltage.
- at 122nm
- b at 254nm
- at 852nm
- Measured using a red filter Toshiba IR-D80A.
- at 4A/Im
- at 10A/lm
- at 1000A/lm
- (h) Dark counts per second (cps)
- Dark counts per second (cps) after one hour storage at -20°C. Background noise per minute (cpm)

HAMAMATSU

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Information in this catalog is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omission.

Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein.

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